



Cite this: *J. Mater. Chem. C*, 2022,  
10, 13395

## Recent progress on the effects of impurities and defects on the properties of Ga<sub>2</sub>O<sub>3</sub>

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Ga<sub>2</sub>O<sub>3</sub> is attractive for power devices and solar-blind ultraviolet photodetectors due to its ultra-wide bandgap, large breakdown field, and favorable stability. However, it is difficult to prepare the ideal Ga<sub>2</sub>O<sub>3</sub> since there are plenty of defects (e.g., vacancies and interstitial atoms) in the bulk and films which can affect the physical properties of Ga<sub>2</sub>O<sub>3</sub>. Besides, the deep level defects act as trapped centers and have influence on the sensitivity and responsivity of optoelectronic devices. It has been discovered that doping is an effective strategy to modulate the properties of Ga<sub>2</sub>O<sub>3</sub>. In this review, the effects of defects and impurities on the material properties of Ga<sub>2</sub>O<sub>3</sub> are mainly discussed. Considering that β-Ga<sub>2</sub>O<sub>3</sub> is the most stable and the most studied currently, it is the main focus of this review. Firstly, the intrinsic properties (e.g., electronic, absorption, thermal and mechanical properties) of β-Ga<sub>2</sub>O<sub>3</sub> are introduced, and then the influence of impurities (e.g., dopants and passivators) and defects on the electronic properties of β-Ga<sub>2</sub>O<sub>3</sub> is discussed emphatically. Besides, the other properties (e.g., luminescence, magnetic, and piezoelectric properties) of β-Ga<sub>2</sub>O<sub>3</sub> modulated by defects and impurities are also briefly discussed. Meanwhile, some new research directions are also worth exploring. These problems and potential directions are summarized and discussed in the last section.

Received 20th March 2022,  
Accepted 29th April 2022

DOI: 10.1039/d2tc01128j

rsc.li/materials-c

### I. Introduction

Gallium oxide (Ga<sub>2</sub>O<sub>3</sub>), one of the ultra-wide bandgap (UWBG) semiconductors, has attracted more and more attention in recent years, as shown in Fig. 1.<sup>1–5</sup> The literature on Ga<sub>2</sub>O<sub>3</sub> exploded in the beginning of this century. Ga<sub>2</sub>O<sub>3</sub> possesses many superior characteristics compared with other foregone semiconductors (e.g., SiC, GaN, GaAs, Si, and so on). For example,

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Fig. 1 Number of research studies on Ga<sub>2</sub>O<sub>3</sub> as a function of time (data derived from Web of Science).

Ga<sub>2</sub>O<sub>3</sub> single wafers with large areas can be prepared by scalable and low-cost melt growth techniques. Moreover, its large bandgap ( $E_g$ ) ranges from 4.6 eV to 5.3 eV, and its breakdown field is up to 8 MV cm<sup>-1</sup>, which further improves its applications in high voltage devices, as shown in Fig. 2(a).<sup>6,7</sup> The relationship between the on-resistance and breakdown voltage of common semiconductors is shown in Fig. 2(b). Such log-log plots represent Baliga's figure of merit (BFOM) of semiconductors which is a typical FOM for the low-frequency unipolar vertical power switch. Generally, the high voltage and low on-resistance properties of semiconductors facilitate generation of less heat and help obtain a similarly ideal situation at high voltage for the switch-type power device.<sup>7</sup> Such characteristics are beneficial for developing efficient manufacturing processes and reducing the size and cost in the field of power switching devices. The ultra-wide bandgap semiconductor Ga<sub>2</sub>O<sub>3</sub> possesses a higher BFOM than the traditional semiconductor so that Ga<sub>2</sub>O<sub>3</sub> based devices provide more efficient power switching and energy savings than the devices based on

Si, GaAs, SiC, and GaN.<sup>8</sup> In addition, the large bandgap leads to its cut-off wavelength located in the deep ultraviolet region. The cut-off wavelength of Ga<sub>2</sub>O<sub>3</sub>-based photodetectors ranges from 250 nm to 280 nm, which meets the requirements of deep ultraviolet light (DUV) detection, as shown in Fig. 2(c).<sup>9</sup> Meanwhile, the photodetectors based on Ga<sub>2</sub>O<sub>3</sub> are insensitive to visible and infrared light, which improves the sensitivity of ultraviolet (UV) detection. In addition, the solar-blind photodetectors based on Ga<sub>2</sub>O<sub>3</sub> can also overcome the shortcomings of other semiconductor-based photodetectors, e.g. Al<sub>x</sub>Ga<sub>1-x</sub>N and Mg<sub>x</sub>Zn<sub>1-x</sub>O. That is, high temperatures are required when the Al component to be incorporated is high in photodetectors based on Al<sub>x</sub>Ga<sub>1-x</sub>N ( $T > 1350$  °C). The phase separation from wurtzite to the rock-salt structure occurs in photodetectors based on Mg<sub>x</sub>Zn<sub>1-x</sub>O when the Mg component is high.<sup>10-14</sup> Besides, Ga<sub>2</sub>O<sub>3</sub> has a relatively high density (6.44 g cm<sup>-3</sup>) and radiation resistance, as well as rapid scintillation and decay time constant of several nanoseconds, which makes it a promising candidate for nuclear radiation detection.<sup>15,16</sup> Therefore, the applications of Ga<sub>2</sub>O<sub>3</sub> are more and more extensive with the development of science and technology. Fig. 3 summarizes the frequently applied devices based on Ga<sub>2</sub>O<sub>3</sub>. The main application areas of Ga<sub>2</sub>O<sub>3</sub> are photoelectronic detection, power devices, and some other applications (e.g., radiation detection, flame detectors, gas sensors, memory devices, and photocatalysts). The successful applications of these areas are related to the unique properties of Ga<sub>2</sub>O<sub>3</sub> closely. To obtain high-performance devices based on Ga<sub>2</sub>O<sub>3</sub>, understanding the basic properties of Ga<sub>2</sub>O<sub>3</sub> is indispensable in the process of device preparation and application.

Ga<sub>2</sub>O<sub>3</sub> has six phases (*i.e.*, β-Ga<sub>2</sub>O<sub>3</sub>, ε-Ga<sub>2</sub>O<sub>3</sub>, α-Ga<sub>2</sub>O<sub>3</sub>, δ-Ga<sub>2</sub>O<sub>3</sub>, γ-Ga<sub>2</sub>O<sub>3</sub>, and κ-Ga<sub>2</sub>O<sub>3</sub>) and β-Ga<sub>2</sub>O<sub>3</sub> is the most stable phase under ambient conditions. That is, the rest of the phases can be transformed into β-Ga<sub>2</sub>O<sub>3</sub> under specific temperature, pressure, or other conditions. Therefore, most devices are based on β-Ga<sub>2</sub>O<sub>3</sub> up to now. Note that Ga<sub>2</sub>O<sub>3</sub> behaves as an insulator if it satisfies the stoichiometric ratio. However, the Ga<sub>2</sub>O<sub>3</sub> prepared in the experiments behaves as an electron-rich (*i.e.*, n-type) semiconductor instead of the so-called insulator. For example, intrinsic β-Ga<sub>2</sub>O<sub>3</sub> contains a certain electron concentration ( $n = 10^{17}$ – $10^{18}$  cm<sup>-3</sup>) and mobility ( $\mu < 200$  cm<sup>2</sup> V<sup>-1</sup> s<sup>-1</sup>). However, the electron concentration is low and the mobility is far from the theoretical value ( $\mu = 300$  cm<sup>2</sup> V<sup>-1</sup> s<sup>-1</sup>).<sup>5,17-19</sup> These cannot meet the criteria of high-performance devices. Besides, due to the unique Ga-O arrangement configuration, β-Ga<sub>2</sub>O<sub>3</sub> can be exfoliated to obtain low-dimensional Ga<sub>2</sub>O<sub>3</sub> which is considered to have potential applications in flexible electronic and optoelectronic devices.<sup>20-25</sup> However, freshly exfoliated low-dimensional Ga<sub>2</sub>O<sub>3</sub> is unstable and has no obvious quantum confinement effects, which will negatively affect the electronic performance and reliability of the devices. Therefore, it will hinder further applications based on low-dimensional Ga<sub>2</sub>O<sub>3</sub> greatly.<sup>26,27</sup> It has been found that the main reason for these unsatisfactory results is the defects in Ga<sub>2</sub>O<sub>3</sub>, e.g., vacancies, interstitial atoms, dangling bonds, and deep level defects, which are usually introduced in the preparation process. Therefore, it is very



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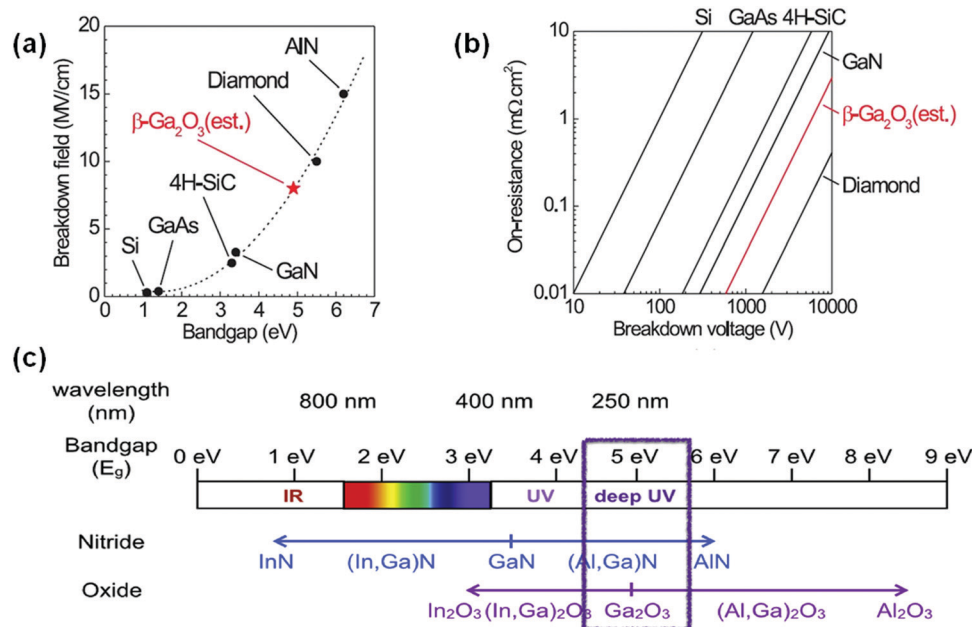


Fig. 2 (a) Relationship between the breakdown fields and the bandgaps of different generation semiconductors. Reproduced with permission.<sup>6</sup> Copyright 2012, American Institute of Physics Publishing. (b) Relationship between the breakdown voltages and switching resistances of different generation semiconductors. Reproduced with permission.<sup>235</sup> Copyright 2014, WILEY-VCH Verlag GmbH & Co. KGaA, Weinheim. (c) The bandgap and wavelength range of GaN and Ga<sub>2</sub>O<sub>3</sub> modulated by varying the alloy's composition. Reproduced with permission.<sup>377</sup> Copyright 2017, Elsevier Ltd.



Fig. 3 Schematic illustration of various device applications based on Ga<sub>2</sub>O<sub>3</sub>.

crucial to understand the mechanism of these defects and modulate the defects to design and obtain high-performance Ga<sub>2</sub>O<sub>3</sub> materials and devices. Doping engineering and passivation engineering are important methods to modulate the material properties of semiconductors. On the one hand, substituting host atoms with suitable impurity atoms can modulate the electronic properties of the doping systems, e.g., the electronic structure, carrier concentrations, and carrier mobility. On the

other hand, it has a certain influence on the defects. It has been discovered that passivating the surface dangling bonds is essential for achieving high stability and excellent electronic properties of low-dimensional Ga<sub>2</sub>O<sub>3</sub>. Meanwhile, other material properties (e.g., magnetic, luminescence, scintillation, and piezoelectric) can also be modulated by doping engineering for application in other areas.

Herein, we summarize the recent progress on the effects of impurities and defects on the properties of Ga<sub>2</sub>O<sub>3</sub>. Because  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> is the most stable structure under ambient conditions, it is the focus of the present review, supplemented by the situations of low-dimensional Ga<sub>2</sub>O<sub>3</sub> and other metastable Ga<sub>2</sub>O<sub>3</sub>. The basic properties of Ga<sub>2</sub>O<sub>3</sub> are introduced firstly, and then other properties (e.g., electronic, magnetic, luminescence, scintillation, and piezoelectric) based on the host  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> modulated by impurities and defects are described in depth. Finally, the issues to be solved in this area and prospects in the future are given.

## II. Basic properties

### 1. Polymorphs of Ga<sub>2</sub>O<sub>3</sub>

There are five commonly identified polymorphs of Ga<sub>2</sub>O<sub>3</sub> including hexagonal phase ( $\alpha$ -Ga<sub>2</sub>O<sub>3</sub>), monoclinic phase ( $\beta$ -Ga<sub>2</sub>O<sub>3</sub>), cubic defective spinel phase ( $\gamma$ -Ga<sub>2</sub>O<sub>3</sub>), cubic bixbyite phase ( $\delta$ -Ga<sub>2</sub>O<sub>3</sub>), and hexagonal wurtzite phase ( $\epsilon$ -Ga<sub>2</sub>O<sub>3</sub>).<sup>28–30</sup> The formation energy coupled with the thermodynamic stability of these five polymorphs is ranked as  $\beta < \epsilon < \alpha < \delta < \gamma$ .<sup>5</sup> In recent years, another new phase, the metastable  $\kappa$ -Ga<sub>2</sub>O<sub>3</sub>, is also synthesized on sapphire.<sup>31–33</sup> Note that any other metastable phases can be converted into  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> at high



Fig. 4 Schematic diagram of six phase structures and their phase transition relationships in  $\text{Ga}_2\text{O}_3$  ( $\alpha$ - $\text{Ga}_2\text{O}_3$ ,  $\beta$ - $\text{Ga}_2\text{O}_3$ ,  $\delta$ - $\text{Ga}_2\text{O}_3$ ,  $\gamma$ - $\text{Ga}_2\text{O}_3$ ,  $\varepsilon$ - $\text{Ga}_2\text{O}_3$ , and  $\kappa$ - $\text{Ga}_2\text{O}_3$ ). Reproduced with permission.<sup>4</sup> Copyright 2019, Elsevier Ltd.

temperatures (400–700 °C) under special conditions, as shown in Fig. 4 schematically. Only  $\beta$ - $\text{Ga}_2\text{O}_3$  can be grown as bulk crystals from melts, fluxes, or gas phases, while other phases can be obtained as thin films or thick layers.<sup>34</sup> Theoretically, the opinion that these metastable phases could not be transformed from  $\beta$ - $\text{Ga}_2\text{O}_3$  has been accepted for a long time. However, a recent study discovered that  $\beta$ - $\text{Ga}_2\text{O}_3$  could convert into  $\alpha$ - $\text{Ga}_2\text{O}_3$  under high pressure by shock compression experiments.<sup>35</sup> The phase transition condition between  $\alpha$ - $\text{Ga}_2\text{O}_3$  and  $\beta$ - $\text{Ga}_2\text{O}_3$  was estimated to be 2.0–3.0 GPa, 1200–1500 K. In addition, the phase transition was also observed at high temperature and pressure, *i.e.* 19.2 GPa<sup>36</sup> and 20–22 GPa<sup>37</sup> or 21 GPa, 1873 K.<sup>38</sup> It was reported that phase transitions initialized at relatively low pressures and then expanded to higher pressures, *e.g.*, from about 6 GPa<sup>39</sup> to 40 GPa,<sup>40</sup> or from

13.6–16.4 GPa to 39.2 GPa.<sup>41</sup> Note that the temperature increases the regrowth of  $\beta$ - $\text{Ga}_2\text{O}_3$ ; thus complete phase transition into pure  $\alpha$ - $\text{Ga}_2\text{O}_3$  is almost impossible. Therefore, mixtures of the two phases are usually prepared under high pressure experimentally. The structure and properties of these phases of  $\text{Ga}_2\text{O}_3$  will be discussed in detail in the subsequent sections. The intrinsic structural parameters and fundamental physical constants of these  $\text{Ga}_2\text{O}_3$  polymorphs are summarized in Table 1.

**$\beta$ - $\text{Ga}_2\text{O}_3$ .** It is a typical monoclinic structure with the space group  $C2/m$  whose lattice constants are  $a = 12.21 \text{ \AA}$ ,  $b = 3.04 \text{ \AA}$ ,  $c = 5.67 \text{ \AA}$ ,  $\alpha = \gamma = 90^\circ$ ,  $\beta = 103.8^\circ$ .<sup>42,43</sup>  $\beta$ - $\text{Ga}_2\text{O}_3$  is a kind of anion-dense accumulation structure. The  $b$ -axis of the centrosymmetric unit cell is the two-fold rotational axis in the  $\beta$ - $\text{Ga}_2\text{O}_3$  cell. Each  $\beta$ - $\text{Ga}_2\text{O}_3$  unit cell has two inequivalent Ga sites

Table 1 Crystal structures, lattice parameters, bandgaps, and electron effective masses of the  $\text{Ga}_2\text{O}_3$  family

Phase	Structure	Space group	Lattice parameters	Bandgap (eV)	Electron effective mass ( $m_e$ )	Ref.
$\alpha$	Hexagonal	$R\bar{3}c$	$a = b = 4.98 \text{ \AA}$ , $c = 13.43 \text{ \AA}$ , $\alpha = \beta = 90^\circ$ , $\gamma = 120^\circ$	5.2–5.3	0.276 $m_0$	80 and 81
$\beta$	Monoclinic	$C2/m$	$a = 12.23 \text{ \AA}$ , $b = 3.04 \text{ \AA}$ , $c = 5.80 \text{ \AA}$ , $\alpha = \gamma = 90^\circ$ , $\beta = 103.8^\circ$	$E_{g(\text{indirect})} = 4.69 \text{ eV}$ $E_{g(\text{direct})} = 4.66 \text{ eV}$	0.27 $m_0$ –0.34 $m_0$	101–103
$\Gamma$	Cubic	$Fd\bar{3}m$	$a = b = c = 8.24 \text{ \AA}$ , $\alpha = \beta = \gamma = 90^\circ$	5.0(direct), 4.4(indirect)	—	45
$\delta$	Cubic	$Ia\bar{3}$	$a = b = c = 9.52 \text{ \AA}$ , $\alpha = \beta = \gamma = 90^\circ$	—	—	45
$\varepsilon$	Hexagonal	$P6_3mc$	$a = b = 2.90 \text{ \AA}$ , $c = 9.26 \text{ \AA}$ , $\alpha = \beta = 90^\circ$ , $\gamma = 120^\circ$	4.9–5.0	0.24 $m_0$	90 and 93
$\kappa$	Orthorhombic	$Pna2_1$	$a = 5.05 \text{ \AA}$ , $b = 8.70 \text{ \AA}$ , $c = 9.28 \text{ \AA}$ , $\alpha = \beta = \gamma = 90^\circ$	4.62	—	31



(Ga<sub>(1)</sub> and Ga<sub>(2)</sub>) and three inequivalent O sites (O<sub>(1)</sub>, O<sub>(2)</sub>, and O<sub>(3)</sub>). Half of the Ga atoms are at Ga<sub>(1)</sub> sites, forming a slightly distorted tetrahedron with four O ions. The other half of the Ga atoms are located at Ga<sub>(2)</sub> sites, forming a highly distorted octahedron with six O ions. Each O<sub>(1)</sub> is threefold-coordinated, located at the intersection point of two octahedra and one tetrahedron. Each O<sub>(2)</sub> is threefold-coordinated, shared by an octahedron and two tetrahedra. Each O<sub>(3)</sub> is fourfold-coordinated, located at the corner of three octahedra and one tetrahedron.<sup>44–48</sup> In the bulk β-Ga<sub>2</sub>O<sub>3</sub>, the Ga–O bond lengths are Ga<sub>(1)</sub>–O<sub>(1)</sub> = 1.853 Å, Ga<sub>(1)</sub>–O<sub>(2)</sub> = 1.833 Å, Ga<sub>(1)</sub>–O<sub>(3)</sub> = 1.803 Å, Ga<sub>(2)</sub>–O<sub>(1)</sub> = 2.077 Å, Ga<sub>(2)</sub>–O<sub>(2)</sub> = 1.940 Å, and Ga<sub>(2)</sub>–O<sub>(3)</sub> = 1.978 Å. The structure and lattice parameters of β-Ga<sub>2</sub>O<sub>3</sub> are shown in detail in Fig. 5.<sup>48</sup> These structural characteristics lead to low symmetry for β-Ga<sub>2</sub>O<sub>3</sub>, which leads to significant anisotropy in structural, optical, and electronic properties. Besides, β-Ga<sub>2</sub>O<sub>3</sub> can be grown by the low-cost melt methods, e.g., Czochralski method (CZ method),<sup>49,50</sup> edge-defined film-fed growth method (EFG method),<sup>51</sup> floating-zone method (FZ method),<sup>52</sup> and vertical Bridgman method.<sup>53</sup> Meanwhile, the β-Ga<sub>2</sub>O<sub>3</sub> film can also be realized by epitaxial methods, e.g., metal–organic chemical vapor deposition (MOCVD),<sup>54–58</sup> mist-chemical vapor deposition (mist-CVD),<sup>59</sup> halide vapor phase epitaxy (HVPE),<sup>60–62</sup> laser molecular beam epitaxy (LMBE),<sup>63,64</sup> pulsed laser deposition (PLD)<sup>65–69</sup> and magnetron sputtering.<sup>70–73</sup> Compared with the expensive costs of crystal growth of other wide bandgap semiconductors (e.g., GaN and SiC) and irrealizable wafer of other phases, β-Ga<sub>2</sub>O<sub>3</sub> has advantages in crystal growth and large-scale applications. Therefore, state-of-the-art microelectronic and optoelectronic devices are almost based on β-Ga<sub>2</sub>O<sub>3</sub> in Ga<sub>2</sub>O<sub>3</sub>'s family.

**α-Ga<sub>2</sub>O<sub>3</sub>.** The formation of metastable Ga<sub>2</sub>O<sub>3</sub> depends on the lattice structure of the substrate and the growth temperature. Since the metastable phase α-Ga<sub>2</sub>O<sub>3</sub> possesses a similar structure and little lattice mismatches to sapphire, the high-quality metastable phase α-Ga<sub>2</sub>O<sub>3</sub> can be deposited on sapphire substrates by heteroepitaxial methods, e.g., pulsed laser deposition (PLD),<sup>74</sup>

halide vapor phase epitaxy (HVPE),<sup>75</sup> metal–organic chemical vapor deposition (MOCVD),<sup>76</sup> low-temperature atomic layer deposition (ALD),<sup>77</sup> and mist-CVD.<sup>78,79</sup> α-Ga<sub>2</sub>O<sub>3</sub> is a typical hexagonal crystal with the space group *R*3̄*c*, whose lattice constants are *a* = *b* = 4.98 Å, *c* = 13.43 Å, α = γ = 90°, β = 120°.<sup>80,81</sup> Compared with β-Ga<sub>2</sub>O<sub>3</sub>, α-Ga<sub>2</sub>O<sub>3</sub> has a larger bandgap (*E*<sub>g</sub> = 5.2–5.3 eV). Meanwhile, α-Ga<sub>2</sub>O<sub>3</sub> can form tunable component alloys with In<sub>2</sub>O<sub>3</sub> and Al<sub>2</sub>O<sub>3</sub>, for example, α-(In<sub>*x*</sub>Ga<sub>1–*x*</sub>)<sub>2</sub>O<sub>3</sub> and α-(Al<sub>*x*</sub>Ga<sub>1–*x*</sub>)<sub>2</sub>O<sub>3</sub>. Note that the α-(Al<sub>*x*</sub>Ga<sub>1–*x*</sub>)<sub>2</sub>O<sub>3</sub> alloy will not undergo phase transition when the Al component (*x*) varies in the range of 0–100%.<sup>82</sup> Besides, the carrier concentrations in α-Ga<sub>2</sub>O<sub>3</sub> can be modulated effortlessly. Thus, α-Ga<sub>2</sub>O<sub>3</sub> has remarkable potential applications. In recent years, Sn or Si doped α-Ga<sub>2</sub>O<sub>3</sub> is applied in the Schottky barrier diode (SBD) and metal–semiconductor field-effect transistors (MESFETs). For example, Shiojima *et al.* investigated the effects of annealing temperature on the interface contact properties of the doped α-Ga<sub>2</sub>O<sub>3</sub> SBD.<sup>83</sup> They found that both forward and reverse currents increased with 400 °C annealing due to thermal degradation and different electrode materials. Dang *et al.* proposed a cost-effective strategy to realize high-performance Sn doped α-Ga<sub>2</sub>O<sub>3</sub> MESFETs.<sup>84</sup> By optimizing the dimension of MESFETs, the on/off ratio could reach up to 2 × 10<sup>7</sup>, and the rectification ratio and reverse breakdown voltage were 6 × 10<sup>6</sup> and ~20 V, respectively. Compared with β-Ga<sub>2</sub>O<sub>3</sub>-based power devices, the performance of α-Ga<sub>2</sub>O<sub>3</sub>-based power devices has been improved summarily.

**γ-Ga<sub>2</sub>O<sub>3</sub>.** The space group of γ-Ga<sub>2</sub>O<sub>3</sub> is *Fd*3̄*m*. Its lattice parameters are *a* = *b* = *c* = 8.24 Å, α = β = γ = 90°.<sup>45</sup> It has a crystal structure similar to that of an ideal spinel (e.g., MgAl<sub>2</sub>O<sub>4</sub>). Different from the ideal spinel structure, Ga atoms in γ-Ga<sub>2</sub>O<sub>3</sub> only occupy the octahedral sites. γ-Ga<sub>2</sub>O<sub>3</sub> can be epitaxially grown on sapphire and spinel substrates by mist-CVD,<sup>85</sup> molecular beam epitaxy (MBE),<sup>86</sup> and PLD.<sup>87–89</sup>

**δ-Ga<sub>2</sub>O<sub>3</sub>.** It is a metastable phase with a body-centered cubic structure and the space group is *Ia*3. It is isomorphous with some bixbyite crystals (e.g., In<sub>2</sub>O<sub>3</sub>, and Mn<sub>2</sub>O<sub>3</sub>).<sup>4,90,91</sup> The lattice parameters of δ-Ga<sub>2</sub>O<sub>3</sub> are *a* = *b* = *c* = 9.52 Å, α = β = γ = 90°.<sup>45</sup> Although Sharma *et al.* synthesized nano-structured δ-Ga<sub>2</sub>O<sub>3</sub> by the chemical precipitation method, there were still some β-Ga<sub>2</sub>O<sub>3</sub> components in the nano-film, which made it impure.<sup>92</sup> Therefore, a relevant in-depth research study is still needed to prepare pure δ-Ga<sub>2</sub>O<sub>3</sub> films.

**ε-Ga<sub>2</sub>O<sub>3</sub>.** Hexagonal ε-Ga<sub>2</sub>O<sub>3</sub> is prepared by heteroepitaxial growth normally. The lattice parameters of ε-Ga<sub>2</sub>O<sub>3</sub> are *a* = *b* = 2.90 Å, *c* = 9.26 Å, α = β = 90°, γ = 120°.<sup>90,93</sup> Note that hexagonal ε-Ga<sub>2</sub>O<sub>3</sub> has a larger spontaneous polarization (*P*<sub>(ε-Ga<sub>2</sub>O<sub>3</sub>)</sub> = 24.44 μC cm<sup>–2</sup>) compared with GaN.<sup>33,94</sup> Inspired by the previous work on the Al<sub>*x*</sub>Ga<sub>1–*x*</sub>N/GaN heterojunctions, high-density two-dimensional electron gas (2DEG) can be formed at the ε-(Al<sub>*x*</sub>Ga<sub>1–*x*</sub>)<sub>2</sub>O<sub>3</sub>/ε-Ga<sub>2</sub>O<sub>3</sub> interface without any intentional doping. It has been discovered that the 2DEG charge densities at the ε-(Al<sub>*x*</sub>Ga<sub>1–*x*</sub>)<sub>2</sub>O<sub>3</sub>/ε-Ga<sub>2</sub>O<sub>3</sub> interface can reach up to 1.4 × 10<sup>14</sup> cm<sup>–2</sup> by varying the barrier type and ε-AlGaO<sub>3</sub> thickness.<sup>95</sup> Meanwhile, charge contrast ratios over 1500 can be realized by the thick ε-Ga<sub>2</sub>O<sub>3</sub> cap layer and thin ε-AlGaO<sub>3</sub> layers.

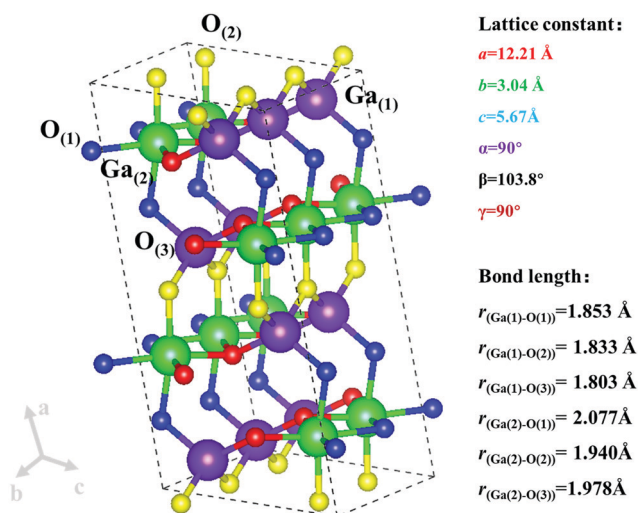


Fig. 5 Schematic diagram of the structure of the unit cell of β-Ga<sub>2</sub>O<sub>3</sub>.

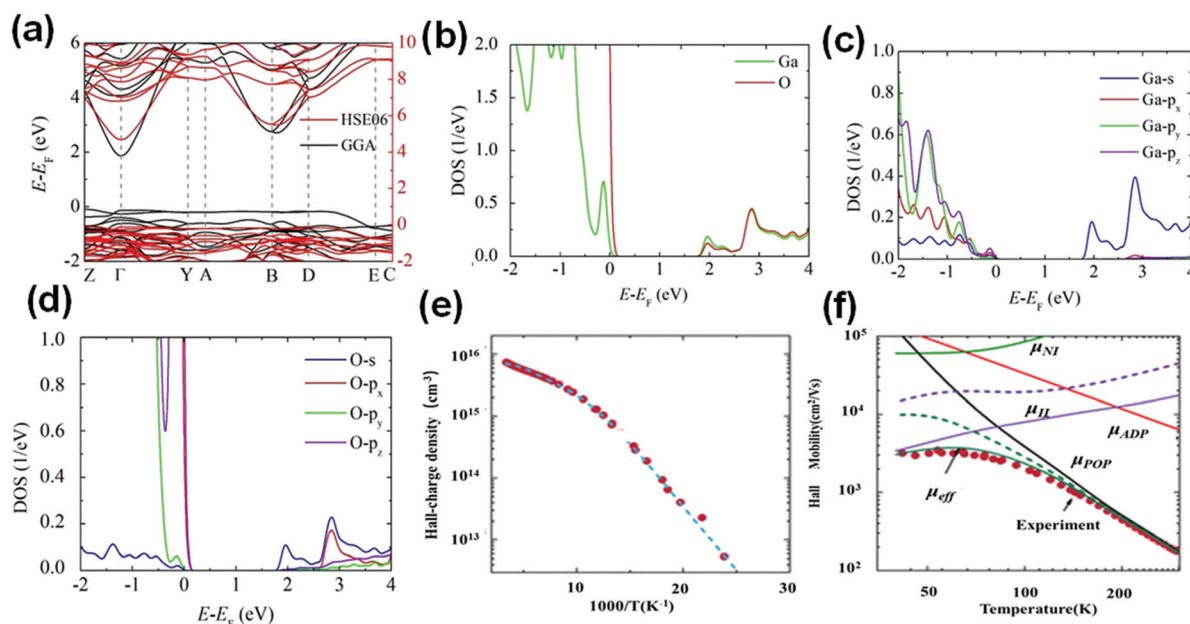
This phenomenon reveals its potential applications in modulation-doped field effect transistors (MODFETs), non-volatile memory, and neuromorphic applications.<sup>95,96</sup>

**$\kappa$ -Ga<sub>2</sub>O<sub>3</sub>.** Orthorhombic  $\kappa$ -Ga<sub>2</sub>O<sub>3</sub> has attracted scholars in recent years.  $\kappa$ -Ga<sub>2</sub>O<sub>3</sub> was considered to be the orthorhombic  $\varepsilon$ -Ga<sub>2</sub>O<sub>3</sub> incorrectly due to their similar crystal structure in the previous research. In 2017, Cora *et al.* investigated the real structure of the Ga<sub>2</sub>O<sub>3</sub> film deposited by MOVPE on the  $\alpha$ -Al<sub>2</sub>O<sub>3</sub> substrate in detail.<sup>31</sup> They discovered that the layer had a columnar structure perpendicular to the interface and its origin was related to the formation of small domains. By transmission electron microscopy (TEM), it was observed that O atoms of the Ga<sub>2</sub>O<sub>3</sub> layer formed a densely packed structure along the *c*-axis, while Ga atoms and these O atoms formed tetrahedral and octahedral structures, respectively. Meanwhile, these two different geometric structures formed two types of polyhedral layers. The oxygen positions are similar with 4H-SiC (ABAC) type close-packed stacking. Furthermore, the detailed TEM results revealed that the microstructure was ordered in 5–10 nm large domains and each domain was found to belong to the orthorhombic (*Pna2*<sub>1</sub>) structure, which was regarded as the structure of  $\kappa$ -Ga<sub>2</sub>O<sub>3</sub>. This phenomenon was different from that discovered in  $\varepsilon$ -Ga<sub>2</sub>O<sub>3</sub>, so this work laid a foundation for in-depth understanding of the correct structure of  $\kappa$ -Ga<sub>2</sub>O<sub>3</sub>. The lattice parameters of  $\kappa$ -Ga<sub>2</sub>O<sub>3</sub> are *a* = 5.05 Å, *b* = 8.70 Å, *c* = 9.28 Å,  $\alpha = \beta = \gamma = 90^\circ$ .<sup>31</sup> Furthermore, it has been discovered that  $\kappa$ -Ga<sub>2</sub>O<sub>3</sub> can be prepared by pulsed-laser deposition (PLD),<sup>97</sup> metal-organic vapor phase epitaxy (MOVPE),<sup>31,76</sup> and HVPE.<sup>98,99</sup> Note that recent research discovered that  $\kappa$ -Ga<sub>2</sub>O<sub>3</sub> was expected to exhibit a larger spontaneous polarization

( $P_{(\kappa\text{-Ga}_2\text{O}_3)} = 26.39 \mu\text{C cm}^{-2}$ ) along the *c*-axis compared with GaN and  $\varepsilon$ -Ga<sub>2</sub>O<sub>3</sub>.  $\kappa$ -Ga<sub>2</sub>O<sub>3</sub> with expected spontaneous polarization and piezoelectric effects will be applied in high-performance power devices to form two-dimensional electron gas at the hetero-interface. Such features are expected to further improve the performance of HEMTs.

## 2. Electronic properties of $\beta$ -Ga<sub>2</sub>O<sub>3</sub>

In terms of the electronic properties of  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>, band structure, density of states (DOS) and transport properties are the focus, because they are related to device performance closely. The electronic structures of  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> calculated by density functional theory (DFT) are illustrated in Fig. 6(a). Here, the GGA functional and the HSE06 hybrid functional are applied to obtain the band structure of  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>, respectively. Note that the bandgap derived from HSE06 is closer to the experimental bandgap, while the bandgap obtained from GGA is underestimated because the exchange–correlation terms of the two functionals are different. As shown in Fig. 6(a), the conduction band minimum (CBM) and the valence band maximum (VBM) are located at the  $\Gamma$  and *M* points, respectively, which leads to the indirect bandgap in  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>. On the other hand, in most previous publications,  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> exhibits the direct bandgap in which both CBM and VBM are located at the  $\Gamma$  point.<sup>59,100</sup> Since the difference of the VBM between the *M* and  $\Gamma$  points is less than 100 meV, the measured indirect bandgap ( $E_{\text{g(indirect)}} = 4.69 \text{ eV}$ ) is a little larger than the measured direct bandgap ( $E_{\text{g(direct)}} = 4.66 \text{ eV}$ ). Furthermore, it can be observed that the CBM is mainly contributed by the Ga 4s orbital in the DOS diagram (see Fig. 6(b and c)), and the dispersive degree is large.



**Fig. 6** (a) Band structure of bulk  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> obtained by the HSE06 functional (red solid line) and GGA functional (black solid line). (b–d) Partial density of states (PDOS) of bulk  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> obtained with permission.<sup>21</sup> Copyright 2018, American Chemical Society. (e) Measured Hall-charge density as a function of 1000/*T* (the dashed line presents the fitting of the charge density calculated based on the charge neutrality equation). (f) Experimental and calculated dependence of the Hall mobility in different scattering mechanisms on the temperature. Reproduced with permission.<sup>378</sup> Copyright 2019, American Institute of Physics Publishing.

The electron effective mass of  $\beta\text{-Ga}_2\text{O}_3$  is small, which is in the range of  $0.27m_0$ – $0.34m_0$  obtained by first-principles calculations.<sup>101–103</sup> The band structure and conclusions are in good agreement with the experimental results.<sup>104–106</sup> Note that both theoretical and experimental valence bands of  $\beta\text{-Ga}_2\text{O}_3$  show weak band dispersion. As shown in Fig. 6(b–d), combined with the relevant partial density of states (PDOS), the valence band maximum is mainly composed of O 2p orbitals, and the dispersive degree is small, thus it is flat. Although the VBM of  $\beta\text{-Ga}_2\text{O}_3$  is mainly composed of p orbitals, the contribution of each p orbital component is not equal. The VBM is mainly contributed by the  $2p_x$  and  $2p_z$  orbitals of O atoms. In general, the p shell contains three p orbitals, that is,  $p_x$ ,  $p_y$ , and  $p_z$ , which are dumbbell-shaped but in different stretching directions. Therefore, the three different components of p orbitals show anisotropy. The characteristics of orbital contributions connected with the band structure reveal the anisotropy of electronic properties from another perspective. Similar experimental and theoretical methods have also measured the bandgaps ( $E_g$ ) and electron effective masses of other phases, as listed in Table 1.

As mentioned above, the electron clouds of the Ga 4s orbital are spherically symmetric so that the band dispersion of the CBM in the Brillouin zone is symmetrical. In other words, the electron effective masses of  $\beta\text{-Ga}_2\text{O}_3$  obtained from the CBM exhibit the isotropic character. Note that the electron clouds of the s orbital have a large radius, which results in the large overlapping electronic conduction path. It is thought that the mean free path of electrons in  $\beta\text{-Ga}_2\text{O}_3$  is greater than the chemical bond length of  $\beta\text{-Ga}_2\text{O}_3$ . As a result, the small electron effective masses of  $\beta\text{-Ga}_2\text{O}_3$  suggest the high electron mobility in  $\beta\text{-Ga}_2\text{O}_3$ .<sup>4</sup> However, such electron mobility is far lower than that of other wide bandgap semiconductors, such as 4H-SiC ( $\sim 1000 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$ ) and GaN ( $\sim 1200 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$ ).<sup>5,107</sup> Moreover, the electron mobility of  $\beta\text{-Ga}_2\text{O}_3$  ( $\mu_{\text{experiment}} = 20\text{--}170 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$ ) is much lower than the theoretical expectation ( $\mu_{\text{theory}} = 300 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$ ) in the experiments.<sup>17,18,108–111</sup> On the one hand, the low mobility is attributed to a large number of internal defects in  $\beta\text{-Ga}_2\text{O}_3$ . Therefore, the modulations of defects are very urgent and vital to realizing high-performance  $\beta\text{-Ga}_2\text{O}_3$  based devices. On the other hand, the reasons are attributed to the different scattering mechanisms of electrons within different temperature ranges and the complex vibration modes of phonons in  $\beta\text{-Ga}_2\text{O}_3$ . It has been discovered by exploring of the influence of temperature on the mobility of  $\beta\text{-Ga}_2\text{O}_3$  that  $\beta\text{-Ga}_2\text{O}_3$  is affected by strong electron–phonon interaction (EPI) effects. Unlike the traditional notions of carrier transport in Si and GaAs, the low symmetry  $\beta\text{-Ga}_2\text{O}_3$  crystal contains a variety of phonon modes generally and the carrier transport mechanism is quite different. The lattice vibration will disturb the potential field of the periodic crystal with the variation of temperature in the low symmetry crystal. Thus, the phonon vibration modes will combine with electron motion. This results in that the mobility of electrons is affected by electron–phonon interaction effects. This EPI effect plays a pivotal role in controlling the mobility of intrinsic semiconductors, and the interaction is a long-range Coulomb interaction essentially.

Unfortunately, this phenomenon cannot be avoided in a semiconductor with a low symmetry structure. Among them, the polarized optical phonon (POP) scattering which is one of the representatives of EPI effects has been investigated a lot because it is an important scattering mechanism at medium temperature (e.g., room temperature). Besides, as shown in Fig. 6(e and f), other mechanisms also affect the carrier mobility in  $\beta\text{-Ga}_2\text{O}_3$ , e.g., ionized ( $\mu_{\text{II}}$ ) scattering, neutral impurity ( $\mu_{\text{NI}}$ ) scattering, and acoustic deformation potential scattering ( $\mu_{\text{ADP}}$ ). Through theoretical analysis, the values of the Hall mobility at different temperatures after being affected by these scattering mechanisms are listed in detail.

In the bulk  $\beta\text{-Ga}_2\text{O}_3$ , the long-range interaction controls the intrinsic electron transport. In this condition, the same dipole moment is produced by transverse optical (TO) and longitudinal optical (LO) vibrational mode splitting at the long-wavelength limit. The LO modes gain slightly higher energy than their TO counterparts. The electron and LO modes are coupled in the long-range EPI effect. This coupling is polar and the scattering resulting from this coupling is regarded as POP scattering. At low temperatures, the POP scattering effect in  $\beta\text{-Ga}_2\text{O}_3$  is weak and the impurity scattering plays a dominant role. As the temperature increases gradually, the electrons' energy also increases and the ionized impurity scattering decreases, which increases the bulk electron mobility. In addition, POP scattering attempts to dominate with a further increase in temperature. The rate of POP scattering increases with increasing temperature due to the increase in the Bose occupancy number. Therefore, the bulk electron mobility begins to drop. As mentioned earlier, the bulk mobility in  $\beta\text{-Ga}_2\text{O}_3$  at moderate temperature is also affected by other scattering mechanisms. However, according to the Fermi-Golden rule, the effects of these scatterings on bulk electron mobility are small compared with that of POP scattering. They can be ignored when investigating the transport problems in  $\beta\text{-Ga}_2\text{O}_3$  generally. It is discovered that the POP scattering effect is the main culprit in reducing the bulk electron mobility in bulk  $\beta\text{-Ga}_2\text{O}_3$  in the range of moderate temperatures. To suppress the POP scattering, one possible solution is to screen the POP modes. This strategy needs higher carrier concentrations in the bulk  $\beta\text{-Ga}_2\text{O}_3$ .

Unfortunately, the carrier concentrations in intrinsic  $\beta\text{-Ga}_2\text{O}_3$  are so low that the POP scattering is unable to be suppressed. Low carrier concentrations and mobility result in low electrical conductivity ( $\sigma$ ) so that it limits the device performance of  $\beta\text{-Ga}_2\text{O}_3$ . Doping is an available strategy to tune the properties of semiconductors. In general, substitution doping with external atoms different from host valence electrons will modulate the properties of semiconductors. In  $\beta\text{-Ga}_2\text{O}_3$ , the incorporation of some electron-rich metals (e.g., Sn, Si) can increase the carrier concentrations by orders of magnitude. Nevertheless, electron mobility still fails to reach the theoretical value (less than half of the theoretical value).<sup>112</sup> To obtain electrons with high mobility, the electron transport path needs to be optimized to satisfy the features of less scattering, and the two-dimensional electron gas (2DEG) matches these conditions. Therefore, the device performance can be improved by obtaining

two-dimensional electron gas to improve carrier mobility. It has been discovered that two-dimensional electron gas with high mobility can be formed by modulation doping at the  $(\text{Al}_x\text{Ga}_{1-x})_2\text{O}_3/\text{Ga}_2\text{O}_3$  heterojunction interface. Therefore, the mobility of 2DEG ( $>100 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$ ,  $\mu_{\text{max}} = 1000 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$ ) will be higher than that in the bulk through reasonable modulated doping and band matching of the heterojunction interface; then electrons with high mobility are expected to be realized in  $\text{Ga}_2\text{O}_3$ .<sup>18,110,113,114</sup>

### 3. Absorption and transmittance properties

As an ultra-wide bandgap semiconductor,  $\beta\text{-Ga}_2\text{O}_3$  has high transmittance and low absorption in the visible and near-infrared regions of the solar spectrum, and hence it can be applied in transparent conductive electrodes in some areas.<sup>115,116</sup> Meanwhile, the absorption cutoff edge and the maximum absorption peak are located in the ultraviolet region, and it has strong absorption in the solar-blind ultraviolet region. It is noted by polarized optical absorption and reflectance measurements that the light absorption of  $\beta\text{-Ga}_2\text{O}_3$  in three different directions of [100], [010], and [001] is also different, as shown in Fig. 7(a), suggesting anisotropy in the optical properties of  $\beta\text{-Ga}_2\text{O}_3$ . Although the absorption situations are different in the three different directions, the absorption intensity is weaker in the low-energy region and greater in the high-energy region. According to the absorption coefficient curve derived from the Tauc plot method, the optical bandgaps of  $\beta\text{-Ga}_2\text{O}_3$  are different in three different directions. Fig. 7(a) shows that the bandgap along the [010] orientation is the largest ( $E_{\text{g}[010]} = 4.850 \text{ eV}$ ), while the optical bandgap along

the other two directions ([100] and [001]) is 4.585 eV and 4.560 eV, respectively. Onuma *et al.* applied a 300 W Xe lamp to measure the optical absorption and transmittance at room temperature.<sup>117</sup> In addition to the anisotropic light absorption, the transmittance of  $\beta\text{-Ga}_2\text{O}_3$  in different directions was also investigated (see Fig. 7(b)). The transmittance of  $E\parallel b$  orientation is higher than that of  $E\parallel a$  and unpolarized orientation. Furthermore, they revealed the absorption and transmittance mechanism by using experimental results coupled with theoretical calculations, as shown in Fig. 7(c). Such anisotropic optical absorption and transmittance can be explained by the inconsistent band-to-band transition. Each primitive cell contains the following bands, called  $\Gamma_1^+$ ,  $\Gamma_2^+$ ,  $\Gamma_1^-$ , and  $\Gamma_2^+$  bands. The CBM is isotropic and is expressed as the  $\Gamma_1^+$  band. Except for the transitions from the  $\Gamma_1^+$  and  $\Gamma_2^+$  bands to the  $\Gamma_1^+$  band of the CBM which are dipole forbidden, the other band-to-band transitions are dipole allowed. Therefore, the transitions from the rest of the different bands of the VBM to the  $\Gamma_1^+$  band of the CBM represent optical properties in different directions.<sup>46,117–119</sup> This explains the anisotropy in the optical properties of  $\beta\text{-Ga}_2\text{O}_3$  reasonably.

### 4. Thermal and mechanical properties

Although  $\beta\text{-Ga}_2\text{O}_3$  has many excellent properties that have attracted scholars, there are still many troublesome problems which need to be overcome. Thermal conductivity ( $\kappa$ ) is an important parameter that severely affects the performance and reliability of devices including both power devices and optoelectronic devices. There are several methods to obtain the thermal conductivity of  $\beta\text{-Ga}_2\text{O}_3$ . The theoretical method may

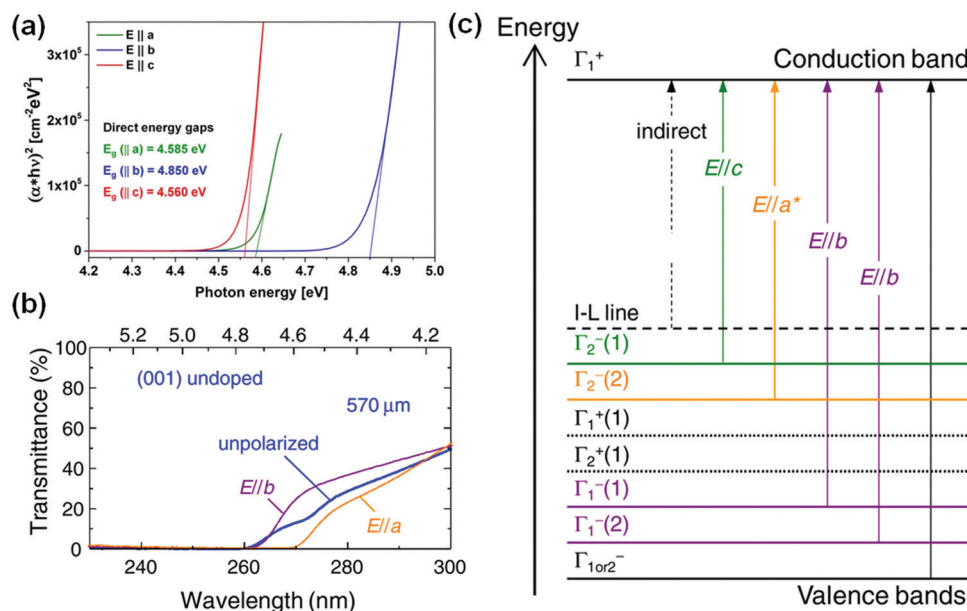


Fig. 7 (a) Polarization-dependent absorption edge of bulk  $\beta\text{-Ga}_2\text{O}_3$  crystal samples obtained by the Czochralski method. Reproduced with permission.<sup>42</sup> Copyright 2018, IOP Publishing Ltd. (b) Unpolarized (blue solid line) and polarized (purple and orange solid lines) transmittance spectra of the (001) undoped  $\beta\text{-Ga}_2\text{O}_3$  substrate at room temperature. (c) Irreducible representations and rough transition process of the band structure in  $\beta\text{-Ga}_2\text{O}_3$ . The horizontal solid and dotted lines represent the valence bands for the dipole allowed and forbidden transitions at  $\Gamma$ , respectively. The vertical solid lines represent the rough transition process. Reproduced with permission.<sup>117</sup> Copyright 2015, The Japan Society of Applied Physics.



involve independent first-principles calculations or could be coupled with machine learning.<sup>120</sup> The experimental methods are the  $3\omega$  method and the time domain thermo-reflectance (TDTR) method.<sup>121,122</sup> Due to the continuous optimizations and updates of calculation methods, the theoretical thermal conductivity (e.g.,  $\kappa_{[010]} = 20.00 \text{ W m}^{-1} \text{ K}^{-1}$ ,<sup>123</sup>  $21.54 \text{ W m}^{-1} \text{ K}^{-1}$ <sup>124</sup>) has been very close to the experimental value (e.g.,  $\kappa_{[010]} = 21.00 \text{ W m}^{-1} \text{ K}^{-1}$ <sup>125</sup>). Therefore, the scholars use theoretical calculations to predict and then evaluate the thermal properties rather than complex experiments. Note that the thermal conductivity of  $\beta\text{-Ga}_2\text{O}_3$  is lower than that of some semiconductors commonly applied up to now, e.g.  $\kappa_{\text{GaN}} = 240.00 \text{ W m}^{-1} \text{ K}^{-1}$ ,<sup>126-128</sup>  $\kappa_{\text{Si}} = 140.00 \text{ W m}^{-1} \text{ K}^{-1}$ ,<sup>129</sup> and  $\kappa_{\text{SiC}} = 350.00 \text{ W m}^{-1} \text{ K}^{-1}$ .<sup>129</sup> The low thermal conductivity of  $\beta\text{-Ga}_2\text{O}_3$  needs more in-depth research on the internal mechanism, which should be noticed in device

applications. Galazka *et al.* measured the thermal conductivity of  $\beta\text{-Ga}_2\text{O}_3$  along the  $[010]$  direction by applying the laser flash diffusivity method, where the thermal conductivity decreased with increasing temperature in the range of 20–1200 °C.<sup>125</sup> They found that the point defect scattering played a major role in the thermal conductivity at low temperature, while the phonon–phonon Umklapp scattering gradually dominated at high temperatures (above 150 K). Note that the thermal conductivity of  $\beta\text{-Ga}_2\text{O}_3$  is anisotropic due to the low symmetry structure. Guo *et al.* investigated the four different orientations in the  $\beta\text{-Ga}_2\text{O}_3$  bulk by the time domain thermo-reflectance (TDTR) method.<sup>122</sup> They measured the thermal conductivity of different orientations by varying the temperature and found that the thermal conductivity decreased as the temperature increased in general, as shown in Fig. 8(a and b). Based on the verification of previous studies, they



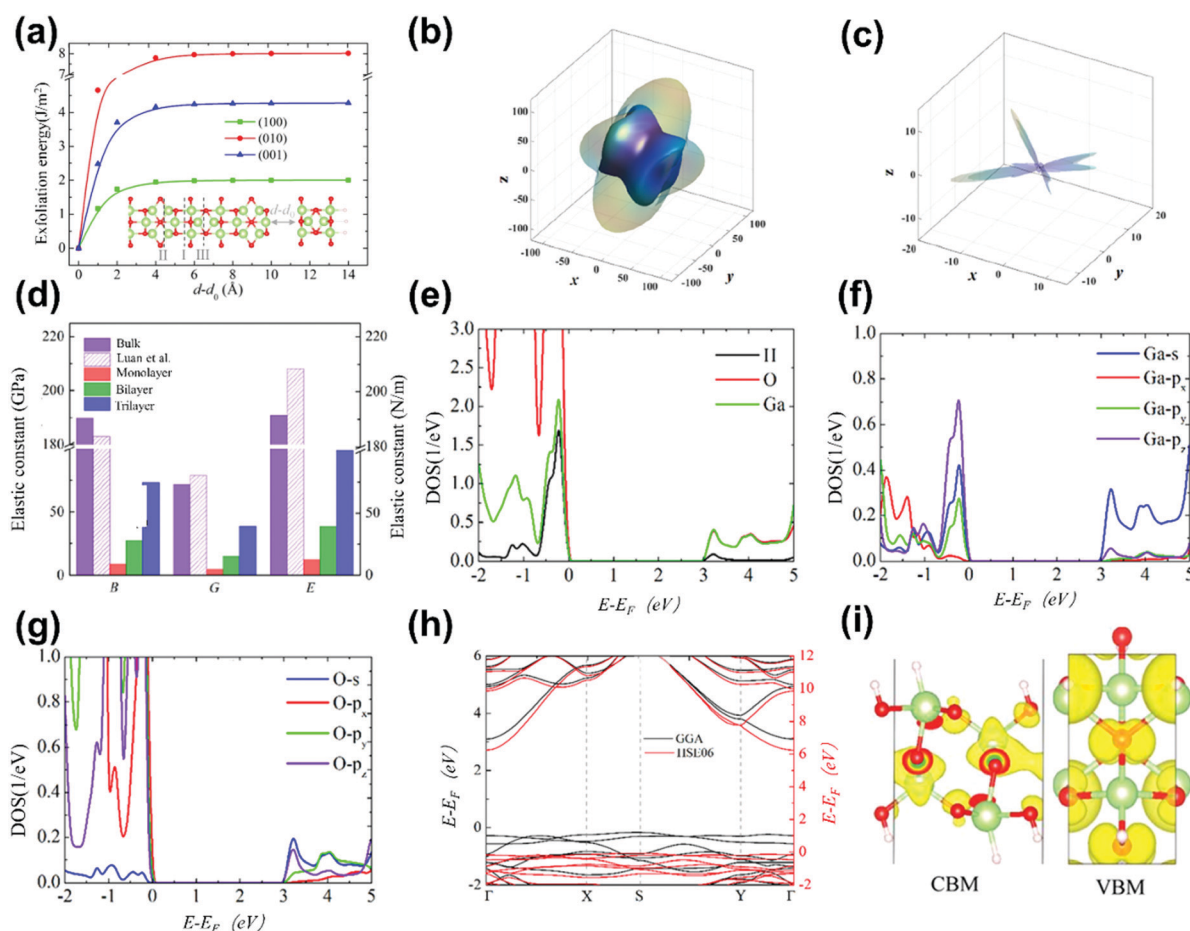
**Fig. 8** (a) Temperature-dependent thermal conductivity in the log scale along different crystal orientations of  $\beta\text{-Ga}_2\text{O}_3$  by the TDTR approach as a function of temperature (K). (b) Temperature-dependent thermal conductivity in the linear scale along different crystal orientations of  $\beta\text{-Ga}_2\text{O}_3$  by the TDTR approach as a function of  $1/T$  ( $\text{K}^{-1}$ ). Reproduced with permission.<sup>122</sup> Copyright 2015, American Institute of Physics Publishing. The direction-dependent (c) Young's modulus and (d) shear modulus of bulk  $\beta\text{-Ga}_2\text{O}_3$  in 3D representation surfaces. Reproduced with permission.<sup>132</sup> Copyright 2019, Elsevier Ltd.

also found that the reason for anisotropic thermal conductivity was due to the discrepancies in the speed of sound along different crystal orientations.

The thermal coefficients are related to the mechanical coefficients in the process of investigating other crystal properties. As for monoclinic  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>, it has 13 kinds of elastic constants ( $C_{11}$ ,  $C_{22}$ ,  $C_{33}$ ,  $C_{44}$ ,  $C_{55}$ ,  $C_{66}$ ,  $C_{12}$ ,  $C_{13}$ ,  $C_{15}$ ,  $C_{23}$ ,  $C_{25}$ ,  $C_{35}$ , and  $C_{46}$ ).<sup>23,130–132</sup> They are usually obtained by first-principles calculations, as well as Young's modulus  $E$ , bulk modulus  $B$ , shear modulus  $G$ , and other mechanical constants. Note that the obvious differences of these mechanical constants in different orientations indicate that the mechanical properties of the bulk  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> are anisotropic obviously. Fig. 8(c and d) displays the 3D representation surfaces of direction-dependent Young's and shear moduli of bulk  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>, respectively. It is not a common sphere and has different values in different directions, that is, it is anisotropic. Meanwhile, the minimum thermal conductivity  $\kappa_{\min}$  is closely related to the above elastic properties and can be obtained by

the following formula:  $\kappa_{\min} = 0.87k_B N_A^{2/3} N^{2/3} \rho^{1/6} E^{1/2} / M^{2/3}$ , where  $k_B$ ,  $N_A$ ,  $N$ ,  $\rho$ ,  $E$ , and  $M$  are the Boltzmann constants, Avogadro's number, the number of atoms in the unit cell, density, Young's modulus, and the weight of the unit cell, respectively.<sup>23,133,134</sup> Therefore, this also explains the reasons for the different thermal conductivity of bulk  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> in different directions observed in the experiment from another aspect.

In addition, it has been found that  $C_{11}$  is less than  $C_{22}$  and  $C_{33}$ , while  $C_{55}$  and  $C_{66}$  are greater than  $C_{44}$ , suggesting that the bond strength along the [100] direction of bulk  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> is weaker than that in other directions. Thus, it can be sliced into quasi two-dimensional flakes along the (100) surface. The exfoliation energy of  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> along the (100) surface is calculated by the DFT method, as shown in Fig. 9(a).<sup>21</sup> The mechanical properties of low-dimensional Ga<sub>2</sub>O<sub>3</sub> after exfoliation also have great variations compared with that of bulk. For example, the anisotropies in the compressive and shear behaviors in the monolayer Ga<sub>2</sub>O<sub>3</sub> are enhanced as shown in Fig. 9(b and c).



**Fig. 9** (a) Calculated exfoliation energy in different crystal planes as a function of  $d - d_0$ . Reproduced with permission.<sup>21</sup> Copyright 2018, American Chemical Society. The direction-dependent (b) Young's modulus and (c) shear modulus of low-dimensional Ga<sub>2</sub>O<sub>3</sub> in 3D representation surfaces. (d) Bulk modulus ( $B$ ), shear modulus ( $G$ ), and Young's modulus ( $E$ ) of the bulk and different layers of low-dimensional Ga<sub>2</sub>O<sub>3</sub>. Reproduced with permission.<sup>132</sup> Copyright 2019, Elsevier Ltd. (e–g) PDOS of H-passivated low-dimensional Ga<sub>2</sub>O<sub>3</sub>. (h) Band structure of monolayer low-dimensional  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> obtained by the HSE06 functional (red solid line) and GGA functional (black solid line). (i) Projected charge densities of the CBM and VBM of H-passivated low-dimensional Ga<sub>2</sub>O<sub>3</sub>. Reproduced with permission.<sup>21</sup> Copyright 2018, American Chemical Society.

Their shapes are far from sphere shapes. Meanwhile, the modulus  $B$ ,  $G$ , and  $E$  of monolayer  $\text{Ga}_2\text{O}_3$  decrease (see Fig. 9(d)) while the thermal constant  $\kappa$  increases up to  $49 \text{ W m}^{-1} \text{ K}^{-1}$ .<sup>23</sup> It is expected to alleviate the heat dissipation problem caused by the poor thermal conductivity in the bulk  $\text{Ga}_2\text{O}_3$ .

Unluckily, this exfoliation property is not observed in other metastable  $\text{Ga}_2\text{O}_3$  up to now. As mentioned above,  $\beta\text{-Ga}_2\text{O}_3$  is composed of a chain structure in which  $[\text{GaO}_4]$  tetrahedra intersect with  $[\text{GaO}_6]$  octahedra. Because the atoms in the crystal need to meet the rule of the dense packing properties, the O atoms and Ga atoms at the interface between  $[\text{GaO}_4]$  tetrahedra and  $[\text{GaO}_6]$  octahedra often have long bond lengths. This is the unique feature of this crossed chain structure. In contrast, the lattice structures of other phases are composed of only  $[\text{GaO}_6]$  octahedra, which are not easy to exfoliate into the low-dimensional structure. Thus, the subsequent research is mainly based on the low-dimensional  $\text{Ga}_2\text{O}_3$  obtained from exfoliated  $\beta\text{-Ga}_2\text{O}_3$ .

### 5. Low-dimensional $\text{Ga}_2\text{O}_3$

Due to the unique structure of  $\beta\text{-Ga}_2\text{O}_3$ , the low-dimensional structure can be obtained by exfoliating the bulk  $\beta\text{-Ga}_2\text{O}_3$ . As the thickness of the material decreases to the atomic thickness, the properties change accordingly. However, since  $\beta\text{-Ga}_2\text{O}_3$  is not a van der Waals material, obtaining ultra-thin flakes with a thickness of less than 100 nm is a huge challenge. Kwon *et al.* solved this problem in 2017.<sup>135</sup> They mechanically exfoliated the bulk  $\beta\text{-Ga}_2\text{O}_3$  with tape and then applied plasma etching to tune the thickness of exfoliated  $\text{Ga}_2\text{O}_3$ . Combined with the  $\text{SF}_6$  atmosphere, the thickness of the  $\beta\text{-Ga}_2\text{O}_3$  flake could be tuned from 300 nm down to  $\sim 60$  nm. Because the reaction between  $\text{SF}_6$  and  $\text{Ga}_2\text{O}_3$  generated oxygen and volatile oxyfluoride compounds, and non-volatile compounds (*e.g.*,  $\text{GaF}_x$ ) that can be moved by ion bombardment, the thickness of exfoliated  $\text{Ga}_2\text{O}_3$  can be reduced. Meanwhile, Van de Walle *et al.* and Bermudez attempted to thin the thickness of  $\beta\text{-Ga}_2\text{O}_3$  along the  $[100]$  orientation down to half to attain the monolayer  $\beta\text{-Ga}_2\text{O}_3$  theoretically and then investigated the properties of monolayer  $\beta\text{-Ga}_2\text{O}_3$  briefly.<sup>48,136</sup> In the process of exploring the transport properties of low-dimensional  $\text{Ga}_2\text{O}_3$ , the carrier mobility ( $\sim 130 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$ ) of  $\beta\text{-Ga}_2\text{O}_3$  membranes exfoliated by Hwang *et al.* was found to be close to that of the bulk.<sup>22</sup> However, the mobility value is still not comparable to those of other wide bandgap semiconductors. The lack of quantum confinement effects has been observed in the unpassivated  $\beta\text{-Ga}_2\text{O}_3$  flake. What's more, the exfoliated  $\text{Ga}_2\text{O}_3$  is unstable under ambient conditions because of the dangling bonds on the surface. It is found that surface passivation technology is one of the good solutions to the instability of low-dimensional wide bandgap semiconductors.<sup>137</sup> Based on previous research results, Su *et al.* did further research on exfoliated  $\text{Ga}_2\text{O}_3$  by surface passivation engineering.<sup>21,27,132,138</sup> They put forward a new strategy for applying hydrogen to passivate the surface of low-dimensional  $\text{Ga}_2\text{O}_3$ , which further enhanced the quantum confinement effects. They found that the H passivated structure demonstrated a larger bandgap (5–6 eV) and higher carrier

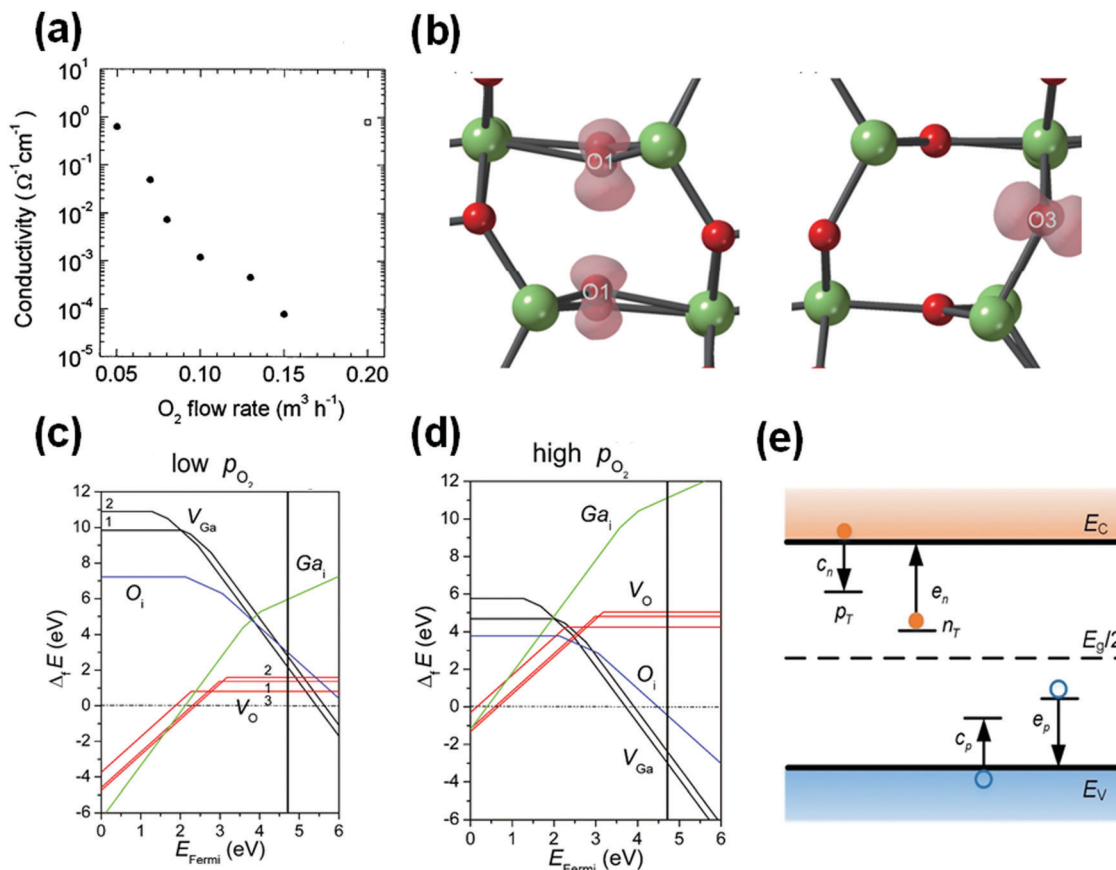
mobility ( $\sim 25\,000 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$ ), which led to its application in optoelectronic devices. Meanwhile, samples with hydrogen passivation had a long electron relaxation time ( $\sim 4$  ps) and larger exciton binding energy (1–2 eV) than the bulk. Although some theoretical studies have been carried out on low-dimensional  $\text{Ga}_2\text{O}_3$ , it still needs to be confirmed by subsequent related experiments. In addition to the mechanical exfoliation mentioned above, it should be noticed that the low-dimensional  $\text{Ga}_2\text{O}_3$  monolayer can also be obtained by the chemical synthesis method and MBE, but the exfoliation method is widely applied because of its simple process.<sup>139,140</sup>

Although H passivated monolayer  $\text{Ga}_2\text{O}_3$  has many excellent properties, there are still some problems that need to be solved, *e.g.*, many defects in the parent bulk  $\text{Ga}_2\text{O}_3$  are also accompanied by the monolayer  $\text{Ga}_2\text{O}_3$  during the exfoliation. Besides, similar to the bulk  $\text{Ga}_2\text{O}_3$ , the VBM of monolayer  $\text{Ga}_2\text{O}_3$  is still mainly contributed by the 2p orbitals of O, as shown in Fig. 9(e and g). The dispersion degree of monolayer  $\text{Ga}_2\text{O}_3$ 's valence band is low (see Fig. 9(h)), and the effective mass of the hole is large, which affects the hole transport. Meanwhile, the generated holes do not become free holes instead of the localized holes formed near the O atoms (see Fig. 9(i)). Effective p-type doping is difficult to be obtained. Therefore, investigating the effects of impurities and defects on the properties of low-dimensional  $\text{Ga}_2\text{O}_3$  is similar to the situation in the bulk  $\text{Ga}_2\text{O}_3$  to a degree.

## III. Effects of defects and impurities on electronic properties

Although  $\beta\text{-Ga}_2\text{O}_3$  has been fabricated by several methods, there are inevitable defects (*e.g.*, vacancies, deep level defects, *etc.*) in  $\beta\text{-Ga}_2\text{O}_3$  which significantly affect the properties of  $\beta\text{-Ga}_2\text{O}_3$  and the performance of  $\beta\text{-Ga}_2\text{O}_3$  based devices.<sup>52,141</sup> On the one hand, defects can serve as scatter centers to affect the carrier mobility and then affect the device output characteristics and responsive characteristics. On the other hand, they can also serve as trapped centers which affect sensitivity in the photodetectors. In addition to the bulk defects, the surface and interface defects of  $\beta\text{-Ga}_2\text{O}_3$  are also associated with poor device performance, such as threshold voltage instability, reduced channel carrier mobility, and poor device reliability. Therefore, the defects including vacancies and interstitial atoms in the  $\beta\text{-Ga}_2\text{O}_3$  host material are worth to be studied.

Metal oxides are insulators under the condition of meeting the stoichiometric ratio, but their growth has a great relationship with the composition of the ambient atmosphere in the actual process. The insufficiency or excess of O atoms in the chemical composition results in oxygen vacancies ( $\text{V}_\text{O}$ ) or oxygen interstitials ( $\text{O}_\text{i}$ ), respectively.<sup>142,143</sup>  $\text{V}_\text{O}$  and  $\text{O}_\text{i}$  play the roles of donor and acceptor, respectively, thus making the conductivity of oxides vary with the oxygen content at room temperature, as shown in Fig. 10(a). Meanwhile, considering the differences of growth environments such as Ga rich and O rich, other single defects ( $\text{V}_\text{Ga}$  and  $\text{Ga}_\text{i}$ ) and double defects also



**Fig. 10** (a) The electrical conductivity of the  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> single crystals along the  $b$  axis as a function of the O<sub>2</sub> flow rate. The closed circles and the open square refer to samples grown from undoped and Sn-doped Ga<sub>2</sub>O<sub>3</sub>, respectively. Reproduced with permission.<sup>46</sup> Copyright 1997, American Institute of Physics Publishing. (b) Relaxed atomic configurations and iso-surfaces of the squared wave functions of the SHTs on the O<sub>1</sub> and the O<sub>3</sub> site in  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>. Reproduced with permission.<sup>379</sup> Copyright 2019, American Physical Society. Formation energies of point defects (e.g., V<sub>Ga</sub>, V<sub>O</sub>, Ga<sub>i</sub>, and O<sub>i</sub>) in  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> as a function of the Fermi energies in (c) O-poor and (d) O-rich conditions. Reproduced with permission.<sup>146</sup> Copyright 2013, American Physical Society. (e) Four processes of capture and emission of carriers between deep-level defects and the valence band (VB) or the conduction band (CB) in terms of the well-known Shockley–Read–Hall model. Reproduced with permission.<sup>380</sup> Copyright 2021, IOP Publishing Ltd.

exist in  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>.<sup>144</sup> Besides, some impurities inevitably enter  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> crystals and act as impurities in the actual growth process of bulk  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>; for example, hydrogen (H) and Si impurities, *etc.*, even form complexes with the vacancies in the host.<sup>105,145–147</sup> Meanwhile, the Ir ions are observed in the bulk  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> due to the utilization of crucible in the melt method in recent years.<sup>148</sup> These dopants introduced unintentionally during the preparation are deemed unintentional dopants. The unintentional dopants are related to the raw materials and vessels applied in the preparation closely, and they are generally unavoidable. Therefore, they are considered to be another origin of n-type performance in intrinsic  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>.

The electronic performance of devices needs to be further modulated in the applications of  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> devices. Doping engineering is an effective method. The available dopants, *e.g.*, Si,<sup>149</sup> Ge,<sup>150</sup> Sn,<sup>141</sup> *etc.*, are commonly applied in  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>. These dopants tune the electron concentrations of  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> ranging from 10<sup>15</sup> to 10<sup>21</sup> cm<sup>-3</sup>, which meet the basic requirements of high-performance devices. However, effective p-type doping, the troublesome question, is difficult to be realized in

$\beta$ -Ga<sub>2</sub>O<sub>3</sub> due to the flat valence band, self-trapped effects, and so on.<sup>151,152</sup> The self-trapped effects in  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> are generally induced by the lattice distortion.<sup>153</sup> Self-trapped charges are localized and the wave function of the electrons is only localized around the O atoms but not involved in the whole crystal, as shown in Fig. 10(b). This has also been confirmed by some characterization methods, *e.g.*, deep-level transient spectroscopy (DLTS) and deep-level optical spectroscopy (DLOS). The conditions are also observed in other wide bandgap oxides such as ZnO, SnO<sub>2</sub>, and In<sub>2</sub>O<sub>3</sub>.<sup>154</sup> Since the existent defects and impurities have significant effects on the fabrication and application of  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>, understanding the physical properties of defects and impurities of  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> is of great significance. Meanwhile, the significance of obtaining p-type Ga<sub>2</sub>O<sub>3</sub> is not only to overcome the problems of Ga<sub>2</sub>O<sub>3</sub> itself but also to some extent to provide guidance for effective p-type doping of other wide bandgap oxide semiconductors.

In the following section, the common defects and impurities in  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> are summarized, *e.g.*, vacancies and interstitial atoms, deep level defects, unintentional doping impurities,



available doping impurities, and surface passivators. The intrinsic defects of bulk  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> and the effects of donors, acceptors, and passivators on the electronic properties are described. Meanwhile, the effects of defects and impurities on the electronic properties of low-dimensional  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> are comparatively reviewed here.

## 1. Intrinsic defects

**1.1 Oxygen vacancy (V<sub>O</sub>).** Note that both bulk  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> grown by the melt method and epitaxial film obtained by vapor deposition often show a certain conductivity after the growth process or subsequent heat treatment in the atmosphere of N<sub>2</sub>, H<sub>2</sub>, or vacuum. Moreover, the conductivity ( $\sigma$ ) of  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> varies with the oxygen flow conditions, as shown in Fig. 10(a).<sup>52</sup> Specifically,  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> has high conductivity at a low O<sub>2</sub> flow rate and it decreases with increasing O<sub>2</sub> content. These treatments significantly tune the concentrations of oxygen vacancies (V<sub>O</sub>) in  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>. Therefore, the conductivity of  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> is related to the O<sub>2</sub> content in the atmosphere, which is related to the oxygen vacancy (V<sub>O</sub>) concentrations in  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>. The V<sub>O</sub> is regarded as the donor, and the carriers ionized by V<sub>O</sub>s will further increase the background carrier concentrations in the undoped Ga<sub>2</sub>O<sub>3</sub> bulk or film. For example, Lee *et al.* prepared  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> thin films by magnetron sputtering, and then annealed them in the O<sub>2</sub> and N<sub>2</sub> atmosphere, respectively.<sup>155</sup> Dong *et al.* annealed the sputtered  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> thin film in an atmosphere of O<sub>2</sub> of different volume percentage.<sup>156</sup> They all found that the conductivity of the as-grown Ga<sub>2</sub>O<sub>3</sub> film also varied with the variation of O<sub>2</sub> content in the annealed atmosphere. They suggested that V<sub>O</sub> which played the role of a donor provided additional carriers based on X-ray photoelectron spectroscopy (XPS). In the O 1s XPS spectra, two main peaks can be obtained by the fitting of the O 1s peak by Gaussian fitting. The strongest peaks with binding energies of 531.6–531.9 eV were assigned to lattice oxygen (*i.e.*, Ga–O bond), and the peaks with the highest binding energy around 532 eV were assigned to oxygen vacancy (V<sub>O</sub>) in general.<sup>157–167</sup> The as-grown Ga<sub>2</sub>O<sub>3</sub> films were post-annealed in the O<sub>2</sub> and N<sub>2</sub> atmospheres respectively in Lee *et al.*'s research. The O content increased more in the O<sub>2</sub> environment (O/Ga = 1.43) than in the N<sub>2</sub> environment (O/Ga = 1.42). Meanwhile, the carrier concentrations of the films obtained by the *C*–*V* measurement in O<sub>2</sub> and N<sub>2</sub> atmospheres were  $1.62 \times 10^{16} \text{ cm}^{-3}$  and  $2.01 \times 10^{16} \text{ cm}^{-3}$ , respectively. Thus, it can be derived from the experiments that the variation of carrier concentrations and electrical conductivity was commonly caused by oxygen vacancies (V<sub>O</sub>s). The related mechanism is that an oxygen vacancy (V<sub>O</sub>) often captures two electrons to maintain its neutral oxygen vacancy. Free electrons can be ionized by single or double neutral oxygen vacancies in  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>. This mechanism allows  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> to produce excess electrons to behave as an electron-rich oxide. Thus,  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> shows conductivity upon annealing in the absence of an oxygen atmosphere. The V<sub>O</sub> is presumed to introduce a shallow donor level, which will provide electrons to increase the carrier concentrations and further increase the conductivity. Meanwhile, it is found that the V<sub>O</sub> is a shallow donor level located at about

$\sim 0.02$ – $0.03$  eV below the CBM in the experiment.<sup>168</sup> However, the viewpoint that the conductivity of  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> is induced by V<sub>O</sub>s is refuted by other results. Zacherle *et al.* found the related phenomena.<sup>143,169–171</sup> Although V<sub>O</sub>s were easily formed at the low oxygen partial pressure, the transition level from the neutral state to the +2 state was the deep level in the bandgap whether in the O-rich or O-poor ambient condition, as shown in Fig. 10(c and d). One of the three types of V<sub>O</sub>s (V<sub>O(2)</sub>) in  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> was close to the CBM, and the other two (V<sub>O(1)</sub> and V<sub>O(3)</sub>) were far away in the  $\Delta E_{\text{form}} - E_{\text{Fermi}}$  diagram. However, the defect level  $E_{(0/+2)}$  introduced by V<sub>O(2)</sub> close to the conduction band was still more than 1 eV (*i.e.*,  $E_c - E_{(0/+2)} > 1$  eV), which had also been obtained in other literature.<sup>171–173</sup> This indicated that the V<sub>O</sub> was a deep-level defect. Moreover, Onuma *et al.* found that the blue emission was observed in  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>, which was attributed to the recombination between the deep local donor and the trapped hole.<sup>174,175</sup> The deep-level donor states here were speculated to be derived from V<sub>O</sub>s. The deep defects may not increase the electron concentrations.<sup>105,143,172</sup> This phenomenon is similar to the case in other oxides, *e.g.*, ZnO and In<sub>2</sub>O<sub>3</sub>.<sup>176</sup> In addition, the deep V<sub>O</sub> states are also confirmed by deep level transient spectroscopy (DLTS), deep resolution cathodoluminescence spectroscopy, and surface photoelectric voltage spectroscopy.<sup>177,178</sup> The results show that the distance from the defect level related to V<sub>O</sub> to the CBM is over 1 eV. Thus, whether the oxygen vacancy (V<sub>O</sub>) is the main source of n-type conductivity for  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> is still worth discussing and investigating.

As discussed in the previous section, the intrinsic defects (*e.g.*, V<sub>O</sub>s) cannot be avoided in the low-dimensional Ga<sub>2</sub>O<sub>3</sub> due to the direct exfoliation from the parent  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> bulk, which will have significant impact on the electronic properties of low-dimensional Ga<sub>2</sub>O<sub>3</sub>. To explore the effects of ordinary vacancies and explain the mechanism of defective low-dimensional Ga<sub>2</sub>O<sub>3</sub>, defective low-dimensional Ga<sub>2</sub>O<sub>3</sub> models were constructed and explained theoretically by Sun *et al.*<sup>179</sup> They found that the effects of defects on the low-dimensional Ga<sub>2</sub>O<sub>3</sub> were similar to that in the bulk. For example, the V<sub>O</sub>s introduced impurity states into the bandgap, which further reduced the bandgap and affected the performance of low-dimensional Ga<sub>2</sub>O<sub>3</sub>.

In general, V<sub>O</sub>s existing in the bulk  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> are considered as annoying defects in the power and optoelectronic devices. V<sub>O</sub> hinders the fabrication of bipolar devices because the p-type Ga<sub>2</sub>O<sub>3</sub> is difficult to obtain as mentioned before. That is, V<sub>O</sub> has been regarded as the donor in much research, especially in devices based on thin films grown by physical vapor phase epitaxy. It ionizes several electrons to increase the background carrier concentrations in Ga<sub>2</sub>O<sub>3</sub> and then compensates the acceptor dopants which have a low ionization rate to decrease the hole concentrations. Therefore, researchers have to consider applying a combination of heterogeneous p/n-type semiconductor materials in forming bipolar transistors or field-effect transistors in complementary devices and circuits technology. Besides, V<sub>O</sub>s as the trapped centers affect the sensitivity and responsivity in optoelectronic detectors, which should be noticed in the actual applications.

Effective ohmic-type metal–semiconductor contacts are important steps in the fabrication of transistors. In field-effect transistors based on metal-oxides, ohmic contact is often expected to be realized by the production of many  $V_{\text{O}}$ s in the semiconductor at the interface of field-effect transistors. In the fabrication of  $\beta\text{-Ga}_2\text{O}_3$  based transistors, Ti is chosen as the direct contact layer with  $\beta\text{-Ga}_2\text{O}_3$ , and Au is deposited upon Ti. The ohmic contact between Ti/Au and  $\text{Ga}_2\text{O}_3$  is formed by rapid thermal annealing (RTA) in a  $\text{N}_2$  atmosphere in the range of 450–500 °C.<sup>107,180,181</sup> Because the O atoms located at the Ti– $\text{Ga}_2\text{O}_3$  interface upon annealing in the absence of oxygen can spread into Ti contacted with  $\text{Ga}_2\text{O}_3$  to form  $\text{TiO}_x$ , the interface at  $\text{Ga}_2\text{O}_3$  forms lots of  $V_{\text{O}}$ s. This reduces the contact barrier located at the interface of  $\text{Ga}_2\text{O}_3$ , enabling easy formation of the ohmic contact. As for the non-volatile storage area, *e.g.*, resistance random access memory (RRAM),  $V_{\text{O}}$ s are of great benefit for device applications.<sup>182–184</sup> The conductive filament model composed of the oxygen vacancies is the main conduction mechanism of RRAM. The switching between low and high resistance states (LRS and HRS) in the resistive memory is carried out by the formation and disconnection of  $V_{\text{O}}$  conductive filaments in the  $\text{Ga}_2\text{O}_3$  layer, which is expected to update the existing von Neumann architecture of memory.

**1.2 Gallium vacancy ( $V_{\text{Ga}}$ ).** Different from the  $V_{\text{O}}$ , gallium vacancy ( $V_{\text{Ga}}$ ) is a p-type acceptor defect which may be formed in  $\beta\text{-Ga}_2\text{O}_3$  under the O-rich condition in theory. In recent years, Zacherle *et al.* obtained the formation energy and defect levels of  $V_{\text{Ga}}$  by first-principles calculations, as shown in Fig. 10(c and d).<sup>185</sup> Gallium vacancy ( $V_{\text{Ga}}$ ) promotes  $\beta\text{-Ga}_2\text{O}_3$  to form a p-type semiconductor theoretically, that is, the Fermi level ( $E_{\text{F}}$ ) is close to the valence band. However, the formation energy of  $V_{\text{Ga}}$  is very large in this situation, indicating that  $V_{\text{Ga}}$  is not easy to form. Although the formation energy of  $V_{\text{Ga}}$  decreases significantly as the Fermi level approaches the CBM of  $\text{Ga}_2\text{O}_3$ , the expected p-type  $\text{Ga}_2\text{O}_3$  is not observed in the experiments. The phenomenon that the formation energies of cation vacancies are too high to realize p-type semiconductors can be discovered in other oxides, *e.g.*, ZnO and  $\text{In}_2\text{O}_3$ .<sup>143,186,187</sup> In order to further determine the existence of  $V_{\text{Ga}}$  and its possible compensation effects in  $\text{Ga}_2\text{O}_3$ , positron annihilation spectroscopy is applied to explore the compensation of vacancy defects in  $\text{Ga}_2\text{O}_3$  films in terms of experiments.<sup>188</sup> The conclusion reveals that the compensation is not constrained by cation vacancy. Similar results can be obtained by other research.<sup>105,170,189,190</sup> Moreover, advanced detection methods of defects in the materials provide convenience for locating deep defect levels in materials. Polyakov *et al.* discovered the deep acceptor level by low-temperature photo-capacitance and capacitance–voltage measurement. The acceptor level was regarded as  $V_{\text{Ga}}$  and it was located at the position of  $E_{\text{v}} + 2.5\text{--}2.8$  eV.<sup>178,191,192</sup> Meanwhile, they found another  $V_{\text{Ga}}$  in the gap located at the position of  $E_{\text{v}} + 1.3$  eV by deep level transient spectroscopy with electrical and optical excitation (DLTS and ODLTS).<sup>193</sup> Therefore,  $V_{\text{Ga}}$  is a deep acceptor defect and does not contribute to the p-type conduction in  $\text{Ga}_2\text{O}_3$ . It is difficult to realize p-type  $\text{Ga}_2\text{O}_3$  by  $V_{\text{Ga}}$  in the host material. Although the

formation energy of a single  $V_{\text{Ga}}$  is very high and it is hard to realize, the formation of other defects will induce the  $V_{\text{Ga}}$  generated in the experiments, for example, the H treatment discussed in the “Unintentional doping mechanism” section.

**1.3 Oxygen and gallium interstitials ( $\text{O}_i$  and  $\text{Ga}_i$ ).** Gallium and oxygen interstitials ( $\text{Ga}_i$  and  $\text{O}_i$ ) play the roles of donor and acceptor respectively in principle. They have some effects on n-type conduction and p-type conduction. However, the theoretical calculations show that their formation energies are higher than that of other defects, and therefore the concentrations of these defects are less in  $\beta\text{-Ga}_2\text{O}_3$  crystals, as shown in Fig. 10(c and d).<sup>143,146</sup> Their effects on the whole defective systems’ properties can be ignored normally.

**1.4 Deep-level defects.** Deep-level defects are noteworthy defects in semiconductors because they have strong effects on carriers’ capture and recombination although they have weak influence on carrier concentrations and conductivity. These deep-level defects are investigated by deep-level transient spectroscopy (DLTS) and deep-level optical spectroscopy (DLOS). The detective fundamental is the Shockley–Read–Hall model which contains the excitation and capture of the carriers at the defect level, as shown in Fig. 10(e). The excitation and recombination of carriers can occur not only between the conduction band and the valence band but also between the conduction band/valence band and defect levels in the bandgap. Five kinds of deep levels (*viz.*  $E_1, \dots, E_5$ ) have been reported in the  $\text{Ga}_2\text{O}_3$  bulk and films, as shown in Fig. 11(a). By using DLTS, Zhang *et al.* observed that the  $E_1$ ,  $E_2$ , and  $E_3$  levels were located at 0.62 eV, 0.82 eV, and 1.00 eV from the CBM, respectively.<sup>178</sup> Similar positions of these deep levels were also found by Irmscher *et al.* and Farzana *et al.*<sup>192,194</sup> The other two deep defect levels named  $E_4$  and  $E_5$  respectively were observed by DLOS. They were located at 2.16 eV and 4.40 eV from the CBM, respectively. These deep levels were often located in the bandgap as compensation levels or trapped centers. Other researchers have also observed deep defect levels in bulk or thin film  $\text{Ga}_2\text{O}_3$ . The positions of these deep defect levels are listed in Table 2. There are many speculations about the origin of these deep levels. It is inferred that the source of deep level  $E_1$  may be assigned to transition metal (such as Fe and Co) doping, while the source of  $E_2$  may be caused by Sn doping or Fe doping. In addition, it may also be attributed to  $V_{\text{O}}$ . The source of the  $E_3$  level may be related to transition metal doping or  $V_{\text{O}}$ . Moreover, the results detected in the epitaxial layer suggest that it may also be related to the complex formed by H and intrinsic defects.  $E_4$  is related to the intrinsic defects or  $V_{\text{Ga}}$  coupling with H. The concentrations of  $E_5$  in bulk materials are high up to  $10^{16} \text{ cm}^{-3}$ , which is considered to be related to  $V_{\text{Ga}}$ s or self-trapped holes (STHs). Besides, it is interesting to find that there is an  $E_2^*$  level at 0.72 eV below the conduction band, which may originate from  $V_{\text{Ga}}$ s or their complexes. It should be noticed that the concentrations of these defects are different in bulk and epitaxial films, as shown in Table 2. Meanwhile, the concentrations of  $E_2$  and  $E_4$  levels increase under the proton irradiation condition, which proves that the origin of these two deep levels is

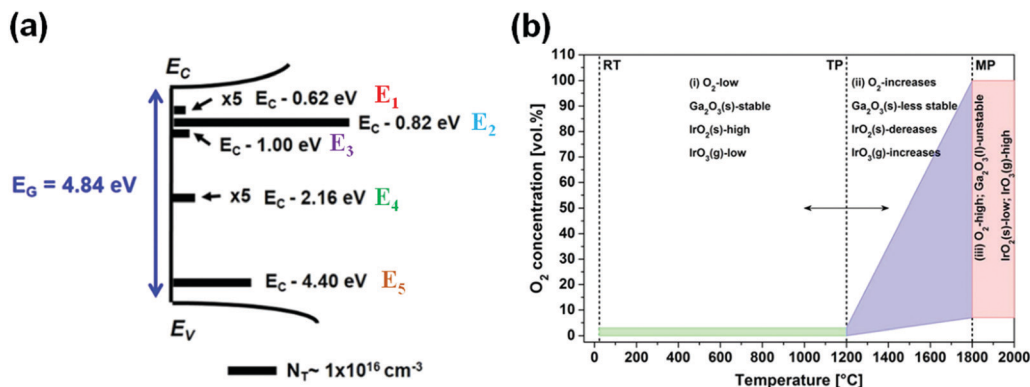


Fig. 11 (a) Summary of the distribution of deep level defect states detected by both DLTS and DLOS in the same EFG-grown  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>(010) materials. Reproduced with permission.<sup>178</sup> Copyright 2016, American Institute of Physics Publishing. (b) Schematic diagram of O<sub>2</sub> delivery to the growth furnace for growing large diameter  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> single crystals from an Ir crucible as a function of temperature by the melt-grown method. Reproduced with permission.<sup>381</sup> Copyright 2017, The Electrochemical Society.

Table 2 Summary of the ionization energy and concentrations of deep level defects in bulk  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> crystals and films

Deep trap level	Type	Ionization energy referenced to CBM ( $E_a$ , eV)	Concentrations ( $\text{cm}^{-3}$ )	Ref.
E1	Bulk	0.62	$10^{14}$ – $10^{15}$	178
	Bulk	0.55	$10^{14}$ – $10^{15}$	192
	Film	0.60	$\sim 10^{13}$	387
E2	Bulk	0.82	$\sim 10^{16}$	192
	Bulk	0.74	$\sim 10^{16}$	192
	Film	0.78	—	148 and 388
	Film	0.80	$\sim 10^{16}$	191 and 253
E2*	Bulk	0.75	—	388
	Film	0.72–0.78	$10^{13}$ – $10^{14}$	387 and 389
E3	Bulk	1.00–1.04	$10^{15}$ – $10^{16}$	178, 192 and 194
	Bulk	0.95	—	390
	Film	0.98	$\sim 10^{15}$	391
	Film	1.05	$\sim 10^{15}$	392
	Film	1.10	$\sim 10^{16}$	191
E4	Bulk	1.30	$\sim 10^{16}$	194
	Bulk	1.48	—	388
	Film	1.20	$\sim 10^{14}$	389
E5	Film	1.35	—	389

Table 3 Summary of electronic properties (electron concentration ( $n$ ), mobility ( $\mu$ ), and conductivity ( $\sigma$ )) of Ga<sub>2</sub>O<sub>3</sub> bulk materials and thin films with unintentional doping prepared by different methods

Type	Preparation method	Carrier concentration $n$ ( $\text{cm}^{-3}$ )	Carrier mobility $\mu$ ( $\text{cm}^2 \text{V}^{-1} \text{s}^{-1}$ )	Conductivity $\sigma$ ( $\text{S cm}^{-1}$ )	Ref.
Thin film	MOVPE	$10^{14}$ – $10^{17}$	100–140	0.001–10	393
Bulk	CZ	$2.5 \times 10^{16}$ – $5 \times 10^{17}$	110–150	—	365
		$10^{17}$ – $10^{18}$	80–127	$\sim 0.87$ –25	125
Bulk	CZ	$\sim 10^{18}$	—	—	195
Bulk	CZ	$2.5 \times 10^{16}$ – $2 \times 10^{18}$	80–152	—	232
Bulk	CZ	$1.8 \times 10^{17}$	—	—	394
Bulk	FZ	$2 \times 10^{18}$	100	—	168
Bulk	FZ	$10^{17}$ – $10^{18}$	20–200	—	395
Bulk	VB	$5.1 \times 10^{16}$	90.5	$\sim 0.74$	396
Bulk	EFG	$1 \times 10^{17}$	150	—	397
Bulk	EFG	$3.92 \times 10^{16}$	107	$\sim 0.67$	398
Bulk	EFG	$2.0 \times 10^{17}$	—	—	265
Bulk	OFZ	$10^{18}$	—	$10^{-4}$ –1	52
Bulk	OFZ	$10^{17}$ – $10^{18}$	50–180	6.82–16.67	399
Bulk	OFZ	$4.99 \times 10^{17}$	87.5	6.99	231

related to the intrinsic defects in Ga<sub>2</sub>O<sub>3</sub>. This character can be also applied to examine the damage of proton irradiation.

## 2. Unintentional doping mechanism

The preparation of  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> by the melt-grown method or epitaxial methods is subject to contamination introduced by some external elements which are often referred to as unintentional dopants. In addition to V<sub>O</sub>, the unintentional dopants are generally regarded as another influencing factor on the intrinsic conductivity of  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> because these unintentional dopants provide high background carrier concentrations by ionization in the  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> single crystal or epitaxial film, thus making it an n-type semiconductor. As shown in Table 3, these unintentional dopants make  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> grown by the melt process and epitaxial methods exhibit high carrier concentrations ( $10^{14}$ – $10^{18} \text{ cm}^{-3}$ ). Besides, the background carriers introduced by these unintentional dopants compensate these low concentration

holes which are induced by the low solubility and high ionization energy of the acceptor in the experiments of  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> doped by the acceptors. Consequently, effective p-type Ga<sub>2</sub>O<sub>3</sub> is difficult to realize. In addition, the background carriers introduced by these unintentional dopants have important effects on the effective doping concentrations and the breakdown field in the field of power devices. The accurate control of doping concentrations in the  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> drift layer can lead to a significant increase in the breakdown field in general. However, there are unintentional impurities in the drift layer which not only compensate the background carriers induced by the unintentional dopants but also act as the scattering centers to affect the mobility of the carriers. Therefore, the doping mechanism of these unintentional dopants should not be ignored.

At present, melt-grown  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> still inevitably introduces these unintentional dopants. The source of these unintentional dopants is often related to the purity of the raw material, of

which Ir element is the most common impurity.<sup>195–197</sup> Fig. 11(b) shows the effects of the growth atmosphere and temperature on the formation of  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> single crystals by the Czochralski method. It is identified that the Ga atoms, O atoms, and Ir atoms satisfy a certain thermodynamic equilibrium relationship. The  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> powder gradually becomes unstable near 1200 °C, and the Ir element gradually begins to be oxidized to IrO<sub>3(g)</sub> at this time. When the growth temperature increases to the melting point of  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> (~1800 °C), IrO<sub>3(g)</sub> becomes stable and mixes into the Ga<sub>2</sub>O<sub>3</sub> melt as an unintentional dopant gradually. In other words, Ir atoms will mix into the Ga<sub>2</sub>O<sub>3</sub> melt and they can substitute some Ga atoms through the growth atmosphere and temperature modulation, which promotes Ga<sub>2</sub>O<sub>3</sub> to become an electron-rich system. Besides, other unintentional doping impurities, *e.g.*, Fe and Si, mostly come from raw materials. The mechanism is similar to the intentional doping mechanism with impurities; thus the only way to suppress the influence of these impurities is to further purify the raw material. As for the chemical vapor deposition methods (*e.g.*, MOCVD), the raw materials are synthesized from trimethylgallium (TMGa) or triethylgallium (TEGa) which inevitably introduces H atoms into Ga<sub>2</sub>O<sub>3</sub>. Note that hydrogen can be introduced in the Ga<sub>2</sub>O<sub>3</sub> host material by two ways: substitution (H<sub>O</sub>) and interstitial (H<sub>i</sub>). It is discovered that some annealed Ga<sub>2</sub>O<sub>3</sub> materials contain more carrier concentrations, which may be due to the introduction of H<sub>i</sub><sup>198,199</sup> because H<sub>i</sub> has low formation energy whether in O-rich conditions or O-poor conditions. Differently, H<sub>O</sub> has low formation energy only in O-poor conditions. Both H<sub>O</sub> and H<sub>i</sub> are predicted to be shallow donors.<sup>105</sup> Interestingly, H can bind to the V<sub>Ga</sub> to form the V<sub>Ga</sub>-H complex, and then impedes the formation of p-type Ga<sub>2</sub>O<sub>3</sub>.<sup>170,190,197,200–202</sup> The V<sub>Ga</sub>-H complex defects have high thermal stability in  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>.<sup>203,204</sup> Meanwhile, the formation energy of H-vacancy complexes can be lower than that of single vacancy, as shown in Fig. 12(a). When the Fermi level becomes closer to the conduction band, that is, the semiconductor becomes more and more degenerate,

although the formation energy of V<sub>Ga</sub> also decreases, the formation energy of V<sub>Ga</sub>-H decreases much faster. The V<sub>Ga</sub>-H complex is often considered to introduce a shallow donor level, thus resulting in increasing background carriers of Ga<sub>2</sub>O<sub>3</sub>. Meanwhile, H can stabilize the presence of negatively charged cation vacancies, and reduce their charge state by passivation. In addition, H is more likely to combine with other acceptor dopants to form complexes, such as Mg,<sup>197</sup> which should be paid attention to in the actual doping process.

As for low-dimensional Ga<sub>2</sub>O<sub>3</sub>, it is directly obtained from the bulk Ga<sub>2</sub>O<sub>3</sub> by mechanical exfoliation. Therefore, it is also affected by the unintentional doping mechanism, which increases the carrier concentrations without intentional doping. The mechanism is similar to that in the bulk material.

### 3. Hetero-valence impurities

**3.1 Donors.**  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> with an ideal stoichiometric ratio is a strong insulator. However, the prepared  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> in practice tends to behave as an n-type semiconductor. The reason for the n-type conductivity of Ga<sub>2</sub>O<sub>3</sub> remains controversial. A widely accepted view is that the electric conductivity of Ga<sub>2</sub>O<sub>3</sub> is larger in an O-poor environment than that in an O-rich environment due to the negative correlation between conductivity and oxygen pressure  $p(\text{O}_2)$ .<sup>205,206</sup> This explanation seems to make sense in the physical vapor deposition method such as magnetron sputtering and pulsed laser deposition. On the other hand, in the chemical vapor deposition and melt method, some electron-rich impurities as unintentional dopants enter into the host material as substitutions or interstitials during the preparation process, which can be regarded as the dopant.<sup>207</sup> Such dopants increase the carrier concentrations and then properly achieve high conductivity. Ir and H as unintentional dopants have been discussed in the previous section.

Although there is a certain concentration of electrons in undoped  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>, such concentrations cannot meet the requirements of high-performance devices. Doping engineering has been regarded as an effective way to modulate the electronic

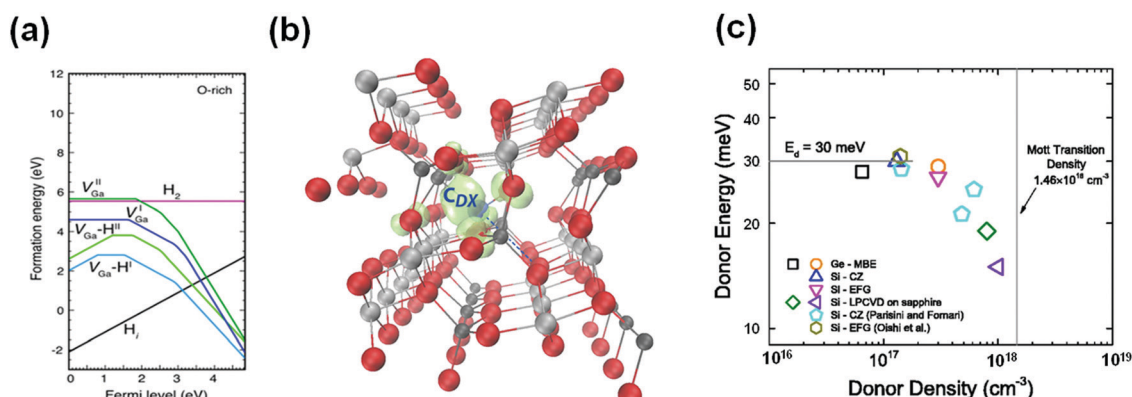


Fig. 12 (a) Formation energies of vacancies (V<sub>Ga</sub>), interstitial atoms (H<sub>i</sub>), and H-vacancy complexes (V<sub>Ga</sub>-H) in  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>, shown in the O-rich conditions. Reproduced with permission.<sup>190</sup> Copyright 2011, IOP Publishing Ltd. (b) Localization of the negatively charged C<sub>Dx</sub><sup>-</sup> defect state in Ga<sub>2</sub>O<sub>3</sub>, illustrated by the iso-surface (green) of the corresponding electron density. Reproduced with permission.<sup>213</sup> Copyright 2018, American Institute of Physics Publishing. (c) Summary of the donor energies as a function of donor concentration. Reproduced with permission.<sup>210</sup> Copyright 2018, American Institute of Physics Publishing.



properties of semiconductors. The dopant atom whose radius is close to that of the host atom is selected for substitution doping generally. If the dopant atom differs greatly from the host atom, interstitial atoms will be introduced or lattice distortion will be produced in the systems. According to this principle, many atoms (*e.g.*, Si, Sn, Ge, Zn, Cu, *etc.*) with a radius close to that of Ga can be applied to substitute the lattice position of the Ga host atom. Many atoms (*e.g.*, N, F, Cl, C, *etc.*) with a radius similar to that of O can be applied to substitute the lattice position of O in the same way. In the process of doping, the numbers of valence electrons of an impurity atom are compared with that of the host atom to define the electron-rich dopant or electron-poor dopant generally.<sup>208,209</sup> Among all the researched dopants of  $\beta\text{-Ga}_2\text{O}_3$  up to now, the group IV<sub>A</sub> elements (*i.e.*, C, Si, Ge, and Sn), the group VII<sub>A</sub> elements (*i.e.*, F, Cl, Br, and I) and some transition metals (*e.g.*, V, W, Mo, Re, Nb, *etc.*) are often applied to substitute the host atoms of  $\beta\text{-Ga}_2\text{O}_3$ . It is noticed that these donor dopants introduce shallow levels relatively. That is, the electron transition from the impurity level to the conduction band requires no more energy so that the carrier concentrations increase by orders of magnitude. So far, electron-rich dopants are available and easy to come into play, mainly because  $\text{Ga}_2\text{O}_3$  prefers n-type conductivity. Ga atoms have more spherical *s* orbital overlaps which make them more suitable for electron transport in the conduction band.<sup>105,207,210–218</sup>

In this section, some of the most commonly applied electron-rich dopants are summarized. The influence of these dopants on the electronic properties (*e.g.*, electron mobility and carrier concentrations) of  $\text{Ga}_2\text{O}_3$  is vital because these parameters reflect the merits and demerits of  $\text{Ga}_2\text{O}_3$  doped with these impurities. This will guide the selection of the dopants for material and device engineers. The carrier concentrations, mobility, and conductivity of different electron-rich element doped  $\text{Ga}_2\text{O}_3$  bulk and films are listed in Table 4.

*IV<sub>A</sub> – C, Si, Ge, and Sn.* The elements in group IV<sub>A</sub> have one more valence electron than that of the Ga element so that they can act as donors theoretically. Typical representatives of the IV<sub>A</sub> elements are C, Si, Sn, and Ge, and they have been proved to be n-type dopants.<sup>105,108,145,219,220</sup> C is easy to form positive charges. It has a radius close to that of the O atom, while it has a disparity with the radius of the Ga atom. C can not only substitute the Ga site ( $\text{C}_{\text{Ga}}$ ) to form a deep impurity level, but can also substitute O ( $\text{C}_{\text{O}}$ ) to produce a shallow level. Of the two situations,  $\text{C}_{\text{O}}$  is the most favorable situation. Interestingly,  $\text{C}_{\text{Ga}}$  can form a DX center, which is mainly caused by the off-site configuration of  $\text{C}_{\text{Ga}}$  due to the lattice distortion, as shown in Fig. 12(b).<sup>213</sup> The DX center is the common deep-level defect. It causes the charge state of the system to change from a positive state to a negative state directly without the experience of the neutral state. Thus,  $\beta\text{-Ga}_2\text{O}_3$  containing  $\text{C}_{\text{Ga}}$  has a promising application prospect in high-density data storage devices and optoelectronic switches. The potential applications have been proved in II–V compounds and alloys, *e.g.*, GaAs and  $\text{Al}_x\text{Ga}_{1-x}\text{As}$ , previously.<sup>221–227</sup>

Si, Sn, and Ge prefer to form shallow donor levels when substituting the Ga site.<sup>105,217</sup> Si-Doped  $\text{Ga}_2\text{O}_3$  was acquired by ion implantation by Sasaki *et al.* successfully.<sup>228</sup> It is noticed that the activation efficiency which is above 60% can be obtained after annealing, with the concentration of the Si dopant varying from  $1 \times 10^{19}$  to  $5 \times 10^{19} \text{ cm}^{-3}$ . Due to the small ionization energy of Si, the maximum carrier concentrations of Si doped  $\beta\text{-Ga}_2\text{O}_3$  can reach up in the range of  $10^{19}$ – $10^{20} \text{ cm}^{-3}$ . In addition, it has been discovered that the donor energy of Si decreases gradually with the increase of donor density, as shown in Fig. 12(c). This principle has been verified in Si doped  $\beta\text{-Ga}_2\text{O}_3$  samples prepared by different methods, *e.g.*, CZ, EFG, and low-pressure chemical vapor deposition (LPCVD). Therefore, it is easy to ionize the doped Si atoms and then increase the electron concentrations in  $\beta\text{-Ga}_2\text{O}_3$ . Meanwhile, high carrier concentrations promote the Burstein–Moss (B–M) effect that occurs in  $\beta\text{-Ga}_2\text{O}_3$ , which results in the absorption edge moving towards the high-energy direction.<sup>229</sup> The Tauc plot method can be applied to analyze  $\text{Ga}_2\text{O}_3$  samples with different carrier concentrations and it is discovered that the optical bandgap of samples with high carrier concentrations caused by Si increase. In addition, the mobility of the doped  $\beta\text{-Ga}_2\text{O}_3$  thin films on the native substrate by homoepitaxy can reach up to  $72 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$ , which is still less than the theoretical value. The reason may be that the carriers are scattered more by ionized impurities. In addition, the contact resistance decreases significantly if the electrode contacts the Si doped  $\beta\text{-Ga}_2\text{O}_3$ . Zhang *et al.* investigated the Si doped  $\beta\text{-Ga}_2\text{O}_3$  film grown on the sapphire by PLD. The Si composition in the epitaxial films was controlled by varying the target composition. It has been discovered that the carrier concentrations varied in the range of  $10^{15}$ – $10^{20} \text{ cm}^{-3}$ . Furthermore, they obtained the variation of the work function of  $\beta\text{-Ga}_2\text{O}_3$  under the condition of varied carrier concentrations by Kelvin force microscopy (KFM), as shown in Fig. 13(a). The work function of Si doped  $\beta\text{-Ga}_2\text{O}_3$  grown by PLD increased gradually when the carrier concentrations exceeded  $10^{15} \text{ cm}^{-3}$ . After analysis, Si doped  $\beta\text{-Ga}_2\text{O}_3$  ( $N_{\text{d}} \approx 5 \times 10^{19} \text{ cm}^{-3}$ ) showed low contact resistance commonly. In general, dopants incorporated into the host system need to be activated to make dopants manifest good performance. In the same year, Son *et al.* investigated the donors' activated situations of Si doped  $\beta\text{-Ga}_2\text{O}_3$  substrates treated at different annealing temperatures.<sup>230</sup> They applied electron paramagnetic resonance (EPR) to study the donors' behavior and revealed that Si doped  $\beta\text{-Ga}_2\text{O}_3$  may also possess the  $\text{DX}^-$  state, as shown in Fig. 13(b). The donors in the substrates annealed at  $\sim 1100$ – $1110 \text{ }^\circ\text{C}$  were partially activated and were shown to behave as the negative charge state  $\text{DX}^-$  locating at  $\sim 28$ – $29 \text{ meV}$  below the CBM. When the annealed temperature increased up to  $1150 \text{ }^\circ\text{C}$ , the donors were fully activated and the ionized electrons were partially delocalized. Meanwhile, the electron concentrations also increased from  $10^{16} \text{ cm}^{-3}$  to  $\sim 9 \times 10^{17} \text{ cm}^{-3}$  and the activation energy decreased from  $49 \text{ meV}$  to  $\sim 17 \text{ meV}$  remarkably. It follows that the low cost and easy availability make Si one of the most common n-type dopants.

**Table 4** Summary of electronic properties (electron concentration ( $n$ ), mobility ( $\mu$ ), and conductivity ( $\sigma$ )) of Ga<sub>2</sub>O<sub>3</sub> bulk materials and thin films with intentional doping prepared by different methods

Type	Preparation method	Dopant	Carrier concentration $n$ (cm <sup>-3</sup> )	Carrier mobility $\mu$ (cm <sup>2</sup> V <sup>-1</sup> s <sup>-1</sup> )	Conductivity $\sigma$ (S cm <sup>-1</sup> )	Ref.
Bulk	CZ	Hf	$7.5 \times 10^{18}$ – $1.9 \times 10^{19}$	65–80	93.46–192.31	250
Bulk	CZ	Li	$1.9 \times 10^{16}$ – $2.9 \times 10^{20}$	106–118	—	232
Bulk	CZ	Sn	$2.5 \times 10^{18}$ – $10^{19}$	50–84	—	232
Bulk	CZ	Sn	$3 \times 10^{18}$ – $10^{19}$	35–52	~16.67–100	125
Bulk	CZ	Mg	—	—	—	125
Bulk	CZ	Cu	$\sim 7 \times 10^{17}$	~79	—	232
Bulk	CZ	Mg, Co, Ni, Al	$< 10^{15}$	—	—	232
Bulk	CZ	Cr	$4.0 \times 10^{17}$ – $10^{18}$	76–120	—	232
Bulk	CZ	Ce	$3.3 \times 10^{16}$ – $2.7 \times 10^{17}$	95–120	—	232
Bulk	CZ	Cu	—	—	$10^{-10}$ – $10^{-7}$	284
Bulk	CZ	Si	$10^{18}$ – $10^{19}$	—	—	232
Bulk	CZ	Si + Ce/Al	$1.0 \times 10^{18}$ – $3.0 \times 10^{18}$	—	—	232
Bulk	CZ	Sn	$10^{18}$ – $10^{19}$	—	—	232
Bulk	CZ	Zr	$6.5 \times 10^{17}$ – $5 \times 10^{18}$	~73–112	11.628–58.82	250
Bulk	CZ	Zr	$1.5 \times 10^{18}$ , $5.0 \times 10^{18}$	—	—	394
Bulk	VB	Sn	$4.7 \times 10^{17}$ – $3.6 \times 10^{18}$	60–111	8.40–34.48	396
Bulk	Verneuil	Mg	—	—	$10^{-10}$ – $10^{-6}$	400
Bulk	Verneuil	Zr	—	—	$10^{-7}$ – $10^{-3}$	400
Bulk	EFG	Sn	$4 \times 10^{18}$	110	—	401
Bulk	EFG	Si	$4.9 \times 10^{18}$	93	~71.43	352
Bulk	EFG	Fe	$\sim 10^{16}$	—	—	265
Bulk	OFZ	Nb	$9.55 \times 10^{16}$ – $1.8 \times 10^{19}$	40–80	$2.78 \times 10^{-3}$ –181.82	246
Bulk	OFZ	Ta	$3.6 \times 10^{16}$ – $3.0 \times 10^{19}$	50–100	~0.60–250	402
Bulk	OFZ	Sn	$2.26 \times 10^{18}$ – $7.12 \times 10^{18}$	49.3–64.7	23.42–56.18	231
Bulk	OFZ	Si	$10^{16}$ – $10^{18}$	~100	0.03–50	149
Bulk	OFZ	Mg	—	—	$1.67 \times 10^{-12}$	117
Thin film	PLD	Si	$10^{15}$ – $10^{20}$	—	$10^{-4}$ –1	382
Thin film	PLD	Si	$2.24 \times 10^{20}$	64.5	2323	266
Thin film	PLD	Si	$2.61 \times 10^{19}$ – $1.74 \times 10^{20}$	18.6–26.5	78–732	403
Thin film	PLD	Zn	$7.16 \times 10^{11}$ – $6.35 \times 10^{12}$	0.52–6.67	$1.43 \times 10^{-7}$ – $1.41 \times 10^{-4}$	404
Thin film	PLD	N	—	—	$10^{-5}$ – $10^3$	405
Thin film	PLD	Sn	$2.9 \times 10^{20}$	—	—	401
Thin film	PLD	Sn	$1.4 \times 10^{19}$	0.44	1	406
Thin film	PLD	Fe	$0.99 \times 10^{11}$	9.3	$4.42 \times 10^{-12}$	407
Thin film	PLD	Sn	$2.01 \times 10^{20}$	62.3	0.60	407
Thin film	PLD	Sn	$2.0 \times 10^{17}$ – $1.0 \times 10^{18}$	—	—	216
Thin film	MOVPE	Sn	$1 \times 10^{18}$	41	—	408
Thin film	MOVPE	Si	$10^{12}$ – $10^{13}$	<100	—	409
Thin film	MOVPE	Si	$4 \times 10^{17}$ – $5 \times 10^{19}$	—	—	410
Thin film	Sputter	Si	—	—	$4.8 \times 10^{-3}$ –1	411
Thin film	Sputter	Mg	—	—	~ $10^{-3}$	412
Thin film	Sputter	Zr	—	—	~ $10^{-3}$ –0.1	412
Thin film	Sputter	Ti	—	—	~0.01–0.1	412
Thin film	Sputter	V	~ $10^{15}$ – $9.3 \times 10^{18}$	0.45–0.56	$1 \times 10^{-5}$ –1	244
Thin film	Sputter	N	$1.01 \times 10^{12}$	—	$2.1 \times 10^{-3}$	291
Thin film	Sputter	Ta	$5.4 \times 10^{15}$ – $2.4 \times 10^{19}$	11.4–84.8	~0.11 to ~3.86	413
Thin film	MOCVD	Sn	—	—	$10^{-9}$ – $10^{-4}$	414
Thin film	MOCVD	Ge	$2.0 \times 10^{16}$ – $3.0 \times 10^{20}$	38–140	—	236
Thin film	MOCVD	Mg	—	—	~ $8 \times 10^{-8}$	415
Thin film	ALD	Sn	$2.3 \times 10^{20}$	—	—	401
Thin film	MBE	Ge	$10^{16}$ – $10^{20}$	40–120	~1–630	150
Thin film	MBE	Ge	$4.0 \times 10^{17}$	111	—	416
Thin film	MBE	Si	Up to $10^{19}$	90–100	—	417
Thin film	Mist-CVD	F	Up to $1.3 \times 10^{19}$	Up to 4.6	~10.4–16.13	240
Thin film	LPCVD	Ge	$10^{17}$ – $10^{19}$	—	—	237

As for another commonly applied n-type dopant in  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>, Sn is of great significance to obtain materials with high electron concentrations in practical applications. Sn is an effective dopant in the preparation of conductive Ga<sub>2</sub>O<sub>3</sub> single-crystals or epitaxial films. Sn prefers to replace Ga<sub>(2)</sub> and there are also localized defect states existing within the bandgap.<sup>231,232</sup> In the aspect of experiments, Du *et al.* obtained Sn-doped Ga<sub>2</sub>O<sub>3</sub> epitaxial film on  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>(100) substrates by MOCVD.<sup>233</sup> They found that the Sn content affected the structural, Raman, and

photoelectric properties of homoepitaxial thin films. That is, the films with varied Sn contents changed the electrical conductivity indeed. The lowest resistivity ( $1.20 \times 10^{-1} \Omega \text{ cm}$ ) and the highest Hall mobility ( $\sim 12.03 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$ ) of these homoepitaxial thin films were obtained for the 10% Sn-doped sample. Meanwhile, the bandgaps of these samples varied from 4.16 eV to 4.69 eV by tuning the Sn content from 1% to 12%. It has potential applications in the mainstream optoelectronic devices. Note that the carrier concentrations introduced by Sn



**Fig. 13** (a) Work function as a function of carrier density by calculation and KFM measurement in Si doped Ga<sub>2</sub>O<sub>3</sub>. Reproduced with permission.<sup>382</sup> Copyright 2016, American Institute of Physics Publishing. (b) Temperature dependence of the donor concentrations in the neutral charge state measured by EPR. The inset shows the schematic energy level of the DX center in this condition. Reproduced with permission.<sup>230</sup> Copyright 2016, AIP Publishing. (c) Hall free carrier concentrations as a function of the concentrations of Si and Sn doped β-Ga<sub>2</sub>O<sub>3</sub> single crystalline epitaxial layers obtained by secondary-ion mass spectrometry (SIMS). Reproduced with permission.<sup>383</sup> Copyright 2017, IOP Publishing. The transition level positions of (d) fourth, (e) fifth and (f) sixth period transition metal doped α-Ga<sub>2</sub>O<sub>3</sub>. Reproduced with permission.<sup>208</sup> Copyright 2021, IOP Publishing Ltd.

show the maximum value in a certain range, which is different from the Si dopant, as shown in Fig. 13(c). The measured effective Sn doping limits by secondary ion mass spectrometry (SIMS) are limited to 10<sup>17</sup>–10<sup>19</sup> cm<sup>-3</sup>. It is found that the addition of Sn atoms deteriorates the crystallization quality of the β-Ga<sub>2</sub>O<sub>3</sub> film constantly, thus reducing the efficiency of doping and having the doping limit.<sup>210</sup> This indicates that the doping concentrations will be limited when the ion radius of the dopant is larger than the radius of the host ion. Moreover, although the doping concentrations increase monotonously, the electron concentrations decrease so that the electronic properties of the film deviate from the expected situation. This phenomenon has also been observed in In<sub>2</sub>O<sub>3</sub>:Sn and SnO<sub>2</sub>:Sb thin films.<sup>234</sup> Notably, recent studies revealed that the Sn dopant did not exist only in the form of Sn<sup>4+</sup>. Sn exhibited two modes which were active mode and inactive mode in the Ga<sub>2</sub>O<sub>3</sub> film grown by MBE.<sup>235</sup> That is, Sn existed in the active mode as Sn<sup>4+</sup>, while it existed in the inactive mode as Sn<sup>2+</sup>, which has been investigated by X-ray absorption spectroscopy (XAS). This fresh phenomenon is worthy of further study.

Although Si, Sn, and Ge are all n-type dopants of Ga<sub>2</sub>O<sub>3</sub>, the host atom sites they substitute are not the same. Sn substitutes Ga<sub>(2)</sub> priorly when they are incorporated in Ga<sub>2</sub>O<sub>3</sub> as the donors, while Si and Ge will substitute Ga<sub>(1)</sub> sites. Therefore, Si and Ge introduce the relatively shallow level which results in the efficient activation at room temperature, while Sn introduces the deep level.<sup>236</sup> Although Si has a high activation rate, Ge will produce more carriers than Si to further increase the carrier concentrations in the systems when the doping concentration

of Ge is similar to that of Si. Meanwhile, the ionized Ge has a greater radius than that of the ionized Si, which matches the sizes of tetrahedrally coordinated Ga<sub>(1)</sub> in β-Ga<sub>2</sub>O<sub>3</sub>. Since Ge does not cause extra lattice distortion and leads to good crystal uniformity of β-Ga<sub>2</sub>O<sub>3</sub>, Ge also has a potential application in n-type doping in β-Ga<sub>2</sub>O<sub>3</sub>. In the actual doping engineering, Ahmadi *et al.* applied MBE to realize Ge doping in β-Ga<sub>2</sub>O<sub>3</sub>. The carrier concentrations could be increased up to 10<sup>20</sup> cm<sup>-3</sup>, and the carrier mobility was up to 120 cm<sup>2</sup> V<sup>-1</sup> s<sup>-1</sup>.<sup>150</sup> Besides, Ranga *et al.* and Alema *et al.* incorporated Ge into β-Ga<sub>2</sub>O<sub>3</sub> by LPCVD and MOCVD, respectively.<sup>236,237</sup> The carrier concentrations of Ge doped β-Ga<sub>2</sub>O<sub>3</sub> prepared by CVD reached up to 10<sup>20</sup> cm<sup>-3</sup>, and the carrier mobility was about 140 cm<sup>2</sup> V<sup>-1</sup> s<sup>-1</sup>, which indicated that the performance of the Ge doped β-Ga<sub>2</sub>O<sub>3</sub> epitaxial film prepared by the CVD method was comparable to that prepared by MBE. Although Ge has many advantages, Si and Sn are more preferred dopants in realizing n-type doped β-Ga<sub>2</sub>O<sub>3</sub> by using group IV<sub>A</sub> elements due to the low-cost and convenient doping technology.

In low-dimensional Ga<sub>2</sub>O<sub>3</sub>, Si, Ge, and Sn can also be used to increase the carrier concentrations. Since low-dimensional Ga<sub>2</sub>O<sub>3</sub> is mostly obtained by slicing it directly from the parent bulk Ga<sub>2</sub>O<sub>3</sub> by mechanical exfoliation, the variation of carrier concentrations after doping is closely related to that in the parent bulk Ga<sub>2</sub>O<sub>3</sub>. Meanwhile, Liu *et al.* confirmed that the Si, Ge, and Sn doping caused low-dimensional Ga<sub>2</sub>O<sub>3</sub> to behave as n-type Ga<sub>2</sub>O<sub>3</sub> by first-principles calculations.<sup>238</sup> Si, Sn, and Ge doped two-dimensional Ga<sub>2</sub>O<sub>3</sub> shifted the Fermi levels into the conduction band, indicating that these elements show donor

behaviors. Meanwhile, no impurity levels existed in the bandgaps of these systems. Note that, unlike the situations in bulk Ga<sub>2</sub>O<sub>3</sub>, Si, Ge, and Sn doping induced indirect-to-direct bandgap transition in low-dimensional Ga<sub>2</sub>O<sub>3</sub>. This transition arose from dopant-induced charge redistribution. The interaction between the dopant and neighboring O atoms affected the states' distribution of the highest valence level, thereby shifting the position of the VBM and leading to this phenomenon.

*VII<sub>A</sub> – F, Cl, Br, and I.* Halogens that can substitute oxygen (F<sub>O</sub>, Cl<sub>O</sub>, Br<sub>O</sub>, and I<sub>O</sub>) have been identified as shallow donor impurities. Konishi *et al.* discovered that the Ga<sub>2</sub>O<sub>3</sub> Schottky diode treated by HF had a high breakdown voltage and a relatively high barrier height (~1.5 eV).<sup>239</sup> Before depositing the metal, fluorine was incorporated into Ga<sub>2</sub>O<sub>3</sub> by HF treatment coupling with the post-annealing treatment. Then, F atoms tended to bond to the semiconductor surface and also tended to diffuse into the material during annealing. Because F tended to react with the ionized donor to form neutral complexes or act as negative ions to compensate n-type doping and further caused the surface loss. The surface depletion area was broadened to increase the breakdown voltage of the device. Besides, Shu *et al.* and Morimoto *et al.* proved that F could improve the conductivity of α-Ga<sub>2</sub>O<sub>3</sub> by first-principles calculations and experiments, respectively.<sup>240,241</sup> It was found that the conductivity could reach up to 16.13 S cm; thus it had potential applications in devices.

The halogen doped β-Ga<sub>2</sub>O<sub>3</sub> has potential applications in the area of photocatalytic decomposition of water.<sup>242</sup> The essence of this application is to modulate the energy position of the band edge in halogen atom doped β-Ga<sub>2</sub>O<sub>3</sub> so that it can better match the O<sub>2</sub>/H<sub>2</sub>O potential and H<sup>+</sup>/H<sub>2</sub> potential of H<sub>2</sub>O. It should be noted that the CBM of pure β-Ga<sub>2</sub>O<sub>3</sub> is lower than the H<sup>+</sup>/H<sub>2</sub> potential (0 eV) and the VBM is higher than the O<sub>2</sub>/H<sub>2</sub>O potential (1.23 eV). Compared with the intrinsic position of the CBM and VBM in β-Ga<sub>2</sub>O<sub>3</sub>, the F element does not modulate the intrinsic positions of the CBM and VBM. The Cl element reduces the CBM to 0.35 eV, and the VBM is increased by 0.13 eV. The CBM and VBM of Br doped β-Ga<sub>2</sub>O<sub>3</sub> are further reduced and elevated, respectively. The VBM of I-doped β-Ga<sub>2</sub>O<sub>3</sub> further decreases to close to the O<sub>2</sub>/H<sub>2</sub>O potential, while the CBM increases. Meanwhile, the bandgaps of these doped systems decrease from 4.50 eV to 2.64 eV with the increase of the number of periods. In conclusion, the photocatalytic reduction and/or oxidation abilities of Cl, Br and I doped β-Ga<sub>2</sub>O<sub>3</sub> are improved compared with pure Ga<sub>2</sub>O<sub>3</sub> and F doped Ga<sub>2</sub>O<sub>3</sub>, which has potential applications in the photocatalytic areas.

*Transition metals.* Transition metals can introduce more than one energy level into the semiconductors by doping due to multiple states of charge.<sup>208,243</sup> Much progress has been made in the research of transition metal doped β-Ga<sub>2</sub>O<sub>3</sub> in recent years. In addition to the unintentional dopants (*e.g.*, Ir) as mentioned before, the researchers have studied the transition metal by intentional doping to further improve the carrier concentrations expected in β-Ga<sub>2</sub>O<sub>3</sub>. Huang *et al.* investigated β-Ga<sub>2</sub>O<sub>3</sub> doped with V, W, Mo, Re, and Nb. They found that the

electronic properties of doped β-Ga<sub>2</sub>O<sub>3</sub> were altered.<sup>244,245</sup> Particularly, it was found that Nb would form the shallow donor level in β-Ga<sub>2</sub>O<sub>3</sub>. Zhou *et al.* proposed that the carrier concentrations could be modulated over the range of  $9.55 \times 10^{16}$ – $1.8 \times 10^{19}$  cm<sup>-3</sup> in Nb-doped β-Ga<sub>2</sub>O<sub>3</sub>.<sup>246</sup> The maximum mobility of the Nb-doped β-Ga<sub>2</sub>O<sub>3</sub> bulk was 182 cm<sup>2</sup> V<sup>-1</sup> s<sup>-1</sup>, which revealed the high transport properties. Shi *et al.* and Zhang *et al.* studied the effects of Nb doping on the properties of β-Ga<sub>2</sub>O<sub>3</sub> films by magnetron sputtering.<sup>246,247</sup> Furthermore, Shi *et al.* focused on the charge-trapping properties of Nb doped β-Ga<sub>2</sub>O<sub>3</sub> by obtaining the metal-oxide-nitride-oxide-silicon (MONOS) structure capacitor; they found that it had better charge-trapping properties with light doping concentrations.<sup>247</sup> However, the performance of the capacitor was deteriorative in heavy doping Nb concentrations. This was mainly related to the Nb out-diffusion degree and interface traps. Light Nb doping could generate more electron traps, while there were more hole traps at the interface with heavy doping. The increase of hole traps would lead to the decrease of the charge trapping capacity of the capacitors, which was reflected in the case of heavy Nb doping. In 2020, Chen *et al.* obtained the Nb-doped β-Ga<sub>2</sub>O<sub>3</sub> nanobelt by a mechanical exfoliation method and the bottom-gate FET was fabricated successfully. The concentration was ~10<sup>18</sup> cm<sup>-3</sup> and the mobility was in the range of 32.11–71.54 cm<sup>2</sup> V<sup>-1</sup> s<sup>-1</sup>. Therefore, the FET showed excellent performance. In addition to Nb, Ta doping was explored in 2019. The concentration and mobility of the Ta doped β-Ga<sub>2</sub>O<sub>3</sub> bulk were  $3.6 \times 10^{16}$ – $3.0 \times 10^{19}$  cm<sup>-3</sup> and 50–100 cm<sup>2</sup> V<sup>-1</sup> s<sup>-1</sup>, respectively. Besides, the d<sup>2</sup>s<sup>2</sup> group (*e.g.*, Hf and Zr) doped β-Ga<sub>2</sub>O<sub>3</sub> has also been studied in recent years. Zr tends to substitute octahedral Ga, and Zr doped β-Ga<sub>2</sub>O<sub>3</sub> has satisfactory mobility in degenerate systems. The mobility of Zr-doped β-Ga<sub>2</sub>O<sub>3</sub> is further improved to 112 cm<sup>2</sup> V<sup>-1</sup> s<sup>-1</sup>, while the maximum carrier concentration is only 10<sup>18</sup> cm<sup>-3</sup>.<sup>248,249</sup> Proper Hf can increase the carrier concentration in β-Ga<sub>2</sub>O<sub>3</sub> up to 10<sup>19</sup> cm<sup>-3</sup>, and the conductivity can reach about 200 cm<sup>2</sup> V<sup>-1</sup> s<sup>-1</sup>.<sup>250</sup> However, Hf and Zr are more expensive than Si; thus Hf and Zr are not optimal selection to obtain β-Ga<sub>2</sub>O<sub>3</sub> with high carrier concentrations normally.<sup>251</sup> Besides, it has been discovered that there are two defect levels located at  $E_c - 0.55$ – $0.60$  eV ( $E_1$ ) and  $E_c - 0.90$ – $1.1$  eV ( $E_3$ ) by DLTS and other measurements, respectively.<sup>191,192,252,253</sup> The origin of the defect levels at these two positions is speculated to be the transition metals. The deep levels do not play an obvious role in improving the conductivity in Ga<sub>2</sub>O<sub>3</sub>, and they may act as the trapped centers as discussed before.

Transition metals have also been applied in the doping engineering of metastable Ga<sub>2</sub>O<sub>3</sub> (*e.g.*, α-Ga<sub>2</sub>O<sub>3</sub>). For example, Wang *et al.* predicted variation laws of defect levels of electron-rich transition metal doped α-Ga<sub>2</sub>O<sub>3</sub> by first-principles calculations, and their positions are shown in Fig. 13(d–f).<sup>208</sup> They summarized that the transition level positions of electron-rich dopants selected from group III<sub>B</sub> to VIII<sub>B</sub> of the Periodic Table almost showed the “N”-shaped variation rule. That is, the transition levels went from deep to shallow at first, and then went into deep levels again. Finally, they went to relatively



shallow levels again. This was mainly due to the different types of chemical bonds between different subgroups and O atoms. If the dopants were selected from group IV<sub>B</sub> to V<sub>B</sub>, the ionic bonds were formed between O and the dopants with raised d-orbitals. On the other hand, if the dopants were selected from group VI<sub>B</sub> to VIII<sub>B</sub>, the covalent characteristics were observed between O and dopants with evident d-orbital splitting, because d orbitals contributed to the levels that were introduced. This was the main reason for the variation of the introduced levels. Note that the anomalous variation of Cr and Mn doped  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> in the fourth period was mainly due to the strong orbitals spin effect.

Besides, the transition metal atoms containing d orbitals can hybridize with O atoms, which makes the doped  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> exhibit special properties.<sup>208,254–256</sup> Due to the unique properties (e.g., multi-orbitals and special d-orbitals), the magnetic and luminescence properties of  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> will be affected, which will be described later.

**3.2 Deep acceptors.** Although the availability of n-type doping in  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> can be fulfilled and succeeded, p-type doping has been a troublesome problem in  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> doping engineering. There are three kinds of important issues that should be faced in p-type doping in Ga<sub>2</sub>O<sub>3</sub>. On the one hand, holes are always predicted to be self-trap holes, resulting in the holes that prefer to form small polarons at O sites rather than free carriers. On the other hand, the dispersion degree of the valence band is small and the energy distribution of the VBM is flat; thus the effective mass of the hole is large. In addition, the high concentrations of background carriers in Ga<sub>2</sub>O<sub>3</sub> make even the small number of holes introduced by the ionized acceptor immediately compensated. Thus, it is difficult to obtain the effective p-type Ga<sub>2</sub>O<sub>3</sub> by doping with potential acceptors, which can also be discovered in other wide bandgap oxide semiconductors.<sup>257</sup> Furthermore, this is becoming one of the factors which hinder the further applications of Ga<sub>2</sub>O<sub>3</sub> as the basis for high-quality semiconductor materials in complementary metal-oxide-semiconductor (CMOS) technology.

In this section, the research progress of some potential acceptor dopants is reviewed, and the effects of some electron-poor metal or non-metal dopants are mainly introduced here. Since effective p-type low-dimensional Ga<sub>2</sub>O<sub>3</sub> cannot be realized by substitution doping, the internal mechanism is similar to that in bulk materials. Therefore, this section mainly discusses the situation in bulk Ga<sub>2</sub>O<sub>3</sub>, while it will not be repeated in low-dimensional Ga<sub>2</sub>O<sub>3</sub>.

**Mg.** Magnesium, which has one less valence electron than Ga, can be an acceptor dopant theoretically. Mg has been proved to be an effective acceptor dopant in other wide bandgap semiconductors (e.g., GaN) in the early research. Although Mg formed complexes with H easily, Hiroshi Amano *et al.* realized Mg doped p-type GaN materials by low-energy electron beam irradiation (LEEEBI) successfully.<sup>258–260</sup> Inspired by this, Mg doped  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> was synthesized by Qian *et al.*<sup>261</sup> Combined with the post-annealing treatment, the doped  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> thin films with various Mg concentrations (i.e., 4.92 at%, 6.88 at%,

and 8.58 at%) were fabricated by magnetron sputtering. The Fermi level of the Mg doped  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> thin film was close to the valence band, indicating a weak p-type characteristic. However, Chikoidze *et al.* proposed that the acceptor level introduced by Mg was more than 1 eV away from the VBM, indicating that it may be a deep level impurity by Hall and photoemission measurements.<sup>262</sup> To understand the internal mechanism of the Mg's effects, the polaron model was built to explain this phenomenon theoretically.<sup>263</sup> By the results of the Koopmans-compliant hybrid functional analysis of the defect levels, Mg would introduce an acceptor level corresponding to a small polaron, which would be formed at the O<sub>(1)</sub> site near the Mg atom. In addition, it has been found that Mg compensates the background carriers of Ga<sub>2</sub>O<sub>3</sub> to reduce the background carrier concentrations. Therefore, the resistivity of the Mg doped Ga<sub>2</sub>O<sub>3</sub> substrate will be further increased, thus transforming into an insulating substrate gradually.

**Fe.** Fe is considered to be the effective compensation dopant in group-III semiconductors, and especially Fe doped  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> is expected to increase the resistance of the  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> bulk and film. Because Fe and Ga<sub>(2)</sub> have the same valence state and their ionic radii are very close ( $r_{(\text{Ga}^{3+})} = 0.062 \text{ nm} \approx r_{(\text{Fe}^{3+})} = 0.064 \text{ nm}$ ), Fe will substitute Ga<sub>(2)</sub> preferentially.<sup>264</sup> The defect level of Fe acts as the recombination center or capture center to compensate the unintentional electrons and holes. The mechanism of trap centers capturing carriers is shown in Fig. 14(a).<sup>264</sup> By capturing electrons (holes), the valence state of Fe<sup>3+</sup> is lowered to Fe<sup>2+</sup> (raised to Fe<sup>4+</sup>), which affects the background carrier concentrations. Meanwhile, the behavior of Fe doping does not promote the generation of other dense traps associated with Fe.<sup>265,266</sup> Therefore, Fe doped  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> realizes the semi-insulating substrate and the current blocking layer. The carrier concentrations of Fe doped  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> are decreased to 10<sup>15</sup>–10<sup>16</sup> cm<sup>-3</sup> gravely, and thus it can be applied as a semi-insulating substrate in power devices.<sup>265</sup> The semi-insulating substrates of Fe doped  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> are commercially available nowadays. The Fe dopant concentrations are about 10<sup>18</sup> cm<sup>-3</sup> in these substrates to compensate background carriers and pin the Fermi level.<sup>265,267,268</sup>

Based on this, homogeneous epitaxial doped  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> films on Fe doped semi-insulating substrates have many advantages compared with heterogeneous epitaxial doped  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> films, e.g., smooth surface (RMS < 0.5), high carrier concentrations (~10<sup>20</sup> cm<sup>-3</sup>) and electrical conductivity ( $\mu_{\text{max}} = 2323 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$ ), low defects, good lattice match with the substrates, *etc.*<sup>269</sup> Therefore, homogeneous epitaxial thin films based on Fe doped semi-insulating substrates are widely applied in power devices. In addition, selecting the appropriate gate oxide dielectric material is crucial in the applications of FETs, because the lattice mismatch existing between the gate dielectric layer and the Ga<sub>2</sub>O<sub>3</sub> channel layer may further deteriorate the electronic performance of the interface. Huang *et al.* proposed that the homoepitaxial Fe doped  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> layer had the potential to be a high-insulated gate dielectric material, which improved the electronic performance of Ga<sub>2</sub>O<sub>3</sub> FETs.<sup>270</sup>

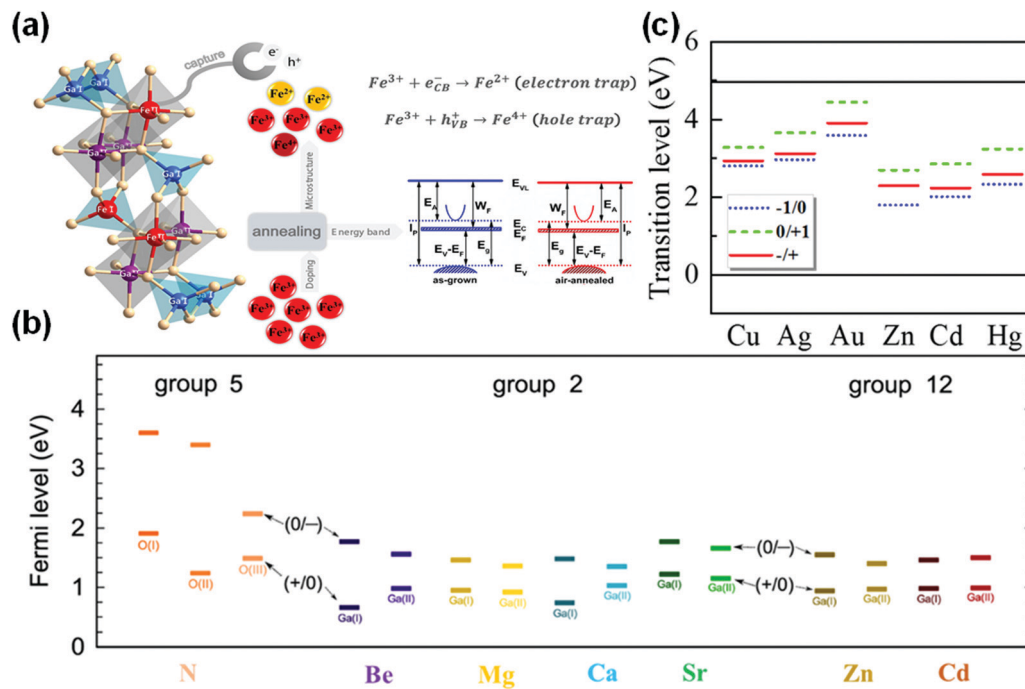


Fig. 14 (a) Schematic diagram of variations of the valence state of Fe in Fe doped  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>. Reproduced with permission.<sup>264</sup> Copyright 2021, Springer Science and Business Media, LLC, part of Springer Nature 2021. (b) The transition levels of N, Be, Mg, Ca, Sr, Zn, and Cd doped  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>. Reproduced with permission.<sup>276</sup> Copyright 2018, IOP Publishing Ltd. (c) The transition levels of I<sub>B</sub> and II<sub>B</sub> group transition metal doped  $\alpha$ -Ga<sub>2</sub>O<sub>3</sub>. Reproduced with permission.<sup>208</sup> Copyright 2021, IOP Publishing Ltd.

They grew Fe-doped  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> films on sapphire substrates by Laser-MBE and investigated the resistance of the samples at different substrate temperatures. The resistances of these samples were on the order of G $\Omega$ . The variation of resistance was modulated by the Fe<sup>3+</sup>/Fe<sup>2+</sup> ratio, that is, when the Fe<sup>3+</sup>/Fe<sup>2+</sup> ratio decreased, the resistance would increase. Compared with pure  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>, the resistance of Fe doped Ga<sub>2</sub>O<sub>3</sub> increased significantly, showing the properties of high insulation. Therefore, it was expected that this approach would be worth trying in the fabrication of dielectric layers in the FETs in the future.

**Zn and Cu.** Zn has one less valence electron than Ga, and thus it can be used as an acceptor dopant. Zn-doped  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> has been extensively studied because the radius of Zn<sup>2+</sup> is close to that of Ga<sup>3+</sup>; thus large lattice distortion will not be introduced during doping.<sup>209,271–275</sup> Therefore, Zn is an ideal dopant for obtaining p-type  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>. However, theoretical research seems to refuse this conclusion. Lyons *et al.* obtained the positions of the Zn-doped  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>'s defect levels by first-principles calculations, as shown in Fig. 14(b).<sup>276</sup> Obviously, the position of the defect level was far from the VBM ( $\Delta E > 1$  eV). Therefore, the defect level introduced by Zn was a deep level, which had little effect on the acquisition of p-type  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>. Considering the difficulty of realizing effective p-type  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> discussed before, Chikoidze *et al.* proposed a new method.<sup>277</sup> They reduced the mean free path of the carriers by incorporating Zn and then obtained p-type  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> with an ultra-high breakdown electric field (13.2 MV cm<sup>-1</sup>), which provided an important reference for the acquisition of

homogeneous bipolar devices with high breakdown electric field subsequently.

In general, considering that the low doping concentrations will introduce the deep level in the bandgap, the high acceptor-doping concentrations promote the introduced acceptor level close to the valence band. This is considered to be another strategy to realize effective p-Ga<sub>2</sub>O<sub>3</sub>. Nevertheless, such a method is unsuccessful in the Zn doped  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>. When the concentration of Zn decreases to  $\sim 1.5\%$ , deep levels are introduced and p-Ga<sub>2</sub>O<sub>3</sub> cannot be obtained.<sup>218,278</sup> When the doping concentration increases up to  $\sim 2\%$ , Zn has negligible change in the basic band structure. It just reduces the bandgap and introduces impurity absorption peaks in the longwave range.<sup>279</sup> The p-Ga<sub>2</sub>O<sub>3</sub> is not realized again. When the concentration of Zn increases up to  $\sim 4\%$ , Zn introduces a shallow level of  $\sim 0.3$  eV up to the valence band.<sup>108</sup> The reason is that the concentrations of V<sub>O</sub> decrease when the concentration of the Zn component increases.<sup>280</sup> The introduction of Zn into  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> as the acceptor dopant compensates the background electrons and reduces the electron concentrations. Although the acceptor level is shallower than that in the condition of low doping concentrations, effective p-type  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> has not been obtained yet. This is mainly due to the large background carrier concentrations caused by unintentional doping. Moreover, with the increase of the Zn component concentration, the Burstein–Moss effect will occur, which modulates the optoelectronic properties.

Compared with Zn, the valence electrons of Cu are fewer, which may be easy to realize p-type doping in Ga<sub>2</sub>O<sub>3</sub>. Yan *et al.*

found that Cu introduced two acceptor impurity levels near the VBM and produced 100% spin polarization near the Fermi level.<sup>281</sup> P-Ga<sub>2</sub>O<sub>3</sub> could be realized by Cu in this research. On the other hand, Kyrtsov *et al.* found that Cu was not an effective acceptor, which was different from the previous research.<sup>218</sup> It would introduce deep acceptor levels in β-Ga<sub>2</sub>O<sub>3</sub>, which was not beneficial to practical device applications. Meanwhile, it should be noticed that Cu-doped β-Ga<sub>2</sub>O<sub>3</sub> will hinder the grain growth, thus deteriorating the crystallinity of the doping systems.<sup>282,283</sup> In order to realize a high-quality Cu doped Ga<sub>2</sub>O<sub>3</sub> single wafer, Galazka *et al.* recently attempted to synthesize Cu doped Ga<sub>2</sub>O<sub>3</sub> by the CZ method but it was in vain.<sup>232</sup> The failure of the experiment was caused by excess Cu evaporation. After analyzing the reasons for the failure, Jesenovc *et al.* improved the CZ method and the VGF method to fabricate the high-quality Cu doped Ga<sub>2</sub>O<sub>3</sub> single crystal successfully.<sup>284</sup> Then they discovered the fresh phenomenon that Cu-doped β-Ga<sub>2</sub>O<sub>3</sub> had a photodarkening effect. They combined theoretical results with experimental conclusions to reveal the internal mechanism. That is, the EPR results revealed that Cu<sup>2+</sup> would transform to Cu<sup>3+</sup> under light exposure, which was a rare oxidation state of Cu. After Cu was introduced into the Ga<sub>2</sub>O<sub>3</sub> single crystal, it would form complexes with unintentional dopants (*i.e.*, H<sub>i</sub> or H<sub>o</sub>). When the Cu<sub>Ga</sub>-H<sub>o</sub> complex absorbed external light, H would be released resulting in the formation of Cu<sup>3+</sup> and O-H modes.

In addition to more research in Zn and Cu doping in β-Ga<sub>2</sub>O<sub>3</sub>, related studies have also been carried out in other metastable phases, but they are few. Recently, aiming to further reveal the effects of the transition metals (I<sub>B</sub> and II<sub>B</sub>) on the electronic properties of α-Ga<sub>2</sub>O<sub>3</sub>, Wang *et al.* made theoretical predictions on Zn and Cu group doped α-Ga<sub>2</sub>O<sub>3</sub>.<sup>208</sup> Different from the traditional deep level defects, they found that Cu and Zn would form an AX center in α-Ga<sub>2</sub>O<sub>3</sub>, as shown in Fig. 14(c). As a deep-level defect similar to the DX center, the AX center limits the maximum free carrier concentrations in the host material.<sup>285–287</sup> The AX centers are the first found in doped α-Ga<sub>2</sub>O<sub>3</sub>, and it is considered to be an important reason for hindering the acquisition of p-type α-Ga<sub>2</sub>O<sub>3</sub>.

*Bi.* As mentioned above, effective p-type doping in Ga<sub>2</sub>O<sub>3</sub> by general acceptor dopants is difficult to form, and they tend to form localized holes. Traditionally, the acceptor dopant is considered according to its outer electrons, that is, the element with fewer extranuclear electrons than the host element is generally selected as the acceptor dopant. However, the appearance of Bi<sub>2</sub>O<sub>3</sub> provides a new idea for p-type doping in semiconductors.<sup>288</sup> The feature of this p-type oxide is that the *s* orbitals of Bi will hybridize with the O orbitals when the compound is formed. Then as a consequence of hybridization a low acceptor level is introduced in the bandgap. Inspired by this, Sabino *et al.* studied β-Ga<sub>2</sub>O<sub>3</sub> doped by Bi with filled *s* orbitals systematically.<sup>289,290</sup> By increasing the concentrations of the Bi element, they found that the acceptor level further decreased, as shown in Fig. 15(a). The specific feasibility needs to be confirmed by subsequent related experiments.

*N.* The number of valence electrons of N is one less than that of O, and the radius of N<sup>3-</sup> is close to that of O<sup>2-</sup>. The lattice distortion degree caused by the addition of N is small. Therefore, it is considered as an ideal non-metallic acceptor. The realization of p-Ga<sub>2</sub>O<sub>3</sub> doped by N has been one of the hot topics that scholars are interested in. Early studies focused more on the optimized preparation and luminescence characteristics in N-doped Ga<sub>2</sub>O<sub>3</sub> nanowires, because the N element can modulate the electronic structure of β-Ga<sub>2</sub>O<sub>3</sub> and introduce defect levels in the bandgap, thus achieving tunable light emission. Meanwhile, good crystal quality, smooth surface, variable bandgap (4.75–4.88 eV), and high visible light transmittance (>80%) Ga<sub>2</sub>O<sub>3</sub> nanowires can be obtained by optimizing the film thickness and annealing conditions.<sup>291–294</sup> These characteristics can make N-doped Ga<sub>2</sub>O<sub>3</sub> applied in transparent electronics such as transparent conductive electrodes. Although the N atom is considered as a potential acceptor, it is found that the defect levels which the N substituted O host atom introduces are deep levels ( $\Delta E > 2$  eV).<sup>104</sup> In addition, the p-type characteristics of the N doped β-Ga<sub>2</sub>O<sub>3</sub> are not obvious, and the main reason is that N doping often couples with some vacancies. Dong *et al.* found that the defects of N<sub>O</sub>V<sub>O</sub> were stable under Ga-rich conditions.<sup>295</sup> These donor defects converted N-doped β-Ga<sub>2</sub>O<sub>3</sub> into a weak n-type β-Ga<sub>2</sub>O<sub>3</sub>. That is, even if holes were generated after N incorporation, these excess holes would be compounded by electrons generated due to intrinsic defects (*i.e.*, V<sub>O</sub>). Meanwhile, they found that the intrinsic absorption edge would red-shift in N-doped β-Ga<sub>2</sub>O<sub>3</sub> coupling with vacancies. Moreover, an extra peak was generated in the low-energy region (1.23 eV). The origin of this peak was related to the recombination of electrons trapped by donors due to V<sub>O</sub> and holes trapped by acceptors due to N doping, which verified the red-light emission observed in the early experiments.<sup>296</sup> Recently, Fang *et al.* proposed a new approach to obtain p-type Ga<sub>2</sub>O<sub>3</sub> by N-doping, and they prepared a solar-blind photodetector based on this.<sup>297,298</sup> That is, they proposed that GaN on the sapphire was oxidized into different components of GaN<sub>x</sub>O<sub>3(1-x)/2</sub> thermally in a modified CVD system. This was caused by an energy-driven multi-step structural phase transition mechanism. It led to partial oxidation and phase transition in GaN, which was equivalent to doping Ga<sub>2</sub>O<sub>3</sub> with N. Based on this process, the hole concentrations and mobility of GaN<sub>x</sub>O<sub>3(1-x)/2</sub> reached up to 10<sup>16</sup> cm<sup>-3</sup> and 41.4 cm<sup>2</sup> V<sup>-1</sup> s<sup>-1</sup>, respectively. However, the hole concentrations and conductivity were still very low, and the electronic performance was far less than that in n-type Ga<sub>2</sub>O<sub>3</sub>. In addition, it was difficult to control the phase transition and doping concentrations of N atoms accurately, which led to complex process implementation. Therefore, it still needs more work to carry out and optimize in this aspect.

Besides, N-doped β-Ga<sub>2</sub>O<sub>3</sub> has also been widely applied in power devices. The β-Ga<sub>2</sub>O<sub>3</sub> layer implanted with N is annealed at a temperature over 1100 °C because such a temperature helps activate the implanted N atoms. The holes generated by N atom incorporation can compensate the background carriers in β-Ga<sub>2</sub>O<sub>3</sub>. This gives rise to the energy barrier in electron

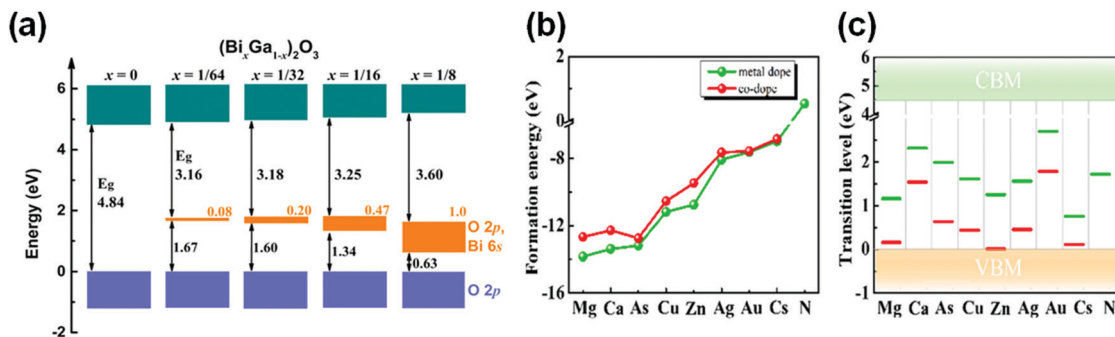


Fig. 15 (a) Schematic representation of the effects of Bi concentrations ( $x = 1/48, 1/24, 1/16,$  and  $1/8$ ) on the defect level position in  $(\text{Ga}_{1-x}\text{Bi}_x)_2\text{O}_3$ . Reproduced with permission.<sup>290</sup> Copyright 2021, American Physical Society. (b) The formation energies and (c) the acceptor levels of single metal doped and (electron-poor metal, N) co-doped  $\beta\text{-Ga}_2\text{O}_3$ . Reproduced with permission.<sup>209</sup> Copyright 2021, Elsevier Ltd.

movement, which further blocks the vertical flow of current effectively. Therefore, N-doped  $\beta\text{-Ga}_2\text{O}_3$  acts as a current blocking layer in depletion-mode vertical Metal-Oxide-Semiconductor Field Effect Transistors (MOSFETs) and as a field-plate (or guard ring) in vertical  $\beta\text{-Ga}_2\text{O}_3$  Schottky barrier diodes.<sup>299–301</sup>

The defect levels introduced by Be, Ca, Sr, and Cd have also been investigated by DFT.<sup>276</sup> Compared with N, these defect levels are relatively close to the valence band but they are still deep levels as shown in Fig. 14(b).

**3.3 Co-doping.** The solubility and activation rate of the dopants are also the fundamental factors which determine the doping effectiveness. The concentrations and activation rates of dopants in  $\text{Ga}_2\text{O}_3$  are often limited, especially in the p-type doping process as discussed in the previous section. At the same time, some doped atoms couple with the defects, which further hinders the realization of p-type doping. The solubility of acceptor dopants in host crystals is generally low. The co-doping strategy is proposed in this situation. Partial co-doping methods have increased the dopant solubility and the activation rate and lowered the ionization energy. For example, the maximum hole concentration in Mg doped GaN is about  $10^{17} \text{ cm}^{-3}$ .<sup>302</sup> The hole concentrations increase by an order of magnitude when O atoms are co-doped with Mg atoms. Inspired by this phenomenon, several co-doping approaches, in particular, electron-poor metal dopant co-doping with the N dopant, have been tried in  $\beta\text{-Ga}_2\text{O}_3$ .<sup>209</sup> Zhang *et al.* found that the formation energy of N-doped  $\beta\text{-Ga}_2\text{O}_3$  could be reduced by (Zn, N) co-doping. This confirms that the co-doping method improves the solubility of N-doping, which is similar to that in GaN. Meanwhile, compared with only one acceptor level in N doped  $\beta\text{-Ga}_2\text{O}_3$  ( $E - E_{\text{VBM}} = 0.761 \text{ eV}$ ), two acceptor levels are introduced in the bandgap in N-Zn co-doped  $\beta\text{-Ga}_2\text{O}_3$  ( $E_1 - E_{\text{VBM}} = 0.149 \text{ eV}$ ,  $E_2 - E_{\text{VBM}} = 0.483 \text{ eV}$ ).<sup>303</sup> However, the underlying mechanism was not unveiled yet. Inspired by previous studies on ZnO, the shallow acceptor level of ZnO can be obtained by co-doping (electron-rich cation, electron-poor anion) due to the donor-acceptor level rejection.<sup>304</sup> Meanwhile the acceptor level position can be reduced by co-doping from the perspective of molecular orbital theory. Yan *et al.* used some electron-poor cations containing p and d orbitals to replace Ga, and they used an N atom to substitute O in  $\beta\text{-Ga}_2\text{O}_3$ , as shown

in Fig. 15(b and c).<sup>209</sup> The acceptor levels reduced significantly because co-doping further moved the Ga–O bonding orbitals up and moved the dopant–O antibonding orbitals coupling with the unoccupied p orbitals of N and O ions down by using the (metal, N) co-doping method instead of pure metal doping.<sup>305</sup> Besides, Ma *et al.* investigated the co-doping of Al–N and In–N, and found that the formation energy was reduced and the acceptor levels were close to the valence band.<sup>306</sup> Since the acceptor level of the In–N co-doping system was closer to the VBM, they further used the In atom for co-doping with more N atoms, and found that the acceptor levels were closer to the valence band compared with the single N atom. That is, increasing the concentration of N is more favorable for obtaining p-type  $\beta\text{-Ga}_2\text{O}_3$ . In the case of non-metallic doping only, N–P co-doping has also been found theoretically to be possible to form p-type  $\beta\text{-Ga}_2\text{O}_3$  with high hole concentrations.<sup>307</sup> From this, the co-doping research studies in  $\beta\text{-Ga}_2\text{O}_3$  are not only beneficial for obtaining p-type  $\beta\text{-Ga}_2\text{O}_3$ , but can also provide a guideline for obtaining other phases of p-type  $\text{Ga}_2\text{O}_3$ . Therefore, the research on co-doping is worthy of further related theoretical and experimental research in-depth.

**3.4 Surface passivation.** The  $\text{Ga}_2\text{O}_3$  bulk is a three-dimensional material, and it has a large number of internal defects and surface defects. Although it is different from materials with a layered structure,  $\text{Ga}_2\text{O}_3$  can be easily exfoliated into a quasi two-dimensional (quasi 2D) structure with a large surface area. Note that the dangling bonds existing on the surface of exfoliated  $\text{Ga}_2\text{O}_3$  form surface states. These surface states will affect the performance of  $\text{Ga}_2\text{O}_3$  materials and devices seriously. For example, they affect the carriers' transport around the surface and the injection of carriers by limiting the interface resistance due to the Fermi pinning effect. Meanwhile, the quasi 2D  $\text{Ga}_2\text{O}_3$  without passivation has other disadvantages, *e.g.*, inconspicuous quantum confinement effects, inconspicuous bandgap variation, instability, *etc.* Therefore, some impurity atoms should be selected for surface treatment to saturate the dangling bonds on the surface of unpassivated quasi 2D  $\text{Ga}_2\text{O}_3$ .

It is found that the electronic properties of the bulk  $\text{Ga}_2\text{O}_3$  will be modulated by the surface treatment and impurity absorption in the research of surface treatment on the bulk



Ga<sub>2</sub>O<sub>3</sub> material. For example, Yang *et al.* investigated the bulk Ga<sub>2</sub>O<sub>3</sub> materials after surface treatment such as plasma treatment (CF<sub>4</sub> and O<sub>2</sub>), gaseous treatment (ultraviolet/O<sub>3</sub>), and liquid treatment (HCl, H<sub>2</sub>O<sub>2</sub>, *etc.*).<sup>308,309</sup> The experimental results about the surface of Ga<sub>2</sub>O<sub>3</sub> absorbed by the different impurities showed that different surface treatments had different effects on the electronic properties (*e.g.*, Schottky barrier height, *etc.*) of bulk Ga<sub>2</sub>O<sub>3</sub>. The results of *I-V* and *C-V* tests showed that the Schottky barrier height decreased and the ideal factor increased under plasma treatment, and the reverse characteristics of diodes based on Ga<sub>2</sub>O<sub>3</sub> deteriorated. The other two treatments did not deteriorate the electronic properties of the near-surface in Ga<sub>2</sub>O<sub>3</sub>. Considering that low-dimensional materials will be sensitive to surface treatment, it is significant to investigate the surface passivation of the unpassivated Ga<sub>2</sub>O<sub>3</sub> for the preparation of high-performance devices based on Ga<sub>2</sub>O<sub>3</sub>.

As for low-dimensional wide bandgap semiconductors, the common approach is to use hydrogen or halogen functional groups for passivation to modulate the electronic properties. This strategy can further improve optoelectronic properties and material stability.<sup>26,60</sup> In addition, the semi-saturated and full saturated functionalization can enhance thermodynamic stability and electron transport performance. As discussed in the previous section, Fig. 9(e–g) shows the PDOS of H passivated low-dimensional monolayer Ga<sub>2</sub>O<sub>3</sub>. Note that the VBM is mainly contributed by O 2p orbitals coupling with Ga 4p and H 1s orbitals.<sup>21,27</sup> It is obvious that the charges are still localized near the O atom in the VBM of the H passivated low-dimensional Ga<sub>2</sub>O<sub>3</sub>, as shown in Fig. 9(i). The charges at the CBM are delocalized, which is the same condition in bulk Ga<sub>2</sub>O<sub>3</sub>. Meanwhile, it can be concluded that the contribution of the H 1s orbital to the VBM is larger than that of the CBM by comparing the contribution of adsorbed H atoms to the CBM and VBM of low-dimensional Ga<sub>2</sub>O<sub>3</sub>. That is, the surface passivated impurity atoms have taken part in the formation and modulation of the band structure of low dimensional Ga<sub>2</sub>O<sub>3</sub>. Considering this, one inspiration is that surface functionalization can modulate the electronic properties by passivating different atoms for application in low-dimensional Ga<sub>2</sub>O<sub>3</sub>. It is similar to passivation modification of surface functional groups. Meanwhile, in realizing the modulating properties of impurity doping in low-dimensional materials, surface passivation is first applied because doping methods such as ion implantation cannot accurately control the doping concentrations when materials are exfoliated to the low-dimensional structure.<sup>310</sup> The general process of passivation is shown in Fig. 16(a) schematically. The sliced monolayer Ga<sub>2</sub>O<sub>3</sub> is exposed to a halogen-rich ambient condition for surface absorption and passivation. The schematic structures after passivation by halogen atoms are shown in Fig. 16(b). Then, Guo *et al.* investigated the effects of passivation with F, Cl, and H separately and in pair combinations (F–F, F–Cl, F–H, Cl–H, and Cl–Cl) on the electronic properties of monolayer Ga<sub>2</sub>O<sub>3</sub>.<sup>63,108</sup> Fig. 16(c) shows that halogen atom (F and Cl) passivation can change the band structure of monolayer Ga<sub>2</sub>O<sub>3</sub>

directly from the indirect bandgap to the direct bandgap compared with H passivation. Meanwhile, the electronic properties of low dimensional Ga<sub>2</sub>O<sub>3</sub> passivated by F and Cl are also different. Although F-passivated low dimensional Ga<sub>2</sub>O<sub>3</sub> has higher stability than Cl-passivated Ga<sub>2</sub>O<sub>3</sub>, it is unfortunate that the transport properties of low dimensional Ga<sub>2</sub>O<sub>3</sub> passivated by F further deteriorate. It has been discovered that the monolayer ClGa<sub>2</sub>O<sub>3</sub>H shows a hole mobility of 3913.52 cm<sup>2</sup> V<sup>-1</sup> s<sup>-1</sup> along the *b* direction, which is the highest value among the passivated samples (as shown in Fig. 17(a and b)). Although Cl passivation can reduce the electron effective mass of low dimensional Ga<sub>2</sub>O<sub>3</sub> effectively, the anisotropy in material properties makes the transport situations disparate in different directions. It is noticed that the electron mobility along the *b* direction is reduced, while the electron mobility along the *c* direction is increased. Cl passivated monolayer Ga<sub>2</sub>O<sub>3</sub> demonstrates high hole and electron mobility and a direct band structure, which can be the theoretical guideline to obtain the higher performance devices compared with F and H passivated monolayer Ga<sub>2</sub>O<sub>3</sub>.

#### 4. Homo-valence impurities (Al and In)

In addition to the hetero-valence doping methods mentioned above, the same group elements (*i.e.*, homo-valence elements) incorporated into semiconductors to form alloys have special phenomena and applications, *e.g.*, Al<sub>x</sub>Ga<sub>1-x</sub>N (*x* = 0–100%), In<sub>x</sub>Ga<sub>1-x</sub>N (*x* = 0–100%) and GaN. The crystal structure of AlN and InN applied in GaN alloy engineering is the same as that of GaN, which will not lead to phase separation during doping. Meanwhile, the valence electrons of Al, Ga, and In atoms are equal so that no impurity states will be introduced into the systems during doping. Besides, the bandgap can also be modulated when GaN is alloyed with AlN and/or InN. Since the *E<sub>g</sub>* of AlN is 6.2 eV (~200 nm) and that of InN is 0.7 eV (~1771 nm), the luminescence area of the Al<sub>x</sub>Ga<sub>1-x</sub>N and In<sub>x</sub>Ga<sub>1-x</sub>N alloys can cover from the infrared region to the deep ultraviolet region by controlling the proportion of the doping component.<sup>311</sup> GaN alloy engineering has been applied to HEMTs, ultraviolet photodetectors, and LEDs by modulating bandgap and energy level matching to improve device performance. Inspired by this research, the Ga<sub>2</sub>O<sub>3</sub> alloy engineering, *i.e.*, (Al<sub>x</sub>Ga<sub>1-x</sub>)<sub>2</sub>O<sub>3</sub> and (In<sub>x</sub>Ga<sub>1-x</sub>)<sub>2</sub>O<sub>3</sub>, can also be realized, which will provide a new idea for the application of Ga<sub>2</sub>O<sub>3</sub> in heterojunction modulation doped field effect transistors (MODFETs) and solar-blind ultraviolet photodetectors.

In this section, (Al<sub>x</sub>Ga<sub>1-x</sub>)<sub>2</sub>O<sub>3</sub> and (In<sub>x</sub>Ga<sub>1-x</sub>)<sub>2</sub>O<sub>3</sub> alloys are discussed here. The effects of the contents of homo-valence elements on the lattice parameters and bandgap of the alloys and the phase separation phenomenon in the alloys are discussed. Finally, the applications of the (Al<sub>x</sub>Ga<sub>1-x</sub>)<sub>2</sub>O<sub>3</sub> and (In<sub>x</sub>Ga<sub>1-x</sub>)<sub>2</sub>O<sub>3</sub> alloys in power devices and optoelectronic devices are introduced briefly to further illustrate the value of alloy engineering realized in Ga<sub>2</sub>O<sub>3</sub>.

**4.1 (Al<sub>x</sub>Ga<sub>1-x</sub>)<sub>2</sub>O<sub>3</sub>.** The stable phase of Al<sub>2</sub>O<sub>3</sub> is a corundum structure rather than a monoclinic structure. In corundum Al<sub>2</sub>O<sub>3</sub>, both Al and O atoms form the [AlO<sub>6</sub>] octahedral configurations. Different from that, the positions occupied by [AlO<sub>6</sub>]



Fig. 16 (a) The schematic diagram of exfoliated and passivated processes to obtain low-dimensional Ga<sub>2</sub>O<sub>3</sub>. Reproduced with permission.<sup>384</sup> Copyright 2020, the Royal Society of Chemistry. (b) The geometric structures of monolayer HGa<sub>2</sub>O<sub>3</sub>H, ClGa<sub>2</sub>O<sub>3</sub>H/FGa<sub>2</sub>O<sub>3</sub>H, and ClGa<sub>2</sub>O<sub>3</sub>Cl/FGa<sub>2</sub>O<sub>3</sub>F/ClGa<sub>2</sub>O<sub>3</sub>Cl. (c) The band structure of hydrogen- and halogen-passivated monolayer  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>. Reproduced with permission.<sup>27</sup> Copyright 2020, Elsevier Ltd.

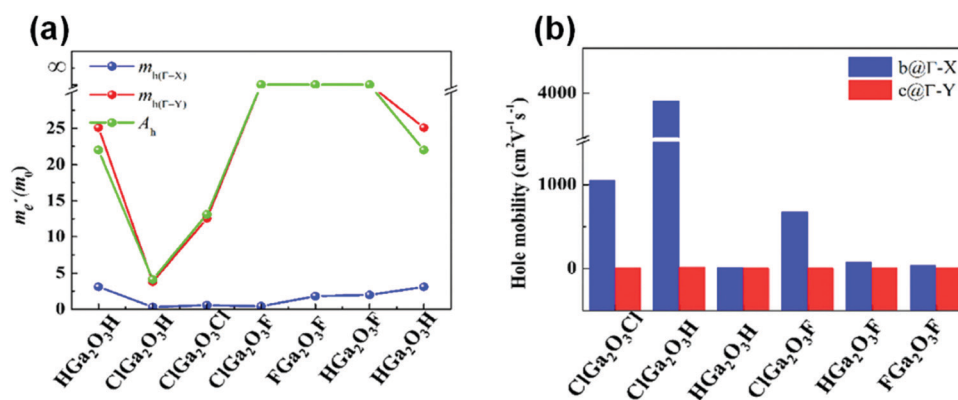


Fig. 17 (a) Effective hole masses and (b) hole mobility of different H/halogen passivated monolayer Ga<sub>2</sub>O<sub>3</sub> along b ( $\Gamma$ -X) and c ( $\Gamma$ -Y) directions. Reproduced with permission.<sup>27</sup> Copyright 2020, Elsevier Ltd.

octahedral configurations and [AlO<sub>4</sub>] tetrahedral configurations are bisected in the monoclinic Al<sub>2</sub>O<sub>3</sub>. The Al atom will occupy the octahedral position preferentially to form  $\beta$ -(Al<sub>x</sub>Ga<sub>1-x</sub>)<sub>2</sub>O<sub>3</sub> when Al atoms are incorporated into  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>. Note that phase separation will occur because the most stable structure of Al<sub>2</sub>O<sub>3</sub> is not the same as that of  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>. Therefore, the related Al

content is worth noting when the phase separation appears. Although the critical components obtained by different preparation methods are different, the substitution mechanism and varied tendency of Al doped  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> are the same. Fig. 18(a) shows the formation enthalpy variation of different structures of the  $\beta$ -(Al<sub>x</sub>Ga<sub>1-x</sub>)<sub>2</sub>O<sub>3</sub> alloy with different Al contents

( $x = 0-100\%$ ). The monoclinic structure of the  $\beta\text{-(Al}_x\text{Ga}_{1-x})_2\text{O}_3$  alloy remains at low Al content ( $x < 0.5$ ). Note that the formation enthalpy of the  $(\text{Al}_x\text{Ga}_{1-x})_2\text{O}_3$  alloy is the lowest under the monoclinic structure when  $x = 0.5$ . Al has substituted all the  $\text{Ga}_{(2)}$  in  $\beta\text{-Ga}_2\text{O}_3$  in this condition. The arrangement minimizes its associated energy cost and enables the ordered alloy to have a very low formation enthalpy. Al atoms begin to occupy tetrahedral configurations if Al component  $x$  is over 0.5. Because corundum  $\text{Al}_2\text{O}_3$  is stable under ambient conditions, the  $\beta\text{-(Al}_x\text{Ga}_{1-x})_2\text{O}_3$  alloy no longer maintains a monoclinic structure when the Al component  $x$  is greater than 0.7. The monoclinic phase could transform into the corundum structure gradually because the radius of the Al atom is smaller than that of the Ga atom. The lattice constant decreases with the increase of Al components; thus the volumes of the  $\beta\text{-(Al}_x\text{Ga}_{1-x})_2\text{O}_3$  alloy will decrease linearly, as shown in Fig. 18(b). The trend of lattice parameters follows Vegard's law. Besides, the bandgap of the  $\beta\text{-(Al}_x\text{Ga}_{1-x})_2\text{O}_3$  alloy can be modulated from 4.9 eV to 7 eV, as shown in Fig. 18(c).<sup>312,313</sup> The bandgap of  $\text{Al}_2\text{O}_3$  is larger than that of  $\beta\text{-Ga}_2\text{O}_3$  so that the bandgap will increase with the increase of Al content. Furthermore, the energy positions of the CBM and VBM of the  $\beta\text{-(Al}_x\text{Ga}_{1-x})_2\text{O}_3$  alloy vary with the alloy component  $x$ . The variations of  $x$  have apparent effects on the positions of the CBM ( $\Delta E_{\text{CBM}} > 3$  eV), while the energy positions of the VBM change little ( $\Delta E_{\text{VBM}} < 0.5$  eV).

As mentioned in the previous section, the CBM of  $\beta\text{-Ga}_2\text{O}_3$  is contributed by the 4s orbitals of Ga, while the VBM is contributed by the 2p orbitals of O. Similarly, the CBM of  $\text{Al}_2\text{O}_3$  is contributed by Al 3s orbitals, and the VBM is contributed by O 2p orbitals. When the Al content increases, the orbital contribution of the CBM of the alloy gradually changes from the Ga 4s orbital to the Al 3s orbital, while the VBM is only contributed by the O 2p orbitals. The metal cation s orbital interacts with O orbitals to form bonding orbitals and anti-bonding orbitals. The overlap of high energy anti-bonding orbitals mainly forms the conduction band of the alloy, while the overlap of low energy bonding orbitals forms the valence band of the alloy. Therefore, with the increase of Al components, the anti-bonding orbitals formed by interaction with O orbitals gradually raise the CBM energy of  $\beta\text{-Ga}_2\text{O}_3$  upward, and thus this tendency appears.<sup>312,314,315</sup>

$\beta\text{-(Al}_x\text{Ga}_{1-x})_2\text{O}_3$  films have been widely studied recently. The  $\beta\text{-(Al}_x\text{Ga}_{1-x})_2\text{O}_3$  film extends the range of potential applications and further optimizes device performance successfully, especially in power devices and optoelectronic devices. One of the advantages of the  $\beta\text{-(Al}_x\text{Ga}_{1-x})_2\text{O}_3$  bandgap engineering is to achieve high breakdown voltage of materials and achieve high response photodetectors. For example, although the dark current of the  $\beta\text{-(Al}_x\text{Ga}_{1-x})_2\text{O}_3$ -based solar-blind photodetector (0.356 nA) is higher than that of pure  $\text{Ga}_2\text{O}_3$  (35.8 pA), the



**Fig. 18** (a) Enthalpy of formation as a function of alloy concentration  $x$  in the corundum and monoclinic structures  $\beta\text{-(Al}_x\text{Ga}_{1-x})_2\text{O}_3$ . The lowest energy structures are represented by the solid symbols and higher energy structures are represented by open symbols under the same condition. Reproduced with permission.<sup>312</sup> Copyright 2018, American Institute of Physics Publishing. (b) The variations of  $\alpha\text{-(Al}_x\text{Ga}_{1-x})_2\text{O}_3$ 's and  $\beta\text{-(Al}_x\text{Ga}_{1-x})_2\text{O}_3$ 's volumes as a function of Al composition  $x$ . (c) The variations of  $\beta\text{-(Al}_x\text{Ga}_{1-x})_2\text{O}_3$ 's bandgap as a function of Al composition  $x$  obtained from many scholars' research. Reproduced with permission.<sup>314</sup> Copyright 2018, American Physical Society. (d) Enthalpy of formation as a function of alloy concentration  $x$  for  $\text{Ga}_2\text{O}_3$  alloying with  $\text{In}_2\text{O}_3$  in the bixbyite (blue squares) and monoclinic (red solid circles) crystal structure. The red open circles are higher-energy metastable alloys' configurations. Reproduced with permission.<sup>328</sup> Copyright 2015, American Physical Society.

responsivity is 15.7 times higher than that of pure Ga<sub>2</sub>O<sub>3</sub>-based solar-blind photodetector.<sup>316</sup> However, because the (Al<sub>x</sub>Ga<sub>1-x</sub>)<sub>2</sub>O<sub>3</sub> alloy is still subject to bulk phonon scattering, the mobility of the alloy (4 cm<sup>2</sup> V<sup>-1</sup> s<sup>-1</sup>) is not as good as that of pure Ga<sub>2</sub>O<sub>3</sub>, so it is not feasible to prepare devices based on the single alloy. At the same time, (Al<sub>x</sub>Ga<sub>1-x</sub>)<sub>2</sub>O<sub>3</sub> with a large bandgap can form the heterojunction with pure Ga<sub>2</sub>O<sub>3</sub>, and the large band-offset promotes the formation of the two-dimensional electron gas at the interface. This overcomes the influence of phonon scattering in the bulk on semiconductor mobility and can be applied to MODFET coupling with a Si δ-doped Ga<sub>2</sub>O<sub>3</sub> layer. Inspired by this, Krishnamoorthy *et al.* researched the performance and carrier mobility of MODFETs based on the β-(Al<sub>x</sub>Ga<sub>1-x</sub>)<sub>2</sub>O<sub>3</sub>/β-Ga<sub>2</sub>O<sub>3</sub> heterojunction.<sup>96,113,317–319</sup> In their studies, the devices showed excellent switching characteristics and the mobility was up to 180 cm<sup>2</sup> V<sup>-1</sup> s<sup>-1</sup> by Hall measurements at room temperature, which is higher than that of bulk materials but still lower than the theoretical mobility. It is found in the experiments that the defects of the (Al<sub>x</sub>Ga<sub>1-x</sub>)<sub>2</sub>O<sub>3</sub> alloy also increase with the increase of Al components.<sup>320–322</sup> Thus, it is still necessary to optimize the defects to achieve higher carrier mobility continuously.

In alloy engineering based on other phases, the bandgap of the alloy increases with the increase of Al composition, while the lattice parameters decrease further. Both of them are similar to the situations in β-(Al<sub>x</sub>Ga<sub>1-x</sub>)<sub>2</sub>O<sub>3</sub> alloy engineering. For example, the bandgap can be tuned from 5.3 eV to 8.5 eV with the variation of the Al component in α-(Al<sub>x</sub>Ga<sub>1-x</sub>)<sub>2</sub>O<sub>3</sub>. The variations of *x* also have effects on the positions of the CBM ( $\Delta E_{\text{CBM}} > 3$  eV), while the energy positions of the VBM change little ( $\Delta E_{\text{VBM}} < 0.1$  eV). Note that α-(Al<sub>x</sub>Ga<sub>1-x</sub>)<sub>2</sub>O<sub>3</sub> still maintains the single corundum structure (*x* = 0–100%)<sup>82</sup> because the structures of Al<sub>2</sub>O<sub>3</sub> and α-Ga<sub>2</sub>O<sub>3</sub> are all corundum structures consisting of octahedral structures. This provides convenience for α-(Al<sub>x</sub>Ga<sub>1-x</sub>)<sub>2</sub>O<sub>3</sub> alloy engineering realized in α-Ga<sub>2</sub>O<sub>3</sub>.

**4.2 (In<sub>x</sub>Ga<sub>1-x</sub>)<sub>2</sub>O<sub>3</sub>.** The ground-state structure of In<sub>2</sub>O<sub>3</sub> is the body-centered cubic bixbyite structure. In this structure, all the In atoms are octahedrally coordinated. The fundamental direct bandgap of In<sub>2</sub>O<sub>3</sub> is about 2.9 eV by XPS measurements and DFT calculations.<sup>323–326</sup> However, its optical bandgap is large (3.73 eV). Due to the inversion center of the bixbyite crystal structure, the electrons' transition from the VBM to the CBM is dipole forbidden.<sup>327</sup> Only transitions from states lower in the valence band are allowed and lead to strong absorption. Therefore, the optical bandgap is relatively large. In addition, it is found that the CBM of In<sub>2</sub>O<sub>3</sub> is contributed by the In 5s orbital, which has a large radius and wave function overlap degree compared with the Ga 4s orbital by the analysis of DOS. Therefore, In doping is more helpful for the conduction of electrons.

In atoms prefer to substitute the octahedral Ga site (Ga<sub>(2)</sub>) in β-(In<sub>x</sub>Ga<sub>1-x</sub>)<sub>2</sub>O<sub>3</sub> alloy because the atomic radius of In is larger than that of Ga. The lattice parameters of the (In<sub>x</sub>Ga<sub>1-x</sub>)<sub>2</sub>O<sub>3</sub> alloy keep increasing with the increase of the In composition, which makes the volume of the (In<sub>x</sub>Ga<sub>1-x</sub>)<sub>2</sub>O<sub>3</sub> alloy system keep increasing. This trend increases linearly and meets Vegard's law, too. By incorporating different components of In, the

bandgap of β-(In<sub>x</sub>Ga<sub>1-x</sub>)<sub>2</sub>O<sub>3</sub> can vary from 2.9 eV to 4.9 eV. Note that the bandgap of β-(In<sub>x</sub>Ga<sub>1-x</sub>)<sub>2</sub>O<sub>3</sub> will decrease when the In content increases because the bandgap of In<sub>2</sub>O<sub>3</sub> is smaller than that of Ga<sub>2</sub>O<sub>3</sub>. The phase separation occurs when In is added with a certain concentration due to the different stable lattice structures between In<sub>2</sub>O<sub>3</sub> and β-Ga<sub>2</sub>O<sub>3</sub>. The critical point of phase separation is related to many factors, *e.g.*, different substrates and temperatures. The results of first-principles calculations can reveal the insight mechanism involved. Peelaers *et al.* further revealed the phase transition mechanism by calculating the formation enthalpy under different In components, as shown in Fig. 18(d).<sup>328</sup> The monoclinic structure of β-(In<sub>x</sub>Ga<sub>1-x</sub>)<sub>2</sub>O<sub>3</sub> will be energetically favorable when *x* < 0.5. This trend can be explained by considering the cationic configuration of different crystal structures. In the monoclinic structure, octahedral Ga and tetrahedral Ga account for half respectively. The In atom tends to occupy an octahedral position and form In–O octahedral configurations. This configuration has the lowest energy. If *x* is over 0.5, In occupies the Ga<sub>(1)</sub> atom gradually because all Ga<sub>(2)</sub> atoms have been occupied by In atoms. This will introduce local strain and require extra energy, which results in energy enlargement. Therefore, this tendency leads to phase instability, which leads to the phase transition from the monoclinic structure to the cubic bixbyite structure gradually. In other metastable phases of Ga<sub>2</sub>O<sub>3</sub>, the variable rules of bandgap and lattice parameters after doping In are the same as those in β-(In<sub>x</sub>Ga<sub>1-x</sub>)<sub>2</sub>O<sub>3</sub>, and the existence of phase separation still needs to be paid attention in practical applications.<sup>329–331</sup>

(In<sub>x</sub>Ga<sub>1-x</sub>)<sub>2</sub>O<sub>3</sub> alloys also have potential applications in power and optoelectronic devices. In 2015, Wenckstern *et al.* investigated the SBD based on the (In<sub>x</sub>Ga<sub>1-x</sub>)<sub>2</sub>O<sub>3</sub> alloy.<sup>325</sup> In the absence of phase transition, the series resistances of the diodes based on (In<sub>x</sub>Ga<sub>1-x</sub>)<sub>2</sub>O<sub>3</sub> decreased with the increase of the In content. Moreover, it limited the forward current of the diode, increased the reverse current, and had a great influence on the rectifier characteristics of the diode. Then they also fabricated the SBD based on the Si-doped (In<sub>x</sub>Ga<sub>1-x</sub>)<sub>2</sub>O<sub>3</sub> alloy. The forward current of the diode based on (In<sub>x</sub>Ga<sub>1-x</sub>)<sub>2</sub>O<sub>3</sub> doped by Si became larger than that of the undoped (In<sub>x</sub>Ga<sub>1-x</sub>)<sub>2</sub>O<sub>3</sub> diode, while the reverse current and series resistance varied little. It can be concluded that the reverse current and series resistance are more dependent on the In content. In addition, the rectification ratio was still very low. In the field of optoelectronic devices, Vasylytsiv *et al.* found that the dark conductivity and the photoconductivity decreased with increasing In composition under the condition that the monoclinic structure of the (In<sub>x</sub>Ga<sub>1-x</sub>)<sub>2</sub>O<sub>3</sub> alloy remains unchanged.<sup>332</sup> The responsivity of the photodetectors increased with the increase of the In component gradually; thus this is an advantage of the detectors based on the (In<sub>x</sub>Ga<sub>1-x</sub>)<sub>2</sub>O<sub>3</sub> alloy.

## IV. Effects of impurities and defects on other properties

In addition to their influence on electronic properties, defects and impurities also have significant influence on the magnetic, piezoelectric, luminescence, and scintillation properties of



$\beta$ -Ga<sub>2</sub>O<sub>3</sub>. The variations and mechanisms of other physical properties induced by defects and impurities are summarized in this section. The defects and impurities induced modulation of these properties broadens the application range of Ga<sub>2</sub>O<sub>3</sub>, such as spintronic devices, piezoelectric devices, scintillators, radiation detectors, *etc.*

### 1. Magnetic properties

Spin manipulation in semiconductors, that is spintronics, provides a new development path for the functional materials.  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> with an ideal stoichiometric ratio does not exhibit good magnetic properties because of the 3d<sup>10</sup> configuration of Ga<sup>3+</sup> ions. In 2007, Sridharan *et al.* discovered the ferromagnetism existing in  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>.<sup>333</sup> They found by PL measurements that the photoluminescence intensity varied greatly with the variation of the magnetic field. They believed that this magnetism could form locally around the specific locations of V<sub>O</sub>s. With further research, the magnetic moment of  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> appeared obviously when V<sub>Ga</sub> was introduced. Although it is still difficult to realize p-type  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> by introducing many V<sub>Ga</sub>s as discussed previously, this phenomenon means that V<sub>Ga</sub> is of great significance for expanding the applications of  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> in spin electronic devices. In general, charged V<sub>Ga</sub>s exist mainly in three forms, *i.e.*, V<sub>Ga</sub><sup>-</sup>, V<sub>Ga</sub><sup>2-</sup> and V<sub>Ga</sub><sup>3-</sup>. Among them, V<sub>Ga</sub><sup>-</sup> and V<sub>Ga</sub><sup>2-</sup> discovered by electron paramagnetic resonance (EPR) under high neutron irradiation exhibit magnetic properties. The origin of magnetism in Ga<sub>2</sub>O<sub>3</sub> is mainly caused by the localization effects of the surrounding oxygen negative ions as revealed by reported research, *i.e.*, due to the presence of unpaired electrons in the 2p orbitals of O ions.<sup>334</sup> In addition, the highly localized holes around oxygen ions and the lattice relaxation due to the presence of charged cation vacancies further confirm that the defect levels introduced by V<sub>Ga</sub> are not shallow. In addition, Son *et al.* performed EPR studies on  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> annealed in an O<sub>2</sub> environment.<sup>335</sup> They found that the annealing process also induced an electron paramagnetic resonance center named IR1. The IR1 was speculated from V<sub>Ga(1)</sub><sup>2-</sup> or the V<sub>Ga(1)</sub>-Ga<sub>1</sub>-V<sub>Ga(1)</sub> complex. Although intrinsic  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> is a non-magnetic material, the magnetic  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> can be realized in different experimental environments, such as annealing, irradiation to create Ga vacancies in the host crystal, doping with some magnetic impurities, *etc.* Therefore, the specific environments make  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> magnetic, which has potential in the application of spintronic devices, *e.g.*, spin-glass, magnetic random access memory (MRAM), *etc.*<sup>336,337</sup>

According to the previous theoretical predictions, doping transition metals, especially Mn, in wide bandgap semiconductors can enable the semiconductors to have a high Curie temperature ( $T_C$ ) exceeding room temperature.<sup>338</sup> Besides, it is found that magnetic impurity doping can achieve good dilute magnetic semiconductor characteristics in wide bandgap oxide semiconductors. Typically, this means replacing a few percent of host atoms with transition metal impurities which carry large spin magnetization in the host ligand field. If these magnetic impurities exhibit ferromagnetic interactions, the entire system may exhibit bulk ferromagnetism as long as the

ferromagnetic interactions extend beyond the impurity distance of typical impurities. These are the prerequisites for obtaining spintronic materials. Previously, Mn<sup>339–342</sup> and Cr<sup>339,343–345</sup> have been incorporated into other wide bandgap semiconductors (*e.g.*, ZnO, GaN, and GaAs) and the doped semiconductors show good magnetism. Inspired by these research phenomena, the magnetic properties of Mn and Cr doped  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> are also studied in many kinds of research.

To realize Mn-doped Ga<sub>2</sub>O<sub>3</sub> successfully, Minami *et al.* prepared it by the sol-gel method, and Kim *et al.* obtained Mn-doped Ga<sub>2</sub>O<sub>3</sub> at an annealing temperature exceeding 100 °C by magnetron sputtering.<sup>346,347</sup> However, the quality of the films prepared by these two methods is not very good. The ferromagnetic properties in their research are not very obvious. Subsequently, Guo *et al.* realized high-quality  $\beta$ -(Ga<sub>1-x</sub>Mn<sub>x</sub>)<sub>2</sub>O<sub>3</sub> on sapphire by the laser molecular beam epitaxy technique.<sup>348,349</sup> The  $\beta$ -(Ga<sub>1-x</sub>Mn<sub>x</sub>)<sub>2</sub>O<sub>3</sub> alloy showed ferromagnetism at room temperature when  $x \geq 0.11$ . Furthermore, the magnetization and coercivity of the  $\beta$ -(Ga<sub>1-x</sub>Mn<sub>x</sub>)<sub>2</sub>O<sub>3</sub> alloy enhanced significantly with the increasing Mn content. That is, as  $x$  increases, the saturation magnetization ( $M_s$ ) monotonically increases from 5.5 emu cm<sup>-3</sup> to the maximum of 33.1 emu cm<sup>-3</sup>, and the coercivity and remanence ( $M_r$ ) also increase. Although they applied the bound magnetic polaron (BMP) model to explain the experimental results, they still did not get reasonable results. Wang *et al.* further revealed the internal mechanism of the ferromagnetic phenomenon and variations caused by Mn doping in Ga<sub>2</sub>O<sub>3</sub> by the first-principles calculations method in 2019. They revealed that the spatial delocalization of O 2p orbitals and the strong overlap of p-d orbitals led to a stable ferromagnetic state at room temperature, as discovered in the early experiment.<sup>348</sup> Besides, Guo *et al.* obtained Cr doped Ga<sub>2</sub>O<sub>3</sub> vermicular nanowires and further explored the magnetic properties.<sup>350</sup> They found that the nanostructured Ga<sub>2</sub>O<sub>3</sub>:Cr exhibited anisotropic magnetic behavior. Derived from the  $M$ - $H$  curve diagram, the largest saturation magnetization and coercivity in the Ga<sub>2</sub>O<sub>3</sub>:Cr nanostructure are 62.2 emu cm<sup>-3</sup> and 115 Oe, respectively.

Additionally, it is found that Zn-doped Ga<sub>2</sub>O<sub>3</sub> may show spin properties as investigated by first-principles calculations in recent years. The formation energy of Zn doped Ga<sub>2</sub>O<sub>3</sub> which is a ferromagnetic (FM) semiconductor with 100% spin polarization is lower than that of the undoped and non-spin Ga<sub>2</sub>O<sub>3</sub> system, which reveals that the ferromagnetic Zn doped system is easy to form. Meanwhile, the spin effects in Zn doped Ga<sub>2</sub>O<sub>3</sub> are affected by the p-d hybridization of O and Zn atoms.<sup>272,351</sup> The magnetic moment of Zn-doped Ga<sub>2</sub>O<sub>3</sub> is 1.0 $\mu_B$  per cell. It is noticed that the magnetic moment of the system will drop to 0.49 $\mu_B$  per cell with the introduction of V<sub>O</sub>s. Therefore, a large number of V<sub>O</sub>s should be avoided to obtain Zn-doped Ga<sub>2</sub>O<sub>3</sub> with excellent magnetic properties.

### 2. Luminescence properties

The doping control of  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> is complicated due to self-compensation and defects, especially point defects. Meanwhile, the research of electronic transitions during light emission

provides a deep understanding of the related mechanism of defects. The luminescence properties of  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> have also attracted extensive attention because they can indirectly reflect the behavior of intrinsic and/or external defects and impurities in  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>. According to recent research, there are no emission peaks in the near band edge of  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>. They nearly exist in the ultraviolet (UVL, 3.2–3.6 eV), blue (BL, 2.8–3.0 eV), and green (GL, 2.4 eV) band regions of the emission spectra of  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>, as shown in Fig. 19(a).<sup>206,352–355</sup> The origins of these different band regions have also been studied in depth by some measurements. In summary, the UVL band is due to the carriers' (electron–hole) recombination, as shown in Fig. 19(b). The BL band is caused by self-trapped holes or electrons trapped by V<sub>O</sub>s and the GL band is caused by the interaction between self-trapped holes and electrons trapped by a cluster of V<sub>O</sub>s. Note that the cathodoluminescence (CL) spectrum is affected by some factors, *e.g.*, temperature. The measurement of the temperature-dependent CL spectrum of the (001) undoped  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> substrate by the FZ method is shown in Fig. 19(a). At low temperatures (<200 K), the intensity of the UVL band is more obvious in the undoped Ga<sub>2</sub>O<sub>3</sub> single crystal. However, the intensities of the GL band and the BL band increase gradually as the temperature increases, while the intensity of the UVL band decreases. This may be due to the gradual strengthening of recombination caused by deep-level defects at high temperatures.

Besides temperature, doping can also have certain effects on the CL spectrum so that it can reveal the influence of impurities and defects. Luminescence measurements are considered to be a very effective tool to detect and identify impurities or intrinsic

defects by the recombination of generated excess carriers at the defect levels. In order to discover the intrinsic mechanism, Ouma *et al.* studied the donor Si and the compensating acceptor Mg doped  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> substrates in detail, and the CL spectrum measurements were carried out, as shown in Fig. 19(c and d).<sup>352</sup> In the Si-doped sample, the intensity was only in the ultraviolet region as the temperature varies, while in the Mg-doped sample, the intensity was similar to that of the undoped sample, but the intensity of the GL band and the BL band became strong under the high-temperature condition. It can be concluded that the UVL band is independent of impurities. The more detailed origins of the UVL band can be attributed to the recombination of free electrons and STHs or STEs. The BL band is attributed to the donor–acceptor pair (DAP) transition including deep donors and acceptors as shown in Fig. 19(b). As mentioned previously, the V<sub>O</sub> is a deep-level donor impurity, while the V<sub>Ga</sub> is a deep-level acceptor impurity in the conclusions obtained from first-principles calculations. The formation energies of charged defects and impurities depend on the position of the Fermi level ( $E_f$ ). In general, the formation energy of charged V<sub>O</sub>s decreases when  $E_f$  is close to the VBM. In the Mg-doped  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> sample,  $E_f$  shifts toward the VBM in a degree. In the Si-doped  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> sample, the formation energy gradually increases as  $E_f$  approaches the CBM. The variations of Fermi levels and formation energies in these two systems can reflect the variations of resistivity indirectly. It is known that the resistivity of intrinsic Ga<sub>2</sub>O<sub>3</sub> is related to vacancies. The variation of resistivity after doping is related to BL intensity in terms of spectrum. Therefore, V<sub>Ga</sub> and V<sub>O</sub>, especially V<sub>O</sub>, have a strong correlation to the BL band. It has

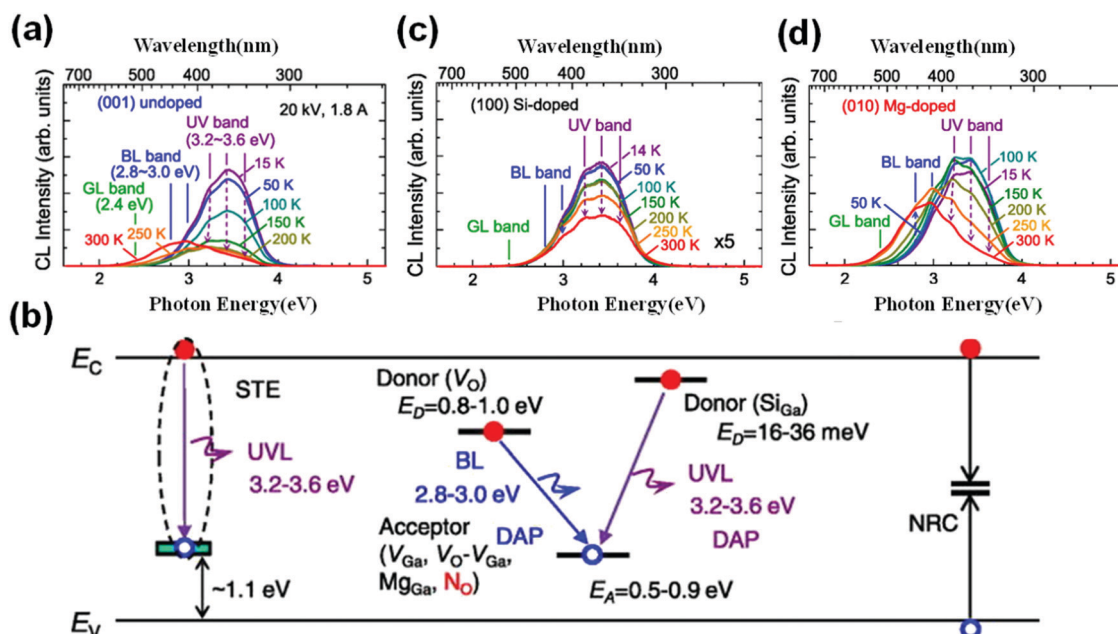


Fig. 19 (a) Temperature-dependent CL spectra of (001) undoped  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> crystal samples. Reproduced with permission.<sup>174</sup> Copyright 2013, American Institute of Physics Publishing. (b) The schematic diagram of emission mechanism models of UVL and BL bands in  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>. Reproduced with permission.<sup>385</sup> Copyright 2018, American Institute of Physics Publishing. Temperature-dependent CL spectrum of (c) (100) Si-doped (enlarged by a factor of 5) and (d) (010) Mg-doped  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> crystal samples. Reproduced with permission.<sup>174</sup> Copyright 2013, American Institute of Physics Publishing.

been inferred that the possible deep donors are  $V_O$  and  $Ga_i$ , and the possible acceptors are  $V_{Ga}$ ,  $V_O-V_{Ga}$  complex, and  $Mg_{Ga}$ . Besides, the effects of doping on intrinsic defects in  $\beta\text{-Ga}_2\text{O}_3$  can be reflected by the change of the BL band indirectly. For example, the suppression of the BL band in heavy N-doped  $\beta\text{-Ga}_2\text{O}_3$  epitaxial films is evidence that N-doping in  $\beta\text{-Ga}_2\text{O}_3$  leads to a decrease in  $V_O$  concentrations and the resulting high resistivity in N-doped epitaxial films.<sup>104,356</sup> In addition, transition metals such as Cr, Fe, Co, Ni, Mn, and Ti (except Cu) have been incorporated into  $\text{Ga}_2\text{O}_3$  for further exploration.<sup>357–360</sup> The results are that the BL bands of these elements doped  $\text{Ga}_2\text{O}_3$  become suppressed. As for the GL band, it has been discovered that it is related to  $\text{O}_2$  partial pressure in FZ growth, but its particular mechanism has not been discovered.<sup>354</sup>

### 3. Piezoelectric properties

The piezoelectric effect is an important phenomenon in semiconductor research. The causes of this phenomenon are that ionic polarization generates a piezoelectric potential in the presence of external strain due to the asymmetric structure of crystals especially, for example, ZnO, GaN, and InN. Because of its structural similarity to GaN,  $\varepsilon\text{-Ga}_2\text{O}_3$  has also been found to have piezoelectric properties, as mentioned previously.<sup>7,214,361,362</sup> Although monoclinic  $\beta\text{-Ga}_2\text{O}_3$  has a low symmetry, no piezoelectric properties are found in it. In recent years, it has been discovered that doped  $\beta\text{-Ga}_2\text{O}_3$  has piezoelectric properties. Different from the previous research focusing on electronic properties by doping, Li *et al.* further found that  $\beta\text{-Ga}_2\text{O}_3$  doped with unique elements manifested piezoelectricity and the positions of doping elements in the Periodic Table were related to the magnitude of the piezoelectric coefficient recently, as shown in Fig. 20(a).<sup>363</sup>

The impurities (*e.g.*, Ni, Cu, Zn, In, and Sn) away from Ga made the doped  $\beta\text{-Ga}_2\text{O}_3$  exhibit strong piezoelectric properties, that is, the values of  $e_{11}$  in different doping systems increase more or less compared with that of intrinsic  $\beta\text{-Ga}_2\text{O}_3$  ( $e_{11} = 0.02\text{--}11.24 \text{ C m}^{-2}$ ). The piezoelectric potential of the  $\beta\text{-Ga}_2\text{O}_3$  crystal can be applied to modulate the carrier behavior at the metal–semiconductor or p–n junction interface, thus optimizing the device performance. Relative studies open new fields for other applications of the family of  $\text{Ga}_2\text{O}_3$ .

### 4. Scintillation properties

A scintillator is a kind of material applied for radiation detectors, which plays an important role in the detection of medical imaging, safety, astrophysics and logging, and other fields. In general, scintillators are made of insulators and semiconductors. In recent years,  $\beta\text{-Ga}_2\text{O}_3$  has been considered as a potential candidate for fast scintillation detection devices.<sup>364</sup> Some elements are selected as dopants and the doping behaviors (*e.g.*, single doping, double doping, and triple doping) will affect the scintillator characteristics.<sup>232,365–370</sup> It has been discovered that the crystal  $\beta\text{-Ga}_2\text{O}_3$  is doped by various dopants such as Ce,<sup>365,370,371</sup> Al,<sup>365,370</sup> Mg,<sup>372</sup> Pr,<sup>373</sup> Be,<sup>372</sup> Ba,<sup>372</sup> Bi,<sup>374</sup> Sn,<sup>367,374</sup> and Si coupled with Ce<sup>375,376</sup> to obtain excellent scintillation properties. The dopants affect the position and shape of the scintillation spectra. For example, Usui *et al.* investigated the scintillation spectra of undoped  $\beta\text{-Ga}_2\text{O}_3$  and that of the  $\beta\text{-Ga}_2\text{O}_3$  bulk doped with some elements (In, Tl, Sn, Pd, Sb, and Bi) under X-ray irradiation, as shown in Fig. 20(b and c).<sup>374</sup> The spectrum of the doped  $\beta\text{-Ga}_2\text{O}_3$  was similar to that of the undoped  $\beta\text{-Ga}_2\text{O}_3$ , but there were still some differences in the shape and position. Generally, these dopants are

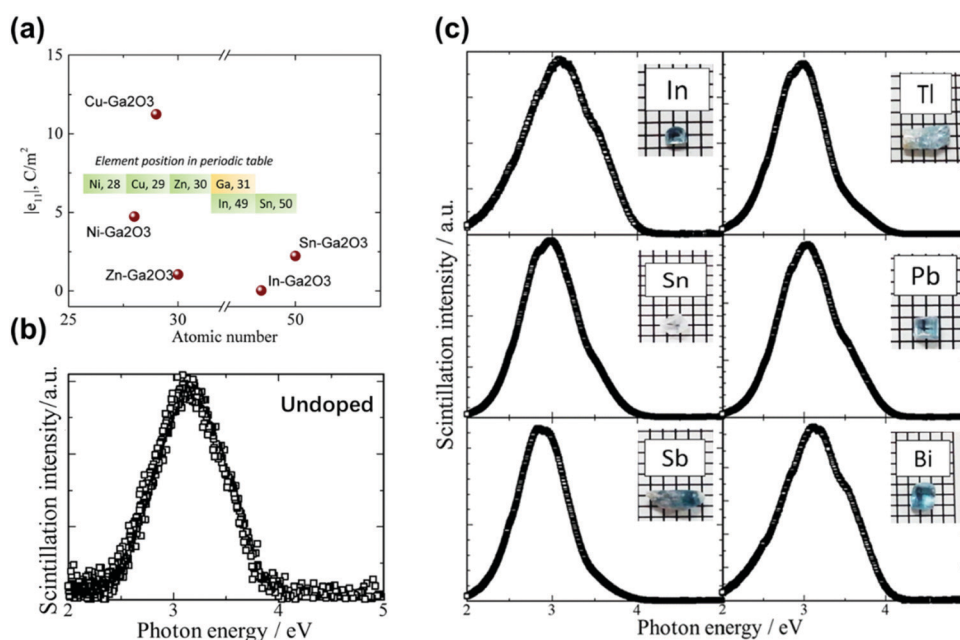


Fig. 20 (a) Piezoelectric coefficients of Ni, Cu, Zn, In, and Sn doped  $\beta\text{-Ga}_2\text{O}_3$ . The inset graph shows dopants' positions in the Periodic Table. Reproduced with permission.<sup>386</sup> Copyright 2021, American Institute of Physics Publishing. Scintillation spectra of (b) undoped and (c) In, Tl, Sn, Pb, Sb, and Bi doped bulk  $\text{Ga}_2\text{O}_3$  under X-ray irradiation. Reproduced with permission.<sup>374</sup> Copyright 2017, Elsevier Ltd.

divided into three groups for scintillation doping: electron-rich and electron-poor elements in main group elements, and rare earth elements. Compared with the undoped  $\beta\text{-Ga}_2\text{O}_3$ , the scintillation properties of  $\text{Ga}_2\text{O}_3$  doped with rare earth elements can be observed obviously. In addition, the emission peaks in  $\beta\text{-Ga}_2\text{O}_3$  doped with electron-poor dopants have different positions, while the  $\beta\text{-Ga}_2\text{O}_3$  doped with electron-rich dopants show fewer changes in the emission shape. These research studies bring significance to the further applications of optoelectronic and radiation detection devices, and thus relative research is deeply being carried out.

## V. Summary and outlook

In this review, we have summarized the recent advances in the effects of doping, defects, and passivation on the material properties (*e.g.*, electronic, optical, magnetic, *etc.*) of  $\text{Ga}_2\text{O}_3$ , especially common  $\beta\text{-Ga}_2\text{O}_3$ . First, the basic properties (electronic, absorption, thermal and mechanical) of intrinsic  $\beta\text{-Ga}_2\text{O}_3$  were summarized. Considering the uniqueness of the monoclinic  $\beta\text{-Ga}_2\text{O}_3$  structure, it was successfully transformed into low-dimensional  $\text{Ga}_2\text{O}_3$  by the mechanical exfoliation method, thereby expanding the research areas of  $\text{Ga}_2\text{O}_3$ . Therefore, the intrinsic properties of the new semiconductor, *i.e.*, low-dimensional  $\text{Ga}_2\text{O}_3$ , were also discussed. Then, some defects (*e.g.*,  $V_{\text{O}}$ ,  $V_{\text{Ga}}$ ,  $\text{Ga}_i$ ,  $\text{O}_i$ , and deep-level defects) in undoped  $\beta\text{-Ga}_2\text{O}_3$  were discussed in detail. Note that the intrinsic  $\beta\text{-Ga}_2\text{O}_3$  manifested n-type semiconductor behavior which was considered to be caused by the effects of  $V_{\text{O}}$ s or defect complexes. Besides, the unintentional doping mechanism had also been accepted to be another reason. Although intrinsic  $\beta\text{-Ga}_2\text{O}_3$  behaved as an electron-rich semiconductor, its low carrier concentrations and high defects cannot meet the requirements of high-performance devices. Doping was a common strategy to modulate semiconductor properties.<sup>379,386</sup> Then, the mechanism of the electronic properties of  $\beta\text{-Ga}_2\text{O}_3$  tuned by single doping (donors and deep acceptors), co-doping, and surface passivation of hetero-valence elements was discussed. Meanwhile, the situations of homo-valence elements (Al and In) substituting Ga to form alloys were also discussed. Note that it was relatively easy to achieve n-type doping in bulk  $\beta\text{-Ga}_2\text{O}_3$ , while the troublesome problem is how to achieve effective p-type doping. No reasonable solutions have been found so far. Besides, considering that it is difficult to precisely control the substitution doping in low-dimensional  $\text{Ga}_2\text{O}_3$  by ion implantation, the properties of low-dimensional  $\text{Ga}_2\text{O}_3$  are usually tuned by surface passivation. The related research is briefly summarized in this review. Lastly, the effects of defects and impurities on other properties (*i.e.*, magnetic, luminescence, scintillation, and piezoelectric) of  $\beta\text{-Ga}_2\text{O}_3$  are discussed briefly.

The intrinsic properties of  $\text{Ga}_2\text{O}_3$  have been studied in detail for a long time, and their advantages have been gradually understood. Subsequently,  $\text{Ga}_2\text{O}_3$  with modulated properties by defects and impurities is considered to further optimize

semiconductor and microelectronics technology. It should be realized that there are still some obstacles which need to be overcome and the directions worthy of being further researched so that large-scale and deep applications of  $\beta\text{-Ga}_2\text{O}_3$  are realized in the future:

(1) The true reasons for undoped  $\beta\text{-Ga}_2\text{O}_3$  manifesting n-type semiconductor behavior: although the fabrication of  $\beta\text{-Ga}_2\text{O}_3$  is relatively mature at present,  $\beta\text{-Ga}_2\text{O}_3$  prepared by either melting method or epitaxy method manifests the features of an n-type semiconductor. There are still controversial opinions about this phenomenon. At present, the generally accepted viewpoints are (a) the effects of intrinsic defects and complexes of impurities coupling with defects, *e.g.*,  $V_{\text{O}}$  and  $V_{\text{Ga}}\text{-H}$  complex; (b) the effects of unintentional dopants such as H and Ir introduced in the process. The n-type feature of  $\beta\text{-Ga}_2\text{O}_3$  deposited by physical vapor deposition is mainly due to  $V_{\text{O}}$  and that prepared by chemical vapor deposition and the melting method is mainly due to  $V_{\text{O}}$  and unintentional dopants; this opinion is widely accepted in the experiments. However, through first-principles calculations, it is found that the defect level position introduced by  $V_{\text{O}}$  is deep. Therefore, it does not play a crucial role in the n-type conduction in undoped  $\beta\text{-Ga}_2\text{O}_3$ . Thus, subsequent research is urgent to further reveal the internal mechanism of undoped  $\beta\text{-Ga}_2\text{O}_3$  depicted as an n-type semiconductor in order to unify the theoretical and experimental results.

(2) The suitable acceptors and the realization of effective p-type  $\beta\text{-Ga}_2\text{O}_3$ : despite continuous explorations of suitable acceptors in  $\beta\text{-Ga}_2\text{O}_3$ , there are still no effective p-type dopants reported. It is reported that effective p-type  $\beta\text{-Ga}_2\text{O}_3$  is difficult to obtain due to the following factors: (a) the VBM of  $\beta\text{-Ga}_2\text{O}_3$  is relatively flat and the dispersion degree is small, and thus the hole effective mass is large and the mobility is low; (b) ionized holes in  $\beta\text{-Ga}_2\text{O}_3$  are easy to form self-trapped holes (STHs), and thus the holes cannot move freely. These affect the holes' transport in  $\beta\text{-Ga}_2\text{O}_3$ ; (c) the acceptors have low solubility and ionization rates, and they will introduce deep levels in the bandgap. The deep level has a little contribution to the p-type conduction in  $\beta\text{-Ga}_2\text{O}_3$ ; (d) the background carriers in  $\beta\text{-Ga}_2\text{O}_3$  are high due to the unintentional doping effects, and a small number of holes ionized by the acceptors are quickly compensated. Considering the above reasons, the optimizations that should further reduce the effects of defects and unintentional impurities in  $\beta\text{-Ga}_2\text{O}_3$  can be adapted, thereby reducing the background carrier concentrations. Meanwhile, co-doping can further improve the solubility of dopants, and thus it can be attempted to achieve p-type  $\beta\text{-Ga}_2\text{O}_3$  by co-doping acceptors instead of single doping in experiments in the future.

(3) The in-depth exploration of the effects of defects and impurities on other properties of  $\beta\text{-Ga}_2\text{O}_3$ : impurities and defects can modulate not only the electronic properties of  $\beta\text{-Ga}_2\text{O}_3$  but also other material properties. As mentioned in this review, impurities and defects can make  $\beta\text{-Ga}_2\text{O}_3$  have magnetic, piezoelectric, photocatalytic, and scintillator properties, which will further expand the applications of  $\beta\text{-Ga}_2\text{O}_3$  beyond optoelectronics and power devices. Relevant studies have established a certain theoretical basis in recent years, and many



scholars have also carried out relevant experimental exploration. Therefore, more in-depth studies are needed to reveal the deeper value of  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> in these fields.

(4) The related research (defects and impurities) in other phases of Ga<sub>2</sub>O<sub>3</sub>: because  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> is the most stable among the six phases of Ga<sub>2</sub>O<sub>3</sub> under ambient conditions, most of the current research is based on  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>. Other phases of Ga<sub>2</sub>O<sub>3</sub> are also worth researching because other phases of Ga<sub>2</sub>O<sub>3</sub> have better performance or novel performance compared with  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> in some areas. For example,  $\alpha$ -Ga<sub>2</sub>O<sub>3</sub> has a larger bandgap, and thus it has a larger breakdown field compared with  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>, which is expected to further improve the performance of Ga<sub>2</sub>O<sub>3</sub> based power devices such as breakdown voltage. Besides, hexagonal  $\varepsilon$ -Ga<sub>2</sub>O<sub>3</sub> has a larger spontaneous polarization compared with GaN. By combining  $\varepsilon$ -Ga<sub>2</sub>O<sub>3</sub> with  $\varepsilon$ -(Al<sub>x</sub>Ga<sub>1-x</sub>)<sub>2</sub>O<sub>3</sub> to form a heterojunction, more two-dimensional electron gas (2DEG) will be generated due to large spontaneous polarization at the  $\varepsilon$ -(Al<sub>x</sub>Ga<sub>1-x</sub>)<sub>2</sub>O<sub>3</sub>/ $\varepsilon$ -Ga<sub>2</sub>O<sub>3</sub> interface. Therefore, the charges increase resulting in the increment of current density under the condition of the same cross-section. The output performance of MODFETs based on  $\varepsilon$ -(Al<sub>x</sub>Ga<sub>1-x</sub>)<sub>2</sub>O<sub>3</sub>/ $\varepsilon$ -Ga<sub>2</sub>O<sub>3</sub> will be improved. Therefore, the research should be extended to other phases of Ga<sub>2</sub>O<sub>3</sub> appropriately in the future. Surprising results may be obtained in these research studies.

(5) Deep research on the appropriate passivation atoms modulating the properties of low-dimensional Ga<sub>2</sub>O<sub>3</sub>: in recent years, with the deepening research of  $\beta$ -Ga<sub>2</sub>O<sub>3</sub>, the scholars find that  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> can be mechanically exfoliated to obtain low-dimensional Ga<sub>2</sub>O<sub>3</sub>. Due to the presence of dangling bonds at the surface, scholars apply atoms such as H and halogen elements (F and Cl) to passivate the surface. In addition to achieving stability, they find that the band structure and orbital contribution of low dimensional Ga<sub>2</sub>O<sub>3</sub> are affected by the passivation atoms. This discovery provides a new avenue to modulate the internal properties of low-dimensional Ga<sub>2</sub>O<sub>3</sub>, that is, surface passivation. Therefore, it is necessary to find appropriate passivation atoms to passivate the dangling bonds on the surface of low-dimensional Ga<sub>2</sub>O<sub>3</sub> in order to obtain stability coupled with improved properties of low-dimensional Ga<sub>2</sub>O<sub>3</sub>. In addition to the theoretical prediction, experiments are needed to confirm it.

## Conflicts of interest

There are no conflicts to declare.

## Acknowledgements

This work was financially supported by the National Key Research and Development Program of China (Grant 2021YFA0715600, 2018YFB2202900), the National Natural Science Foundation of China (52192610), the Key Research and Development Program of Shaanxi Province (Grant 2020GY-310), Wuhu and Xidian University special fund for industry-university-research

cooperation (XWYCY-012021004), the Fundamental Research Funds for the Central Universities and the Innovation Fund of Xidian University.

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